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1 Orderable parts

The PF3000 is available with pre-programmed OTP memory configurations. The devices are identified using the program codes from Table 1. Details of the OTP programming for each device can be found in Table 42.

Table 1. Orderable part variations

| Part number | Temperature (T _A) | Package | Programming options | Notes |
|-----------------|-------------------------------|---|--------------------------|----------|
| MC32PF3000A0EP | | | 0 - Not programmed | |
| //C32PF3000A3EP | | | 1 (i.MX 7 with DDR3L) | |
| MC32PF3000A2EP | | | 2 (i.MX 7 with LPDDR3) | |
| MC32PF3000A3EP | -40 °C to 85 °C | | 3 (i.MX 6SX with DDR3L) | |
| MC32PF3000A4EP | (For use in Consumer | 98ASA00719D, 48 QFN 7.0 mm x 7.0 mm with exposed pad | 4 (i.MX 6SX with DDR3) | (1), (2) |
| MC32PF3000A5EP | applications) | | 5 (i.MX 6SL with LPDDR2) | |
| MC32PF3000A6EP | | | 6 (i.MX 6UL with LPDDR2) | |
| MC32PF3000A7EP | | | 7 (i.MX 6UL with DDR3L) | |
| MC32PF3000A8EP | | | 8 (i.MX 6UL with DDR3) | |
| MC33PF3000A0ES | | | 0 - Not programmed | |
| MC33PF3000A3ES | | -40 °C to 105 °C or use in Automotive applications) 98ASA00933D, 48 QFN 7.0 mm x 7.0 mm WF-type (wettable flank) | 3 (i.MX 6SX with DDR3L) | |
| MC33PF3000A4ES | | | 4 (i.MX 6SX with DDR3) | (1) (2) |
| MC33PF3000A5ES | | | 5 (i.MX 6SL with LPDDR2) | (1), (2) |
| MC33PF3000A6ES | | | 6 (i.MX 6UL with LPDDR2) | |
| MC33PF3000A7ES | | | 7 (i.MX 6UL with DDR3L) | |
| MC34PF3000A0EP | | | 0 - Not programmed | |
| MC34PF3000A1EP | | | 1 (i.MX 7 with DDR3L) | |
| MC34PF3000A2EP | | | 2 (i.MX 7 with LPDDR3) | |
| MC34PF3000A3EP | -40 °C to 105 °C | | 3 (i.MX 6SX with DDR3L) | |
| MC34PF3000A4EP | (For use in Industrial | 98ASA00719D, 48 QFN 7.0 mm x 7.0 mm with exposed pad | 4 (i.MX 6SX with DDR3) | (1), (2) |
| MC34PF3000A5EP | applications) | | 5 (i.MX 6SL with LPDDR2) | |
| MC34PF3000A6EP | | | 6 (i.MX 6UL with LPDDR2) | |
| MC34PF3000A7EP | | | 7 (i.MX 6UL with DDR3L) | |
| MC34PF3000A8EP | | | 8 (i.MX 6UL with DDR3) | |

Notes

- 1. For tape and reel, add an R2 suffix to the part number.
- 2. The programming options specified in this table are reference for customer application. The part number selection should match the board power tree design. Table 42 provides details of the OTP programming for each device.

2 General description

The PF3000 is the power management integrated circuit (PMIC) designed primarily for use with NXP's i.MX 7 series of multi-media application processors. It is also capable of providing full power solution to i.MX 6SL/SX/UL processors.

2.1 Features

This section summarizes the PF3000 features.

- Input voltage range to PMIC: 2.8 V to 4.5 V, or 3.7 V to 5.5 V (3)
 - · Buck regulators
 - · Configurable three to four channels
 - SW1A/B, 2.75 A (single); 0.7 V to 1.425 V, 1.8 V, 3.3 V
 - SW1A, 1.0 A (independent); 0.7 V to 1.425 V, 1.8 V, 3.3 V
 - SW1B 1.75 A (independent); 0.7 V to 1.475 V
 - SW2, 1.25 A; 1.50 V to 1.85 V or 2.50 V to 3.30 V
 - SW3, 1.5 A; 0.90 V to 1.65 V
 - · Dynamic voltage scaling
 - · Modes: PWM, PFM, APS
 - · Programmable output voltage
 - · Programmable current limit
 - · Programmable soft start sequence
 - · Programmable PWM switching frequency
 - Boost regulator
 - SWBST, 5.0 to 5.15 V, 0.6 A, OTG support
 - · Modes: PFM and Auto
 - · OCP fault interrupt
 - LDOs
 - VCC SD, 1.8 V to 1.85 V or 2.85 V to 3.30 V, 100 mA based on SD VSEL
 - V33, 2.85 V to 3.30 V, 350 mA
 - VLDO1, 1.8 V to 3.3 V, 100 mA
 - VLDO2, 0.80 V to 1.55 V, 250 mA
 - VLDO3, 1.8 V to 3.3 V, 100 mA
 - VLDO4, 1.8 V to 3.3 V, 350 mA
- · Always ON RTC Regulator/Switch VSNVS 3.0 V, 1.0 mA
- DDR memory reference voltage, VREFDDR, 0.5 V to 0.9 V, 10 mA
- OTP (One time programmable) memory for device configuration, user-programmable start-up sequence and timing
- · Battery backed memory including coin cell charger
- I²C interface
- · User programmable standby, sleep/LPSR, and Off modes

Notes

3. 2.8 V to 4.5 V when VIN is used at input. 3.7 V to 5.5 V when VPWR is used as input.

2.2 Functional block diagram

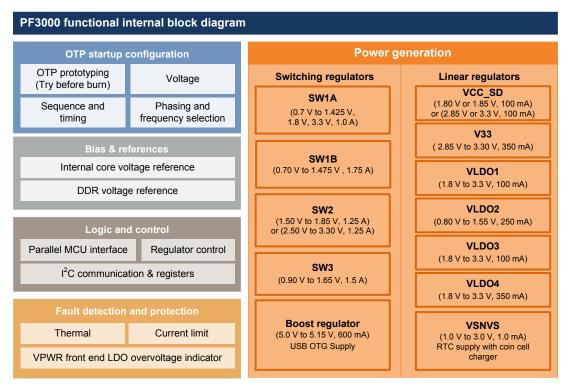


Figure 2. Functional block diagram

3 Internal block diagram

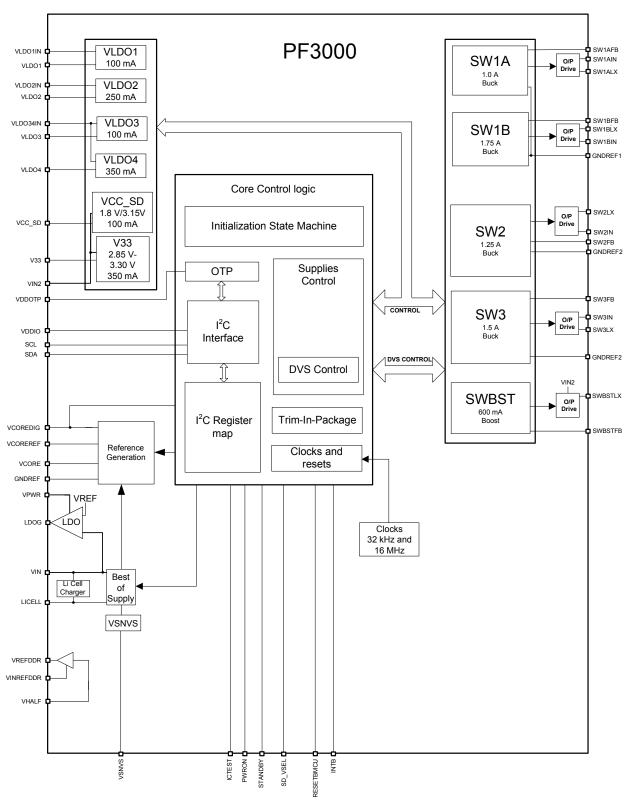


Figure 3. PF3000 simplified internal block diagram

4 Pin connections

4.1 Pinout diagram

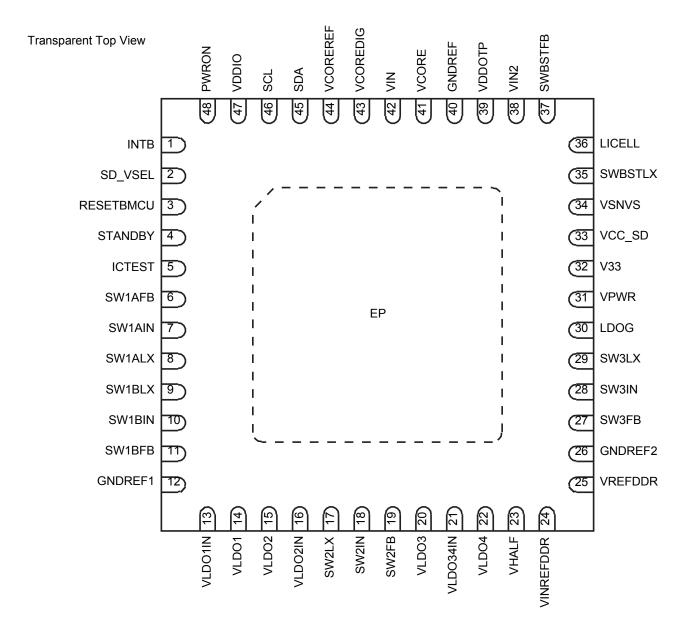


Figure 4. Pinout diagram

4.2 Pin definitions

Table 2. Pin definitions

| Pin number | Pin name | Pin function | Туре | Definition |
|------------|-----------------------|-----------------|-----------------------|--|
| 1 | INTB | 0 | Digital | Open drain interrupt signal to processor |
| 2 | SD_VSEL | I/O | Digital | Input from i.MX processor to select VCC_SD regulator voltage • SD_VSEL=0, VCC_SD = 2.85 V to 3.3 V • SD_VSEL= 1, VCC_SD = 1.8 V to 1.85 V |
| 3 | RESETBMCU | 0 | Digital | Open drain reset output to processor |
| 4 | STANDBY | I | Digital | Standby input signal from processor |
| 5 | ICTEST | 1 | Digital and Analog | Reserved pin. Connect to GND in application |
| 6 | SW1AFB ⁽⁴⁾ | I | Analog | SW1A output voltage feedback pin. Route this trace separately from the high current path and terminate at the output capacitance or near the load, if possible for best regulation |
| 7 | SW1AIN (4) | I | Analog | Input to SW1A regulator. Bypass with at least a 4.7 μ F ceramic capacitor and a 0.1 μ F decoupling capacitor as close to the pin as possible |
| 8 | SW1ALX (4) | 0 | Analog | Switcher 1A switch node connection. Connect to SW1A inductor when used in SW1A independent mode. Connect to SW1BLX and connect to SW1AB inductor when using SW1A/B as a single regulator |
| 9 | SW1BLX (4) | 0 | Analog | Switcher 1B switch node connection. Connect to SW1B inductor when used in SW1B independent mode. Connect to SW1ALX and connect to SW1AB inductor when using SW1A/B as a single regulator |
| 10 | SW1BIN (4) | I | Analog | Input to SW1B regulator. Bypass with at least a 4.7 μ F ceramic capacitor and a 0.1 μ F decoupling capacitor as close to the pin as possible |
| 11 | SW1BFB (4) | I | Analog | SW1B output voltage feedback pin. Route this trace separately from the high current path and terminate at the output capacitor or near the load, if possible for best regulatio |
| 12 | GNDREF1 | GND | GND | Ground reference for SW1A/B. Connect to GND. Keep away from high current ground return paths |
| 13 | VLDO1IN | I | Analog | VLDO1 input supply. Bypass with a 1.0 μF decoupling capacitor as close to the pin as possible |
| 14 | VLDO1 | 0 | Analog | VLDO1 regulator output. Bypass with a 2.2 μF ceramic output capacitor |
| 15 | VLDO2 | 0 | Analog | VLDO2 regulator output. Bypass with a 4.7 μF ceramic output capacitor |
| 16 | VLDO2IN | I | Analog | VLDO2 input supply. Bypass with a 1.0 μF decoupling capacitor as close to the pin as possible |
| 17 | SW2LX (4) | 0 | Analog | Switcher 2 switch node connection.Connect to SW2 inductor |
| 18 | SW2IN (4) | 1 | Analog | Input to SW2 regulator. Bypass with at least a 4.7 μ F ceramic capacitor and a 0.1 μ F decoupling capacitor as close to the pin as possible |
| 19 | SW2FB (4) | I | Analog | SW2 output voltage feedback pin. Route this trace separately from the high current path and terminate at the output capacitor or near the load, if possible for best regulation |
| 20 | VLDO3 | 0 | Analog | VLDO3 regulator output. Bypass with a 2.2 μF ceramic output capacitor |
| 21 | VLDO34IN | I | Analog | VLDO3 and VLDO4 input supply. Bypass with a 1.0 μF decoupling capacitor as close to the pin as possible |
| 22 | VLDO4 | 0 | Analog | VLDO4 regulator output. Bypass with a 2.2 µF ceramic output capacitor |
| 23 | VHALF | I | Analog | Half supply reference for VREFDDR. Bypass with 0.1 μF to ground. |
| 24 | VINREFDDR | 1 | Analog | VREFDDR regulator input. Connect a 0.1 μ F capacitor between VINREFDDR and VHALF pin. Ensure there is at least 1.0 μ F net capacitance from VINREFDDR to groun |
| 25 | VREFDDR | 0 | Analog | VREFDDR regulator output.Bypass with 1.0 μF to ground |

Table 2. Pin definitions (continued)

| 26 | GNDREF2 | GND | GND | Reference ground for SW2 and SW3 regulators. Connect to GND. Keep away from high current ground return paths |
|----|----------------------|-----|---------------------|---|
| 27 | SW3FB ⁽⁴⁾ | I | Analog | SW3 output voltage feedback pin. Route this trace separately from the high current path and terminate at the output capacitor or near the load, if possible for best regulation |
| 28 | SW3IN ⁽⁴⁾ | I | Analog | Input to SW3 regulator. Bypass with at least a 4.7 μF ceramic capacitor and a 0.1 μF decoupling capacitor as close to the pin as possible |
| 29 | SW3LX (4) | 0 | Analog | Switcher 3 switch node connection. Connect the SW3 inductor |
| 30 | LDOG | 0 | Analog | Connect to gate of front-end LDO external pass P-MOSFET. Leave floating if VPWR LDO is not used |
| 31 | VPWR | I | Analog | Input to optional front-end VPWR LDO for systems with input voltage > 4.5 V |
| 32 | V33 | 0 | Analog | V33 regulator output. Bypass with a 4.7 μF ceramic output capacitor |
| 33 | VCC_SD | 0 | Analog | Output of VCC_SD regulator. Bypass with a 2.2 µF ceramic output capacitor. |
| 34 | VSNVS | 0 | Analog | VSNVS regulator/switch output. Bypass with 0.47 μF capacitor to ground. |
| 35 | SWBSTLX (4) | I/O | Analog | SWBST switch node connection. Connect to SWBST inductor and anode of Schottky diode |
| 36 | LICELL | I/O | Analog | Coin cell supply input/output. Bypass with 0.1 µF capacitor. Connect to optional coin cell |
| 37 | SWBSTFB (4) | I | Analog | SWBST output voltage feedback pin. Route this trace separately from the high current path and terminate at the output capacitor |
| 38 | VIN2 | I | Analog | Input to VCC_SD, V33 regulators and SWBST control circuitry. Connect to VIN rail and bypass with 10 μF capacitor |
| 39 | VDDOTP | I | Digital & Analog | Supply to program OTP fuses. Connect VDDOTP to GND during normal application |
| 40 | GNDREF | GND | GND | Ground reference for IC core circuitry. Connect to ground. Keep away from high current ground return paths |
| 41 | VCORE | 0 | Analog | Internal analog core supply. Bypass with 1 µF capacitor to ground |
| 42 | VIN | I | Analog | Main IC supply. Bypass with 1.0 μ F capacitor to ground. Connect to system input supply if voltage \leq 4.5 V. Connect to drain of external PFET when VPWR LDO is used for systems with input voltage $>$ 4.5 V |
| 43 | VCOREDIG | 0 | Analog | Internal digital core supply. Bypass with 1.0 µF capacitor to ground |
| 44 | VCOREREF | 0 | Analog | Main band gap reference. Bypass with 220 nF capacitor to ground |
| 45 | SDA | I/O | Digital | I ² C data line (open drain). Pull up to VDDIO with a 4.7 kΩ resistor |
| 46 | SCL | I | Digital | I ² C clock. Pull up to VDDIO with a 4.7 kΩ resistor |
| 47 | VDDIO | I | Analog | Supply for I ² C bus. Bypass with 0.1 µF ceramic capacitor. Connect to 1.7 to 3.6 V supply. Ensure that VDDIO is always lesser than or equal to VIN |
| 48 | PWRON | I | Digital | Power ON/OFF input from processor |
| - | EP | GND | GND | Expose pad. Functions as ground return for buck and boost regulators. Tie this pad to the inner and external ground planes through vias to allow effective thermal dissipation |

Notes

4. Unused switching regulators should be connected as follows: Pins SWxLX and SWxFB should be unconnected and Pin SWxIN should be connected to VIN with a 0.1 μF bypass capacitor.

5 General product characteristics

5.1 Absolute maximum ratings

Table 3. Absolute maximum voltage ratings

All voltages are with respect to ground, unless otherwise noted. Exceeding these ratings may cause malfunction or permanent damage to the device. The detailed maximum voltage rating per pin can be found in the pin list section.

| Symbol | Description | Value | Unit | Notes |
|---|--|---------------|------|-------|
| Electrical ratings | | | | |
| VPWR, ICTEST, LDOG, SWBSTLX | - | -0.3 to 7.5 | V | |
| VIN, VIN2, VLDO1IN, SW1AIN, SW1BIN, SW2IN, SW3IN, SW1ALX, SW1BLX, SW2LX, SW3LX | - | -0.3 to 4.8 | V | |
| VDDOTP | OTP programming input supply voltage | -0.3 to 10.0 | V | (5) |
| SWBSTFB | Boost switcher feedback | -0.3 to 5.5 | V | |
| INTB, SD_VSEL, RESETBMCU, STANDBY, SW1AFB, SW1BFB, SW2FB, SW3FB, VLDO1, VLDO2IN, VLDO3, VLDO34IN, VLDO4, VHALF, VINREFDDR, VREFDDR, V33, VCC_SD, VSNVS, LICELL, VCORE, SDA, SCL, VDDIO, PWRON | - | -0.3 to 3.6 | V | |
| VLDO2 | VLDO2 linear regulator output | -0.3 to 2.5 | V | |
| VCOREDIG | Digital core supply voltage output | -0.3 to 1.65 | V | |
| VCOREREF | Bandgap reference voltage output | -0.3 to 1.5 | V | |
| V _{ESD} | ESD ratings • Human body model • Charge device model | ±2000 ±500 | V | (6) |

Notes

- 5. 10 V maximum voltage rating during OTP fuse programming. 7.5 V maximum DC voltage rated otherwise.
- 6. ESD testing is performed in accordance with the human body model (HBM) ($C_{ZAP} = 100 \text{ pF}$, $R_{ZAP} = 1500 \Omega$), and the charge device model (CDM), robotic ($C_{ZAP} = 4.0 \text{ pF}$).

5.2 Thermal Characteristics

Table 4. Thermal ratings

| Symbol | Description (rating) | Min. | Max. | Unit | Notes |
|-----------------------|--|------------|-----------|------|-------------------|
| Thermal Ratings | • | | • | | |
| T _A | Ambient operating temperature range • Industrial version • Consumer version | -40 -40 | 105 85 | °C | |
| T _J | Operating junction temperature range | -40 | 125 | °C | (7) |
| T _{ST} | Storage temperature range | -65 | 150 | °C | 1 |
| T _{PPRT} | Peak package reflow temperature | _ | (9) | °C | (8) (9) |
| FN48 thermal re | esistance and package dissipation ratings | <u>,</u> | | | |
| $R_{	hetaJA}$ | Junction to ambient, natural convection • Four layer board (2s2p) • Eight layer board (2s6p) | | 24 15 | °C/W | (10) (11) (12) |
| $R_{\theta JB}$ | Junction to board | _ | 11 | °C/W | (13) |
| $R_{\Theta JCBOTTOM}$ | Junction to case bottom | - | 1.4 | °C/W | (14) |
| ΨJT | Junction to package top • Natural convection | - | 1.3 | °C/W | (15) |

Notes

- 7. Do not operate beyond 125 °C for extended periods of time. Operation above 150 °C may cause permanent damage to the IC. See Thermal Protection Thresholds for thermal protection features.
- 8. Pin soldering temperature limit is for 10 seconds maximum duration. Not designed for immersion soldering. Exceeding these limits may cause a malfunction or permanent damage to the device.
- 9. NXP's package reflow capability meets Pb-free requirements for JEDEC standard J-STD-020C. For peak package reflow temperature and moisture sensitivity levels (MSL), go to www.nxp.com, search by part number (remove prefixes/suffixes) and enter the core ID to view all orderable parts, and review parametrics.
- 10. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
- 11. The Board uses the JEDEC specifications for thermal testing (and simulation) JESD51-7 and JESD51-5.
- 12. Per JEDEC JESD51-6 with the board horizontal.
- 13. Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
- 14. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
- 15. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters (Ψ) are not available, the thermal characterization parameter is written as Psi-JT.

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5.3 Current consumption

The current consumption of the individual blocks is described in detail in the following table.

Table 5. Current consumption summary

 T_A = -40 °C to 105 °C, V_{PWR} = 0 V (External pass FET is not populated), V_{IN} = 3.6 V, V_{DDIO} = 1.7 V to 3.6 V, L_{ICELL} = 1.8 V to 3.3 V, V_{SNVS} = 3.0 V, typical external component values, unless otherwise noted. Typical values are characterized at VIN = 3.6 V, V_{PWR} = 0 V, V_{DDIO} = 3.3 V, L_{ICELL} = 3.0 V, V_{SNVS} = 3.0 V and 25 °C, unless otherwise noted.

| Mode | PF3000 conditions | System conditions | Тур. | Max. | Unit | Notes |
|------------|---|--|--|----------|------|-----------|
| Coin cell | VSNVS from LICELL, All other blocks off, $V_{IN} = 0.0 \text{ V}$ | No load on VSNVS | 4.0 | 7.0 | μΑ | (16) (17) |
| Off | VSNVS from VIN or LICELL Wake-up from PWRON active 32 kHz RC on All other blocks off VIN ≥ UVDET | No load on VSNVS, PMIC able to wake-up | 16 | 25 | μА | (16) (17) |
| Sleep LPSR | VSNVS from VIN Wake-up from PWRON active Trimmed reference active SW3 PFM. All other regulators off. Trimmed 16 MHz RC off 32 kHz RC on VREFDDR disabled | No load on any of the regulators. | 130 ⁽¹⁶⁾ 200 ⁽¹⁹⁾ | 220 (16) | μА | (18) |
| | LDO1 & LDO3 activated in addition to SW3 | No load on any of the regulators. | 170 ⁽¹⁶⁾ 260 ⁽¹⁹⁾ | 248 (16) | μΑ | (18) |
| Standby | VSNVS from either VIN or LICELL SW1A in PFM SW1B in PFM SW2 in PFM SW3 in PFM SWBST off Trimmed 16 MHz RC enabled Trimmed reference active VLDO1-4 enabled V33 enabled VCC_SD enabled VREFDDR enabled | No load on any of the regulators. | 297 | 450 | μΑ | (18) |
| ON | VSNVS from VIN SW1A in APS SW1B in APS SW2 in APS SW3 in APS SWBST off Trimmed 16 MHz RC enabled Trimmed reference active VLDO1-4 enabled V33 enabled VCC_SD enabled VREFDDR enabled | No load on any of the regulators. | 1.2 | | mA | |

Notes

- 16. At 25 °C only.
- 17. When V_{IN} is below the UVDET threshold, in the range of 1.8 V \leq V_{IN} < 2.65 V, the quiescent current increases by 50 μ A, typically.
- 18. For PFM operation, headroom should be 300 mV or greater.
- 19. At 105 °C only.

PF3000

12 NXP Semiconductors

5.4 Electrical characteristics

Table 6. Electrical characteristics - front-end input LDO

All parameters are specified at T_A = -40 °C to 105 °C, V_{PWR} = 5.0 V, V_{IN} = 4.4 V, I_{VIN} = 300 mA, typical external component values, unless otherwise noted. Typical values are characterized at V_{PWR} = 5.0 V, V_{IN} = 4.4 V, I_{VIN} = 300 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes |
|--------------------------|--|------------|--------|------------|------|-------|
| Front end input I | LDO (VPWR LDO) | | • | • | | • |
| V_{PWR} | Operating input voltage In regulation In dropout operation | 4.6 3.7 | _ _ | 5.5 4.6 | V | (20) |
| V _{IN} | On mode output voltage, 4.6 V < V _{PWR} < 5.5 V _, 0.0 mA < I _{VIN} < 3000 mA | 4.3 | 4.4 | 4.55 | ٧ | |
| I _{VIN} | Operating load current at VIN, 3.7 V < V _{PWR} < 5.5 V | 0.0 | - | 3.0 | Α | |
| I _{LDOGQ} | ON mode quiescent current, no load, | - | 5.0 | 10 | mA | |
| V _{IN} | Low-power mode output voltage, 4.6 V < $\rm V_{PWR}$ < 5.5 V 0.0 mA < $\rm I_{VIN}$ < 1.0 mA | 3.7 | | 4.5 | ٧ | |
| V _{IN_OFF} | Off mode output voltage, (CL = 100 μ F) 4.6 V < V _{PWR} < 5.5 V, 0.0 mA < I _{VIN} < 35 μ A | 3.2 | | 4.8 | ٧ | |
| I _{LDOQLP} | Low-power mode quiescent current, no load (Standby/Sleep/LPSR states) | - | 150 | 300 | μА | |
| V _{PWRUV} | VPWR undervoltage threshold (upon undervoltage condition the external pass FET is turned off) | 3.1 | _ | 3.7 | V | |
| V _{PWROV} | VPWR overvoltage threshold (upon overvoltage condition interrupt is asserted at INTB) | 5.5 | _ | 6.5 | V | |
| I _{VINUVILIMIT} | VPWR LDO current limit under VIN short-circuit (V _{IN} < UVDET) | - | - | 300 | mA | |
| I _{VINLEAKAGE} | Reverse leakage current from VIN to VPWR, No external pass FET, VPWR is grounded, device is in OFF state | _ | _ | 1.0 | μΑ | |
| I _{VPWROFF} | VPWR LDO Off mode quiescent current | _ | - | 75 | μΑ | (21) |

Notes

^{20.} While the front end LDO can handle spikes up to 7.5 V at VPWR for as long as 200 μs, the circuit is not expected to be continuously operated when VPWR is above 5.5 V.

^{21.} This specification gives the leakage current in the VPWR LDO block. Total OFF mode current includes the quiescent current from the other blocks as specified in Table 5.

Table 7. Static electrical characteristics – SW1

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = V_{SW1xIN} = 3.6 V, V_{SW1x} = 1.2 V, I_{SW1x} = 100 mA, typical external component values, f_{SW1x} = 2.0 MHz, unless otherwise noted. Typical values are characterized at V_{IN} = V_{SW1xIN} = 3.6 V, V_{SW1x} = 1.2 V, I_{SW1x} = 100 mA, and 25 °C, unless otherwise noted.

| V _{SW1AIN} V _{SW1BIN} V _{SW1AB} | Operating input voltage Nominal output voltage Output voltage accuracy PWM, APS, $2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}$, $0 < \text{I}_{\text{SW1AB}} < 2.75 \text{ A}$ $0.7 \text{ V} \le \text{V}_{\text{SW1AB}} \le 1.2 \text{ V}$ PFM, APS, $2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}$, $0 < \text{I}_{\text{SW1AB}} < 2.75 \text{ A}$ $1.225 \text{ V} < \text{V}_{\text{SW1AB}} < 1.425 \text{ V}$ PFM, steady state, $2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}$, $0 < \text{I}_{\text{SW1AB}} < 1.50 \text{ mA}$ $1.8 \text{ V} \le \text{V}_{\text{SW1AB}} \le 1.425 \text{ V}$ PWM, APS, $2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}$, $0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA}$ $1.8 \text{ V} \le \text{V}_{\text{SW1AB}} \le 3.3 \text{ V}$ PFM, steady state, $2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}$, $0 < \text{I}_{\text{SW1AB}} < 2.75 \text{ A}$ $1.8 \text{ V} < \text{V}_{\text{SW1AB}} < 3.3 \text{ V}$ | 2.8 - -25 -25 -45 -6.0 | Table 53 | 4.5 - 25 35 45 | V V WV mV | (22), (23) |
|--|--|---------------------------------------|------------|----------------------------|---------------|------------|
| V _{SW1AB} | Nominal output voltage $ \begin{array}{l} \text{Output voltage accuracy} \\ \bullet \text{ PWM, APS, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 2.75 \text{ A} \\ 0.7 \text{ V} \leq \text{V}_{\text{SW1AB}} \leq 1.2 \text{ V} \\ \bullet \text{ PFM, APS, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 2.75 \text{A} \\ 1.225 \text{ V} < \text{V}_{\text{SW1AB}} < 1.425 \text{ V} \\ \bullet \text{ PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ 1.8 \text{ V} \leq \text{V}_{\text{SW1AB}} \leq 1.425 \text{ V} \\ \bullet \text{ PWM, APS, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 2.75 \text{A} \\ 1.8 \text{ V} < \text{V}_{\text{SW1AB}} < 3.3 \text{ V} \\ \bullet \text{ PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{ PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{ PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{ PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{ PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{ PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{ PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{ PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{ PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{ PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{ PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{ PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{ PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{ PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 1.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < $ | -25 -25 -45 -6.0 | Table 53 | 25 35 | V mV mV | (22), (23) |
| | Output voltage accuracy $ \begin{array}{l} \bullet \text{PWM, APS, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 2.75 \text{ A} \\ 0.7 \text{ V} \leq \text{V}_{\text{SW1AB}} \leq 1.2 \text{ V} \\ \bullet \text{PFM, APS, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 2.75 \text{A} \\ 1.225 \text{ V} < \text{V}_{\text{SW1AB}} < 1.425 \text{ V} \\ \bullet \text{PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ 1.8 \text{ V} \leq \text{V}_{\text{SW1AB}} \leq 1.425 \text{ V} \\ \bullet \text{PWM, APS, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 2.75 \text{A} \\ 1.8 \text{ V} < \text{V}_{\text{SW1AB}} < 3.3 \text{ V} \\ \bullet \text{PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, 0 < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \\ \bullet \text{PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 1.5 \text{ V}$ | -25 -45 -6.0 | Table 53 | 25 35 | mV mV | |
| | PWM, APS, 2.8 V < V_{SW1xIN} < 4.5 V, 0 < I_{SW1AB} < 2.75 A 0.7 V ≤ V_{SW1AB} ≤ 1.2 V PFM, APS, 2.8 V < V_{SW1xIN} < 4.5 V, 0 < I_{SW1AB} < 2.75A 1.225 V < V_{SW1AB} < 1.425 V PFM, steady state, 2.8 V < V_{SW1xIN} < 4.5 V, 0 < I_{SW1AB} < 150 mA 1.8 V ≤ V_{SW1AB} ≤ 1.425 V PWM, APS, 2.8 V < V_{SW1xIN} < 4.5 V, 0 < I_{SW1AB} < 2.75A 1.8 V < V_{SW1AB} < 3.3 V PFM, steady state, 2.8 V < V_{SW1xIN} < 4.5 V, 0 < I_{SW1AB} < 150 mA | -25 -45 -6.0 | - | 35 | mV | |
| V _{SW1ABACC} | PFM, steady state, 2.8 V < V_{SW1xIN} < 4.5 V, 0 < I_{SW1AB} < 150 mA 1.8 V ≤ V_{SW1AB} ≤ 1.425 V PWM, APS, 2.8 V < V_{SW1xIN} < 4.5 V, 0 < I_{SW1AB} < 2.75A 1.8 V < V_{SW1AB} < 3.3 V PFM, steady state, 2.8 V < V_{SW1xIN} < 4.5 V, 0 < I_{SW1AB} < 150 mA | -6.0 | - | | | |
| SWIADAGG | $\begin{split} &1.8 \text{ V} \leq \text{V}_{\text{SW1AB}} \leq 1.425 \text{ V} \\ \bullet & \text{PWM, APS, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, \text{ 0} < \text{I}_{\text{SW1AB}} < 2.75\text{A} \\ &1.8 \text{ V} < \text{V}_{\text{SW1AB}} < 3.3 \text{ V} \\ \bullet & \text{PFM, steady state, } 2.8 \text{ V} < \text{V}_{\text{SW1xIN}} < 4.5 \text{ V}, \text{ 0} < \text{I}_{\text{SW1AB}} < 150 \text{ mA} \end{split}$ | -6.0 | | | mV | |
| | 1.8 V < V _{SW1AB} < 3.3 V • PFM, steady state, 2.8 V < V _{SW1xIN} < 4.5 V, 0 < I _{SW1AB} < 150 mA | 0.0 | | 6.0 | % | |
| | 1.0 V = V SW IAB = 0.0 V | -6.0 | | 6.0 | % | |
| I _{SW1AB} | Rated output load current, • 2.8 V \leq V _{SW1xIN} \leq 4.5 V, 0.7 V $<$ V _{SW1AB} $<$ 1.425 V, 1.8V, 3.3V | 2750 | _ | - | mA | |
| I _{SW1ABQ} | Quiescent current • PFM mode • APS mode | 1 1 | 22 300 | - - | μА | |
| I _{SW1ABLIM} | Current limiter peak current detection , current through inductor • SW1xILIM = 0 • SW1xILIM = 1 | 3.5 2.6 | 5.5 4.0 | 7.5 5.4 | А | |
| ΔV_{SW1AB} | Output ripple | - | 5.0 | - | mV | |
| R _{SW1ABDIS} | Discharge resistance | _ | 600 | _ | Ω | |
| vitch mode supp | oly SW1A (independent) | | | | | |
| V _{SW1AIN} | Operating input voltage | 2.8 | - | 4.5 | V | (22), (23) |
| V _{SW1A} | Nominal output voltage | - | Table 53 | _ | V | |
| | Output voltage accuracy • PWM, APS, 2.8 V < V_{SW1AIN} < 4.5 V, 0 < I_{SW1A} < 1.0 A 0.7 V $\leq V_{SW1A} \leq$ 1.2 V | -25 | | 25 | mV | |
| | • APS, $3.0 \text{ V} \le \text{V}_{\text{SW1AIN}} \le 3.6 \text{ V}$, $0.01 \text{ A} < \text{I}_{\text{SW1A}} < 0.75 \text{ A}$ $\text{V}_{\text{SW1A}} = 1.225 \text{ V}$, $\text{T}_{\text{A}} = 0 \text{ °C}$ to 85 °C | -25 | | 25 | mV | |
| V _{SW1AACC} | • PWM, APS, 2.8 V < V_{SW1AIN} < 4.5 V, 0 < I_{SW1A} < 1.0 A 1.225 V < V_{SW1A} \leq 1.425 V | -25 | _ | 35 | mV | |
| | PFM, steady state, 2.8 V < V_{SW1AIN} < 4.5 V, 0 < I_{SW1A} < 50 mA 0.7 V ≤ V_{SW1A} ≤ 1.425V | -45 | | 45 | mV | |
| | • PWM, APS, 2.8 V < V_{SW1AIN} < 4.5 V, 0 < I_{SW1A} < 1.0 A 1.8 V $\leq V_{SW1A} \leq$ 3.3 V | -6.0 | | 6.0 | % | |
| | • PFM, steady state, 2.8 V < $\rm V_{SW1AIN}$ < 4.5 V, 0 < $\rm I_{SW1A}$ < 50 mA 1.8 V $\rm \le V_{SW1A} \le$ 3.3 V | -6.0 | | 6.0 | % | |
| I _{SW1A} | Rated output load current 2.8 V < V _{SW1AIN} < 4.5 V, 0.7 V < V _{SW1A} < 1.425 V, 1.8V, 3.3V | 1000 | _ | _ | mA | |
| vitch mode supp | oly SW1a (independent) (Continued) | | | | | |
| I _{SW1AQ} | Quiescent current PFM mode APS mode | - | 50 250 | - | μΑ | |

Table 7. Static electrical characteristics - SW1 (continued)

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = V_{SW1xIN} = 3.6 V, V_{SW1x} = 1.2 V, I_{SW1x} = 100 mA, typical external component values, f_{SW1x} = 2.0 MHz, unless otherwise noted. Typical values are characterized at V_{IN} = V_{SW1xIN} = 3.6 V, V_{SW1x} = 1.2 V, I_{SW1x} = 100 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes |
|----------------------|---|------|------|------|------|-------|
| I _{SW1ALIM} | Current limiter peak current detection, current through inductor • SW1AILIM = 0 | 1.78 | 2.75 | 3.7 | А | |
| | • SW1AILIM = 1 | 1.3 | 2.0 | 2.7 | | |
| ΔV_{SW1A} | Output Ripple | _ | 5.0 | _ | mV | |
| R _{ONSW1AP} | SW1A P-MOSFET R_{DSON} , at $V_{SW1AIN} = 3.3 \text{ V}$ | _ | 265 | 295 | mΩ | |
| R _{ONSW1AN} | SW1A N-MOSFET R _{DSON} , at V_{SW1AIN} = 3.3 V | _ | 300 | 370 | mΩ | |
| I _{SW1APQ} | SW1A P-MOSFET leakage current, V _{SW1AIN} = 4.5 V | _ | _ | 10.5 | μA | |
| I _{SW1ANQ} | SW1A N-MOSFET leakage current, V _{SW1AIN} = 4.5 V | _ | _ | 3.5 | μA | |
| R _{SW1ADIS} | Discharge resistance | _ | 600 | _ | Ω | |

Switch mode supply SW1B (independent)

| V _{SW1BIN} | Operating input voltage | 2.8 | _ | 4.5 | V | (24), (25) |
|----------------------|---|--------------|--------------|----------------|----|------------|
| V _{SW1B} | Nominal output voltage | - | Table 53 | - | V | |
| V _{SW1BACC} | Output voltage accuracy • PWM, APS, 2.8 V < V _{SW1BIN} < 4.5 V, 0 < I _{SW1B} < 1.75 A 0.7 V < V _{SW1B} < 1.2 V • PWM, APS, 2.8 V < V _{SW1BIN} < 4.5 V, 0 < I _{SW1B} < 1.75 A 1.225 V < V _{SW1B} < 1.475 V | -25 -25 | - | 25 35 | mV | |
| | • PFM, steady state 2.8 V < $\rm V_{SW1BIN}$ < 4.5 V, 0 < $\rm I_{SW1B}$ < 50 mA 0.7 V < $\rm V_{SW1B}$ < 1.475 V | -45 | | 45 | | |
| I _{SW1B} | Rated output load current 2.8 V < V _{SW1BIN} < 4.5 V, 0.7 V < V _{SW1B} < 1.475 V | 1750 | - | - | mA | |
| I _{SW1BQ} | Quiescent current PFM mode APS mode | - - | 50 150 | - - | μА | |
| I _{SW1BLIM} | Current limiter peak current detection, current through inductor • SW1BILIM = 0 • SW1BILIM = 1 | 2.4 1.725 | 3.50 2.65 | 4.725 3.575 | А | |
| ΔV_{SW1B} | Output ripple | - | 5.0 | - | mV | |
| R _{ONSW1BP} | SW1B P-MOSFET R _{DSON} , at V _{SW1BIN} = 3.3 V | - | 195 | 225 | mΩ | |
| R _{ONSW1BN} | SW1B N-MOSFET R _{DSON} , at V _{SW1BIN} = 3.3 V | - | 228 | 295 | mΩ | |
| I _{SW1BPQ} | SW1B P-MOSFET leakage current, V _{SW1BIN} = 4.5 V | - | - | 12 | μA | |
| I _{SW1BNQ} | SW1B N-MOSFET leakage current, V _{SW1BIN} = 4.5 V | _ | _ | 4.0 | μA | |
| R _{SW1BDIS} | Discharge resistance during OFF mode | _ | 600 | - | Ω | |

Notes

- 22. The maximum operating input voltage is 4.55 V when VPWR LDO is used.
- 23. Minimum operating voltage is 2.8 V with a valid LICELL voltage (1.8 V to 3.3 V). Minimum operating voltage is 3.1 V when no voltage is applied at the LICELL pin. If operation down to 2.8 V is required for systems without a coin cell, connect the LICELL pin to any system voltage between 1.8 V and 3.3 V. This voltage can be an output from any PF3000 regulator, or external system supply.
- 24. The maximum operating input voltage is 4.55 V when VPWR LDO is used.
- 25. Minimum operating voltage is 2.8 V with a valid LICELL voltage (1.8 V to 3.3 V). Minimum operating voltage is 3.1 V when no voltage is applied at the LICELL pin. If operation down to 2.8 V is required for systems without a coin cell, connect the LICELL pin to any system voltage between 1.8 V and 3.3 V. This voltage can be an output from any PF3000 regulator, or external system supply.

Table 8. Dynamic electrical characteristics - SW1

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = V_{SW1xIN} = 3.6 V, V_{SW1x} = 1.2 V, I_{SW1x} = 100 mA, typical external component values, f_{SW1x} = 2.0 MHz, unless otherwise noted. Typical values are characterized at V_{IN} = V_{SW1xIN} = 3.6 V, V_{SW1x} = 1.2 V, I_{SW1x} = 100 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes |
|-----------------------|---|------|------|------|------|-------|
| Switch mode sup | ply SW1A/B (single phase) | | | | | |
| V _{SW1ABOSH} | Start-up overshoot, $I_{SW1AB}=0$ mA, DVS clk = 25 mV/4 μ s, $V_{IN}=V_{SW1xIN}=4.5$ V, $V_{SW1AB}=1.425$ V | - | _ | 66 | mV | |
| t _{ONSW1AB} | Turn-on time, enable to 90% of end value, I_{SW1AB} = 0 mA, DVS clk = 25 mV/4 μ s, V_{IN} = V_{SW1xIN} = 4.5 V, V_{SW1AB} = 1.425 V | _ | _ | 500 | μs | |
| Switch mode sup | ply SW1A (independent) | | | | | |
| V _{SW1AOSH} | Start-up overshoot, ISW1A = 0 mA, DVS clk = 25 mV/4.0 μ s, V $_{IN}$ = V $_{SW1AIN}$ = 4.5 V, V $_{SW1A}$ = 1.425 V | - | _ | 66 | mV | |
| t _{ONSW1A} | Turn-on time, enable to 90% of end value, I_{SW1A} = 0 mA, DVS clk = 25 mV/4.0 μ s, V_{IN} = V_{SW1AIN} = 4.5 V, V_{SW1A} = 1.425 V | _ | _ | 500 | μs | |
| Switch mode sup | ply SW1B (independent) | | | | | |
| V _{SW1BOSH} | Start-up overshoot, I_{SW1B} = 0 mA, DVS clk = 25 mV/4.0 μ s, V_{IN} = V_{SW1BIN} = 4.5 V, V_{SW1B} = 1.475 V | - | - | 66 | mV | |
| t _{ONSW1B} | Turn-on time, enable to 90% of end value, I_{SW1B} = 0 mA, DVS clk = 25 mV/4 μ s, V_{IN} = V_{SW1BIN} = 4.5 V, V_{SW1B} = 1.475 V | - | _ | 500 | μs | |

Table 9. Static electrical characteristics - SW2

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = V_{SW2IN} = 3.6 V, V_{SW2} = 3.15 V, I_{SW2} = 100 mA, typical external component values, f_{SW2} = 2.0 MHz, unless otherwise noted. Typical values are characterized at V_{IN} = V_{SW2IN} = 3.6 V, V_{SW2} = 3.15 V, I_{SW2} = 100 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes |
|---------------------|--|-------------------------|------------------|------------------------------|------|------------|
| witch mode su | pply SW2 | | l | L | l | 1 |
| V _{SW2IN} | Operating input voltage | 2.8 | _ | 4.5 | V | (26), (27) |
| V_{SW2} | Nominal output voltage | _ | Table 55 | _ | V | |
| V _{SW2ACC} | $ \begin{array}{l} \text{Output voltage accuracy} \\ \bullet \text{ PWM, APS, } 2.8 \text{ V} \leq \text{V}_{\text{SW2IN}} \leq 4.5 \text{ V, } 0 \leq \text{I}_{\text{SW2}} \leq 1.25 \text{ A} \\ \bullet 1.50 \text{ V} \leq \text{V}_{\text{SW2}} \leq 1.85 \text{ V} \\ \bullet 2.5 \text{ V} \leq \text{V}_{\text{SW2}} \leq 3.3 \text{ V} \\ \bullet \text{PFM, } 2.8 \text{ V} \leq \text{V}_{\text{SW2IN}} \leq 4.5 \text{ V, } 0 \leq \text{I}_{\text{SW2}} \leq 50 \text{ mA} \\ \bullet 1.50 \text{ V} \leq \text{V}_{\text{SW2}} \leq 1.85 \text{ V} \\ \bullet 2.5 \text{ V} \leq \text{V}_{\text{SW2}} \leq 3.3 \text{ V} \end{array} $ | -3.0% -6.0% -6.0% | - - - | 3.0% 6.0% 6.0% 6.0% | % | |
| I _{SW2} | Rated output load current, 2.8 V < V_{SW2IN} < 4.5 V, 1.50 V < V_{SW2} < 1.85 V, 2.5 V < V_{SW2} < 3.3 V | 1250 | _ | _ | mA | (28) |
| I _{SW2Q} | Quiescent current • PFM mode • APS mode (low output voltage settings) • APS mode (high output voltage settings, SW2_HI=1) | - - - | 23 145 305 | - - - | μА | |

Notes

- 26. The maximum operating input voltage is 4.55 V when VPWR LDO is used.
- 27. Minimum operating voltage is 2.8 V with a valid LICELL voltage (1.8 V to 3.3 V). Minimum operating voltage is 3.1 V when no voltage is applied at the LICELL pin. If operation down to 2.8 V is required for systems without a coin cell, connect the LICELL pin to any system voltage between 1.8 V and 3.3 V. This voltage can be an output from any PF3000 regulator, or external system supply.
- 28. The higher output voltages available depend on the voltage drop in the conduction path as given by the following equation: $(V_{SW2IN} V_{SW2}) = I_{SW2}^*$ (DCR of Inductor +R_{ONSW2P} + PCB trace resistance).

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Table 9. Static electrical characteristics - SW2 (continued)

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = V_{SW2IN} = 3.6 V, V_{SW2} = 3.15 V, I_{SW2} = 100 mA, typical external component values, f_{SW2} = 2.0 MHz, unless otherwise noted. Typical values are characterized at V_{IN} = V_{SW2IN} = 3.6 V, V_{SW2} = 3.15 V, I_{SW2} = 100 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes | | | | | |
|---------------------|--|----------------|------------|----------------|------|-------|--|--|--|--|--|
| Switch mode sup | Switch mode supply SW2 (continued) | | | | | | | | | | |
| I _{SW2LIM} | Current limiter peak current detection, current through inductor • SW2ILIM = 0 • SW2ILIM = 1 | 1.625 1.235 | 2.5 1.9 | 3.375 2.565 | А | | | | | | |
| ΔV _{SW2} | Output ripple | - | 5.0 | - | mV | | | | | | |
| R _{ONSW2P} | SW2 P-MOSFET R _{DSON} at V _{IN} = V _{SW2IN} = 3.3 V | - | 215 | 245 | mΩ | | | | | | |
| R _{ONSW2N} | SW2 N-MOSFET R _{DSON} at V _{SW2IN} = V _{SW2IN} = 3.3 V | _ | 258 | 326 | mΩ | | | | | | |
| I _{SW2PQ} | SW2 P-MOSFET leakage current, V _{IN} = V _{SW2IN} = 4.5 V | _ | - | 10.5 | μΑ | | | | | | |
| I _{SW2NQ} | SW2 N-MOSFET leakage current, V _{IN} = V _{SW2IN} = 4.5 V | - | - | 3.0 | μΑ | | | | | | |
| R _{SW2DIS} | Discharge resistance during OFF mode | - | 600 | _ | Ω | | | | | | |

Table 10. Dynamic electrical characteristics - SW2

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = V_{SW2IN} = 3.6 V, V_{SW2} = 3.15 V, ISW2 = 100 mA, typical external component values, f_{SW2} = 2.0 MHz, unless otherwise noted. Typical values are characterized at V_{IN} = V_{SW2IN} = 3.6 V, V_{SW2} = 3.15 V, V_{SW2} = 100 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes | | |
|------------------------|--|------|------|------|------|-------|--|--|
| Switch mode supply SW2 | | | | | | | | |
| V _{SW2OSH} | Start-up overshoot, I_{SW2} = 0.0 mA, DVS clk = 25 mV/4 μ s, V_{IN} = V_{SW2IN} = 4.5 V | - | - | 66 | mV | | | |
| t _{ONSW2} | Turn-on time, enable to 90% of end value, I_{SW2} = 0.0 mA, DVS clk = 25 mV/4 $\mu s,V_{IN}$ = V_{SW2IN} = 4.5 V | _ | _ | 500 | μs | | | |

Table 11. Static electrical characteristics - SW3

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = V_{SW3IN} = 3.6 V, V_{SW3} = 1.5 V, I_{SW3} = 100 mA, typical external component values, f_{SW3} = 2.0 MHz. Typical values are characterized at V_{IN} = V_{SW3IN} = 3.6 V, V_{SW3} = 1.5 V, I_{SW3} = 100 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes | | | | |
|--------------------|---|----------------|----------|--------------|------|------------|--|--|--|--|
| Switch mode sup | witch mode supply SW3 | | | | | | | | | |
| V _{SW3IN} | Operating input voltage | 2.8 | _ | 4.5 | V | (29), (30) | | | | |
| V _{SW3} | Nominal output voltage | _ | Table 57 | - | V | | | | | |
| Vsw3acc | Output voltage accuracy • PWM, APS, 2.8 V < V_{SW3IN} < 4.5 V, 0 < I_{SW3} < 1.5 A, 0.9 V < V_{SW3} < 1.65 V • PFM, steady state (2.8 V < V_{SW3IN} < 4.5 V, 0 < I_{SW3} < 50 mA), 0.9 V < V_{SW3} < 1.65 V | -3.0% -6.0% | - | 3.0% 6.0% | % | | | | | |
| I _{SW3} | Rated output load current, 2.8 V < $\rm V_{SW3IN}$ < 4.5 V, 0.9 V < $\rm V_{SW3}$ < 1.65 V, PWM, APS mode | 1500 | - | _ | mA | (31) | | | | |

Notes

- 29. The maximum operating input voltage is 4.55 V when VPWR LDO is used.
- 30. Minimum operating voltage is 2.8 V with a valid LICELL voltage (1.8 V to 3.3 V). Minimum operating voltage is 3.1 V when no voltage is applied at the LICELL pin. If operation down to 2.8 V is required for systems without a coin cell, connect the LICELL pin to any system voltage between 1.8 V and 3.3 V. This voltage can be an output from any PF3000 regulator, or external system supply.
- 31. The higher output voltages available depend on the voltage drop in the conduction path as given by the following equation: (V_{SW3IN} V_{SW3}) = I_{SW3}* (DCR of Inductor +R_{ONSW3P} + PCB trace resistance).

Table 11. Static electrical characteristics - SW3 (continued)

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = V_{SW3IN} = 3.6 V, V_{SW3} = 1.5 V, I_{SW3} = 100 mA, typical external component values, f_{SW3} = 2.0 MHz. Typical values are characterized at V_{IN} = V_{SW3IN} = 3.6 V, V_{SW3} = 1.5 V, I_{SW3} = 100 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes | | | | | |
|---------------------|--|--------------|-------------|--------------|------|-------|--|--|--|--|--|
| Switch mode sup | Switch mode supply SW3 (continued) | | | | | | | | | | |
| I _{SW3Q} | Quiescent current • PFM mode • APS mode | - - | 50 150 | - - | μА | | | | | | |
| I _{SW3LIM} | Current limiter peak current detection, current through inductor • SW3ILIM = 0 • SW3ILIM = 1 | 1.95 1.45 | 3.0 2.25 | 4.05 3.05 | А | | | | | | |
| ΔV _{SW3} | Output ripple | - | 5.0 | _ | mV | | | | | | |
| R _{ONSW3P} | SW3 P-MOSFET R _{DSON} at V _{IN} = V _{SW3IN} = 3.3 V | _ | 205 | 235 | mΩ | | | | | | |
| R _{ONSW3N} | SW3 N-MOSFET R _{DSON} at V _{IN} = V _{SW3IN} = 3.3 V | - | 250 | 315 | mΩ | | | | | | |
| I _{SW3PQ} | SW3 P-MOSFET leakage current, V _{IN} = V _{SW3IN} = 4.5 V | - | - | 12 | μΑ | | | | | | |
| I _{SW3NQ} | SW3 N-MOSFET leakage current, V _{IN} = V _{SW3IN} = 4.5 V | _ | - | 4.0 | μA | | | | | | |
| R _{SW3DIS} | Discharge resistance during Off mode | _ | 600 | _ | Ω | | | | | | |

Table 12. Dynamic electrical characteristics - SW3

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = V_{SW3IN} = 3.6 V, V_{SW3} = 1.5 V, I_{SW3} = 100 mA, typical external component values, f_{SW3} = 2.0 MHz. Typical values are characterized at V_{IN} = V_{SW3IN} = 3.6 V, V_{SW3} = 1.5 V, I_{SW3} = 100 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes |
|---------------------|--|------|------|------|------|-------|
| V _{SW3OSH} | Start-up overshoot, I_{SW3} = 0.0 mA, DVS clk = 25 mV/4 μ s, V_{IN} = V_{SW3IN} = 4.5 V | - | - | 66 | mV | |
| t _{ONSW3} | Turn-on time, enable to 90% of end value, I_{SW3} = 0 mA, DVS clk = 25 mV/4 $\mu s, V_{IN}$ = V_{SW3IN} = 4.5 V | - | - | 500 | μs | |

Table 13. Static electrical characteristics - SWBST

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = $V_{SWBSTIN}$ = 3.6 V, V_{SWBST} = 5.0 V, I_{SWBST} = 100 mA, typical external component values, f_{SWBST} = 2.0 MHz, otherwise noted. Typical values are characterized at V_{IN} = $V_{SWBSTIN}$ = 3.6 V, V_{SWBST} = 5.0 V, I_{SWBST} = 100 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameters | Min. | Тур. | Max. | Unit | Notes |
|-----------------------|---|------------|----------|----------|------|------------|
| Switch mode sup | ply SWBST | | | | | |
| V _{SWBSTIN} | Input voltage range | 2.8 | _ | 4.5 | V | (32), (33) |
| V_{SWBST} | Nominal output voltage | - | Table 59 | _ | V | |
| I _{SWBST} | Continuous load current • 2.8 $V \le V_{IN} \le 3.0 V$ • 3.0 $V \le V_{IN} \le 4.5 V$ | 500 600 | - - | <u>-</u> | mA | |
| V _{SWBSTACC} | Output voltage accuracy, 2.8 V \leq V $_{\text{IN}} \leq$ 4.5 V, 0 $<$ I $_{\text{SWBSTMAX}}$ | -4.0 | _ | 3.0 | % | |
| I _{SWBSTQ} | Quiescent current (auto mode) | _ | 222 | 289 | μΑ | |

Notes

- 32. The maximum operating input voltage is 4.55 V when VPWR LDO is used.
- 33. Minimum operating voltage is 2.8 V with a valid LICELL voltage (1.8 V to 3.3 V). Minimum operating voltage is 3.1 V when no voltage is applied at the LICELL pin. If operation down to 2.8 V is required for systems without a coin cell, connect the LICELL pin to any system voltage between 1.8 V and 3.3 V. This voltage can be an output from any PF3000 regulator, or external system supply.

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Table 13. Static electrical characteristics - SWBST (continued)

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = $V_{SWBSTIN}$ = 3.6 V, V_{SWBST} = 5.0 V, I_{SWBST} = 100 mA, typical external component values, f_{SWBST} = 2.0 MHz, otherwise noted. Typical values are characterized at V_{IN} = $V_{SWBSTIN}$ = 3.6 V, V_{SWBST} = 5.0 V, I_{SWBST} = 100 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameters | Min. | Тур. | Max. | Unit | Notes | | | |
|--------------------------------------|---|------|------|------|-------|-------|--|--|--|
| Switch mode supply SWBST (continued) | | | | | | | | | |
| ΔV_{SWBST} | Output ripple, 2.8 V \leq V _{IN} \leq 4.5 V, 0 $<$ I _{SWBST} $<$ I _{SWBSTMAX} , excluding reverse recovery of Schottky diode | - | - | 120 | mVp-p | | | | |
| I _{SWBSTLIM} | Peak Current Limit | 1400 | 2200 | 3200 | mA | (34) | | | |
| R _{DS(on)BST} | MOSFET on resistance | _ | 206 | 306 | mΩ | | | | |
| I _{SWBSTHSQ} | NMOS Off leakage, V _{SWBST} = 4.5 V, SWBSTMODE [1:0] = 00 | - | 1.0 | 5.0 | μΑ | | | | |

Notes

Table 14. Dynamic electrical characteristics - SWBST

All parameters are specified at T_A = -40 °C to 105 °C, VIN = $V_{SWBSTIN}$ = 3.6 V, V_{SWBST} = 5.0 V, I_{SWBST} = 100 mA, typical external component values, f_{SWBST} = 2.0 MHz, otherwise noted. Typical values are characterized at V_{IN} = $V_{SWBSTIN}$ = 3.6 V, V_{SWBST} = 5.0 V, I_{SWBST} = 100 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes | |
|--------------------------|--|------|------|------|------|-------|--|
| Switch mode supply SWBST | | | | | | | |
| V _{SWBSTOSH} | Start-up overshoot, I _{SWBST} = 0.0 mA | - | _ | 500 | mV | | |
| t _{ONSWBST} | Turn-on time, enable to 90% of VSWBST, ISWBST = 0.0 mA | _ | _ | 2.0 | ms | | |

Table 15. Static electrical characteristics - VSNVS

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 3.6 V, V_{SNVS} = 3.0 V, I_{SNVS} = 5.0 μ A, typical external component values, unless otherwise noted. Typical values are characterized at V_{IN} = 3.6 V, V_{SNVS} = 3.0 V, I_{SNVS} = 5.0 μ A, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes |
|-----------------------|--|---|-----------------|-----------------------------------|------|-------|
| VSNVS | - | l l | | | l . | |
| V _{IN} | Operating input voltage • Valid coin cell range • Valid V _{IN} | 1.8 2.25 | - - | 3.3 4.5 | V | (35) |
| I _{SNVS} | Operating load current, V _{INMIN} < V _{IN} < V _{INMAX} | 1.0 | - | 1000 | μА | |
| V _{SNVS} | Output voltage • 5.0 μA < I_{SNVS} < 1000 μA (OFF), 3.20 V < V_{IN} < 4.5 V • 5.0 μA < I_{SNVS} < 1000 μA (ON), 3.20 V < V_{IN} < 4.5 V • 5.0 μA < I_{SNVS} < 1000μA (Coin cell mode), 2.84 V < V_{COIN} < 3.3 V | -5.0% -5.0% V _{COIN} -0.10 | 3.0 3.0 – | 7.0% 5.0% V _{COIN} | V | |
| V _{SNVSDROP} | Dropout voltage, 2.85 V < V _{IN} < 2.9 V, 1.0 μA < I _{SNVS} < 1000 μA | - | _ | 110 | mV | |
| I _{SNVSLIM} | Current limit, V _{IN} > V _{TH1} | 1100 | _ | 6750 | μА | |
| VSNVS DC, SWI | СН | | | | | |
| V _{LiCell} | Operating input voltage, valid coin cell range | 1.8 | - | 3.3 | V | |
| lenive | Operating load current | 1.0 | _ | 1000 | uА | |

Notes

R_{DS(on)SNVS}

35. The maximum operating input voltage is 4.55 V when VPWR LDO is used

Internal switch R_{DS(on)}, V_{COIN} = 2.6 V

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^{34.} Only in Auto and APS modes.

Table 16. Dynamic electrical characteristics - VSNVS

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 3.6 V, V_{SNVS} = 3.0 V, I_{SNVS} = 5.0 μ A, typical external component values, unless otherwise noted. Typical values are characterized at V_{IN} = 3.6 V, V_{SNVS} = 3.0 V, I_{SNVS} = 5.0 μ A, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes |
|------------------------|---|------|------|------|------|-----------|
| VSNVS | | | | | | |
| V _{SNVSTON} | Turn-on time (load capacitor, 0.47 μ F), from V _{IN} = V _{TH1} to 90% of V _{SNVS} , V _{COIN} = 0.0 V, I _{SNVS} = 5.0 μ A | - | - | 24 | ms | (36),(37) |
| V _{SNVSOSH} | Start-up overshoot, I _{SNVS} = 5.0 μA | _ | 40 | 70 | mV | |
| V _{SNVSLOTR} | Transient load response, 3.2 < $V_{IN} \le 4.5 \text{ V}$, I_{SNVS} = 100 to 1000 μA | 2.8 | - | - | V | |
| V _{TL1} | V _{IN} falling threshold (V _{IN} powered to coin cell powered) | 2.45 | 2.70 | 3.05 | V | |
| V _{TH1} | V _{IN} rising threshold (coin cell powered to V _{IN} powered) | 2.50 | 2.75 | 3.10 | V | |
| V _{HYST1} | V _{IN} threshold hysteresis for V _{TH1} -V _{TL1} | 5.0 | - | - | mV | |
| V _{SNVSCROSS} | Output voltage during crossover, V_{COIN} > 2.9 V, Switch to LDO: V_{IN} > V_{TH1} , I_{SNVS} = 100 μ A, LDO to Switch: V_{IN} < V_{TL1} , I_{SNVS} = 100 μ A | 2.45 | _ | _ | V | |

Notes

- 36. The start-up of V_{SNVS} is not monotonic. It first rises to 1.0 V and then settles to 3.0 V.
- 37. From coin cell insertion to V_{SNVS} = 1.0 V, the delay time is typically 400 ms.

Table 17. Static electrical characteristics - VLDO1

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 3.6 V, V_{LDO1IN} = 3.6 V, V_{LDO1} = 3.3 V, I_{LDO1} = 10 mA, typical external component values, unless otherwise noted. Typical values are characterized at V_{IN} = 3.6 V, V_{LDO1IN} = 3.6 V, V_{LDO1} = 3.3 V, I_{LDO1} = 10 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes | | | | | |
|----------------------|---|---------------------------------------|----------|------------|------|------------|--|--|--|--|--|
| VLDO1 linear reg | /LDO1 linear regulator | | | | | | | | | | |
| V _{LDO1IN} | Operating input voltage • 1.8 V \leq V _{LDO1NOM} \leq 2.5 V • 2.6 V \leq V _{LDO1NOM} \leq 3.3 V | 2.8 V _{LDO1NOM} +0.250 | - 1 | 4.5 4.5 | V | (38), (39) | | | | | |
| V _{LDO1NOM} | Nominal output voltage | - | Table 62 | - | V | | | | | | |
| I _{LDO1} | Rated output load current | 100 | _ | _ | mA | | | | | | |
| V _{LDO1TOL} | Output voltage tolerance, V _{LDO1INMIN} < V _{LDO1IN} < 4.5 V, 0.0 mA < I _{LDO1} < 100 mA, VLDO1 = 1.8 V to 3.3 V | -3.0 | _ | 3.0 | % | | | | | | |
| I _{LDO1Q} | Quiescent current, no load, change in I _{VIN,} when VLDO1 enabled | _ | 13 | _ | μΑ | | | | | | |
| I _{LDO1LIM} | Current limit, I _{LDO1} when V _{LDO1} is forced to V _{LDO1NOM} /2 | 122 | 167 | 280 | mA | | | | | | |

Notes

- 38. The maximum operating input voltage is 4.55 V when VPWR LDO is used.
- 39. Minimum operating voltage is 2.8 V with a valid LICELL voltage (1.8 V to 3.3 V). Minimum operating voltage is 3.1 V when no voltage is applied at the LICELL pin. If operation down to 2.8 V is required for systems without a coin cell, connect the LICELL pin to any system voltage between 1.8 V and 3.3 V. This voltage can be an output from any PF3000 regulator, or external system supply.

Table 18. Dynamic electrical characteristics - VLDO1

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 3.6 V, V_{LDO1IN} = 3.6 V, V_{LDO1} = 3.3 V, I_{LDO1} = 10 mA, typical external component values, unless otherwise noted. Typical values are characterized at V_{IN} = 3.6 V, V_{LDO1IN} = 3.6 V, V_{LDO1} = 3.3 V, I_{LDO1} = 10 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes |
|------------------------|---|-------------|----------------------|----------------------|----------|-------|
| VLDO1 linear reg | ulator | | | | | |
| PSRR _{VLDO1} | PSRR, I _{LDO1} = 75 mA, 20 Hz to 20 kHz • VLDO1 = 1.8 V to 3.3 V, V _{LDO1IN} = V _{LDO1INMIN} + 100 mV • VLDO1 = 1.8 V to 3.3 V, V _{LDO1IN} = V _{LDO1NOM} + 1.0 V | 35 52 | 40 60 | _ _ | dB | |
| NOISE _{VLDO1} | Output noise density, V _{LDO1IN} = V _{LDO1INMIN} , I _{LDO1} = 75 mA • 100 Hz to <1.0 kHz • 1.0 kHz to <10 kHz • 10 kHz to 1.0 MHz | - - - | -114 -129 -135 | -102 -123 -130 | dBV/ √Hz | |
| t _{ONLDO1} | Turn-on time, enable to 90% of end value, $V_{LDO1IN} = V_{LDO1INMIN}$ to 4.5 V, $I_{LDO1} = 0.0$ mA, all output voltage settings | 60 | _ | 500 | μs | |
| t _{OFFLDO1} | Turn-off time, disable to 10% of initial value, $V_{LDO1IN} = V_{LDO1INMIN}$, $I_{LDO1} = 0.0 \text{ mA}$ | - | _ | 10 | ms | |
| LDO1 _{OSHT} | Start-up overshoot, $V_{LDO1IN} = V_{LDO1INMIN}$ to 4.5 V, $I_{LDO1} = 0.0$ mA | _ | 1.0 | 2.0 | % | |

Table 19. Static electrical characteristics - VLDO2

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 3.6 V, V_{LDO2IN} = 3.0 V, V_{LDO2} = 1.55 V, I_{LDO2} = 10 mA, typical external component values, unless otherwise noted. Typical values are characterized at V_{IN} = 3.6 V, V_{LDO2IN} = 3.0 V, V_{LDO2} = 1.55 V, I_{LDO2} = 10 mA and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes | | | | |
|----------------------|---|------|----------|------|------|-------|--|--|--|--|
| VLDO2 linear reg | LDO2 linear regulator | | | | | | | | | |
| V _{LDO2IN} | Operating input voltage | 1.75 | _ | 3.40 | V | | | | | |
| V _{LDO2NOM} | Nominal output voltage | _ | Table 63 | _ | V | | | | | |
| I _{LDO2} | Rated output load current | 250 | _ | _ | mA | | | | | |
| V _{LDO2TOL} | Output voltage tolerance, 1.75 V < V_{LDOIN1} < 3.40 V, 0.0 mA < I_{LDO2} < 250 mA, VLDO2 = 0.8 V to 1.55 V | -3.0 | _ | 3.0 | % | | | | | |
| I _{LDO2Q} | Quiescent current, no load, change in $\rm I_{\rm VIN}$ and $\rm I_{\rm VLDO2IN}$, when $\rm V_{\rm LDO2}$ enabled | - | 16 | - | μΑ | | | | | |
| I _{LDO2LIM} | Current limit, I _{LDO2} when V _{LDO2} is forced to V _{LDO2NOM} /2 | 333 | 417 | 612 | mA | | | | | |

Table 20. Dynamic electrical characteristics - VLDO2

All parameters are specified at TA = -40 °C to 105 °C, VIN = 3.6 V, V_{LDO2IN} = 3.0 V, V_{LDO2} = 1.55 V, I_{LDO2} = 10 mA, typical external component values, unless otherwise noted. Typical values are characterized at V_{IN} = 3.6 V, V_{LDO2IN} = 3.0 V, V_{LDO2} = 1.55 V, I_{LDO2} = 10 mA and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes |
|------------------------|--|-------------|----------------------|----------------------|---------|-------|
| VLDO2 linear reg | ulator | | | | | |
| PSRR _{VLDO2} | PSRR, I _{LDO2} = 187.5 mA, 20 Hz to 20 kHz • VLDO2 = 0.8 V to 1.55 V • VLDO2 = 1.1 V to 1.55 V | 50 37 | 60 45 | - - | dB | |
| NOISE _{VLDO2} | Output noise density, V _{LDO2IN} = 1.75 V, I _{LDO2} = 187.5 mA • 100 Hz to <1.0 kHz • 1.0 kHz to <10 kHz • 10 kHz to 1.0 MHz | - - - | -108 -118 -124 | -100 -108 -112 | dBV/√Hz | |

Table 20. Dynamic electrical characteristics - VLDO2 (continued)

All parameters are specified at TA = -40 °C to 105 °C, VIN = 3.6 V, V_{LDO2IN} = 3.0 V, V_{LDO2} = 1.55 V, I_{LDO2} = 10 mA, typical external component values, unless otherwise noted. Typical values are characterized at V_{IN} = 3.6 V, V_{LDO2IN} = 3.0 V, V_{LDO2} = 1.55 V, I_{LDO2} = 10 mA and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes | | |
|-----------------------------------|---|------|------|------|------|-------|--|--|
| VLDO2 linear regulator (continue) | | | | | | | | |
| t _{ONLDO2} | Turn-on time, enable to 90% of end value, V_{LDO2IN} = 1.75 V to 3.4 V, I_{LDO2} = 0.0 mA | 60 | _ | 500 | μs | | | |
| t _{OFFLDO2} | Turn-off time, disable to 10% of initial value, V_{LDO2IN} = 1.75 V, I_{LDO2} = 0.0 mA | - | _ | 10 | ms | | | |
| LDO2 _{OSHT} | Start-up overshoot, V _{LDO2IN} = 1.75 V to 3.4 V, I _{LDO2} = 0.0 mA | - | 1.0 | 2.0 | % | | | |

Table 21. Static electrical characteristics – VCC_SD

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 3.6 V, VCC_SD = 1.85 V, I_{VCC_SD} = 10 mA, typical external component values, unless otherwise noted. Typical values are characterized at V_{IN} = 3.6 V, VCC_SD = 1.85 V, I_{VCC_SD} = 10 mA, and 25 °C, unless otherwise noted

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes |
|------------------------|--|------|----------|------|------|---------------------|
| VCC_SD linear re | gulator | | 1 | | | 1 |
| V _{IN} | Operating input voltage | 2.8 | _ | 4.5 | V | (40), (41), (41) |
| V _{CC_SDNOM} | Nominal output voltage | - | Table 65 | - | V | |
| I _{VCC_SD} | Rated output load current | 100 | _ | _ | mA | |
| V _{CC_SDTOL} | Output voltage accuracy, 2.8 V < $V_{\rm IN}$ < 4.5 V, 0.0 mA < $I_{\rm VCC_SD}$ < 100 mA, VCC_SD[1:0] = 00 to 11 | -3.0 | _ | 3.0 | % | |
| I _{VCC_SDQ} | Quiescent current, no load, change in I_{VIN} and $I_{VIN2},$ when V_{CC_SD} enabled | - | 13 | - | μА | |
| I _{VCC_SDLIM} | Current limit, I _{VCC_SD} when V _{CC_SD} is forced to V _{CC_SDNOM} /2 | 122 | 167 | 280 | mA | |

Notes

- 40. When the LDO output voltage is set above 2.6 V, the minimum allowed input voltage needs to be at least the output voltage plus 0.25 V.
- 41. The maximum operating input voltage is 4.55 V when VPWR LDO is used.
- 42. Minimum operating voltage is 2.8 V with a valid LICELL voltage (1.8 V to 3.3 V). Minimum operating voltage is 3.1 V when no voltage is applied at the LICELL pin. If operation down to 2.8 V is required for systems without a coin cell, connect the LICELL pin to any system voltage between 1.8 V and 3.3 V. This voltage can be an output from any PF3000 regulator, or external system supply.

Table 22. Dynamic electrical characteristics - VCC_SD

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 3.6 V, VCC_SD = 1.85 V, IVCC_SD = 10 mA, typical external component values, unless otherwise noted. Typical values are characterized at V_{IN} = 3.6 V, VCC_SD = 1.85 V, IVCC_SD = 10 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes |
|-------------------------|---|-------------|----------------------|----------------------|---------|-------|
| VCC_SD linear re | gulator | | | | | |
| PSRR _{VCC_SD} | PSRR, I _{VCC_SD} = 75 mA, 20 Hz to 20 kHz • VCC_SD[1:0] = 00 - 10, V _{IN} = 2.8 V + 100 mV • VCC_SD[1:0] = 10 - 11, V _{IN} = V _{CC_SDNOM} + 1.0 V | 35 52 | 40 60 | - - | dB | |
| NOISE _{VCC_SD} | Output noise density, V _{IN} = 2.8V, I _{VCC_SD} = 75 mA • 100 Hz - <1.0 kHz • 1.0 kHz - <10 kHz • 10 kHz - 1.0 MHz | - - - | -114 -129 -135 | -102 -123 -130 | dBV/√Hz | |
| tonvcc_sd | Turn-on time, enable to 90% of end value, $V_{\rm IN}$ = 2.8 V to 4.5 V, $I_{\rm VCC_SD}$ = 0.0 mA | 60 | - | 500 | μs | |

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Table 22. Dynamic electrical characteristics - VCC_SD (continued)

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 3.6 V, VCC_SD = 1.85 V, IVCC_SD = 10 mA, typical external component values, unless otherwise noted. Typical values are characterized at V_{IN} = 3.6 V, VCC_SD = 1.85 V, IVCC_SD = 10 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes | |
|-------------------------------------|--|------|------|------|------|-------|--|
| VCC_SD linear regulator (continued) | | | | | | | |
| toffvcc_sd | Turn-off time, disable to 10% of initial value, V_{IN} = 2.8 V, I_{VCC_SD} = 0.0 mA | - | - | 10 | ms | | |
| VCC_SD _{OSHT} | Start-up overshoot, V_{IN} = 2.8 V to 4.5 V, I_{VCC_SD} = 0.0 mA | - | 1.0 | 2.0 | % | | |

Table 23. Static electrical characteristics - V33

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 3.6 V, V_{33} = 3.3 V, I_{V33} = 10 mA, typical external component values, unless otherwise noted. Typical values are characterized at V_{IN} = 3.6 V, V_{33} = 3.3 V, V_{33} = 10 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes |
|---------------------|--|------|----------|------|------|---------------------|
| V33 linear regula | itor | | | | | |
| V _{IN} | Operating input voltage, 2.9 V ≤ V _{33NOM} ≤ 3.6 V | 2.8 | - | 4.5 | V | (43), (44), (45) |
| V _{33NOM} | Nominal output voltage | _ | Table 64 | _ | V | |
| I _{V33} | Rated output load current | 350 | _ | _ | mA | |
| V _{33TOL} | Output voltage tolerance, 2.8 V < $V_{\rm IN}$ < 4.5 V, 0.0 mA < $I_{\rm V33}$ < 350 mA, $V_{\rm 33}$ [1:0] = 00 to 11 | -3.0 | - | 3.0 | % | |
| I _{V33Q} | Quiescent current, no load, change in I _{VIN} , when V ₃₃ enabled | _ | 13 | _ | μΑ | |
| I _{V33LIM} | Current limit, I _{V33} when V ₃₃ is forced to V _{33NOM} /2 | 435 | 584.5 | 950 | mA | |

Notes

- 43. When the LDO output voltage is set above 2.6 V the minimum allowed input voltage need to be at least the output voltage plus 0.25 V for proper regulation due to the dropout voltage generated through the internal LDO transistor.
- 44. The maximum operating input voltage is 4.55 V when VPWR LDO is used.
- 45. Minimum operating voltage is 2.8 V with a valid LICELL voltage (1.8 V to 3.3 V). Minimum operating voltage is 3.1 V when no voltage is applied at the LICELL pin. If operation down to 2.8 V is required for systems without a coin cell, connect the LICELL pin to any system voltage between 1.8 V and 3.3 V. This voltage can be an output from any PF3000 regulator, or external system supply.

Table 24. Dynamic electrical characteristics - V33

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 3.6 V, V_{33} = 3.3 V, I_{V33} = 10 mA, typical external component values, unless otherwise noted. Typical values are characterized at V_{IN} = 3.6 V, V_{33} = 3.3 V, V_{33} = 10 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes |
|----------------------|--|-------------|----------------------|----------------------|---------|-------|
| V33 linear regulat | tor | ll. | ll. | I. | | I |
| PSRR _{V33} | PSRR, I_{V33} = 262.5 mA, 20 Hz to 20 kHz, V_{33} [1:0] = 00 - 11, V_{IN} = V_{33NOM} + 1.0 V | 52 | 60 | _ | dB | (46) |
| NOISE _{V33} | Output noise density, V _{IN} = 2.8 V, I _{V33} = 262.5 mA • 100 Hz to <1.0 kHz • 1.0 kHz to <10 kHz • 10 kHz to 1.0 MHz | - - - | -114 -129 -135 | -102 -123 -130 | dBV/√Hz | |
| t _{ONV33} | Turn-on time, enable to 90% of end value, V_{IN} = 2.8 V, to 4.5 V, I_{V33} = 0.0 mA | 60 | _ | 500 | μs | |

Table 24. Dynamic electrical characteristics - V33 (continued)

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 3.6 V, V_{33} = 3.3 V, I_{V33} = 10 mA, typical external component values, unless otherwise noted. Typical values are characterized at V_{IN} = 3.6 V, V_{33} = 3.3 V, I_{V33} = 10 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes | | |
|---------------------|--|------|------|------|------|-------|--|--|
| V33 linear regulate | V33 linear regulator (continued) | | | | | | | |
| t _{OFFV33} | Turn-off time, disable to 10% of initial value, V_{IN} = 2.8 V, I_{V33} = 0.0 mA | - | _ | 10 | ms | | | |
| V _{33OSHT} | Start-up overshoot, V_{IN} = 2.8 V to 4.5 V, I_{V33} = 0.0 mA | - | 1.0 | 2.0 | % | | | |

Notes

Table 25. Static electrical characteristics - VLDO3

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 3.6 V, $V_{LDO34IN}$ = 3.6 V, V_{LDO3} = 3.3 V, I_{LDO3} = 10 mA, typical external component values, unless otherwise noted. Typical values are characterized at V_{IN} = 3.6 V, $V_{LDO34IN}$ = 3.6 V, V_{LDO3} = 3.3 V, I_{LDO3} = 10 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes | | | | |
|----------------------|---|---------------------------------------|----------|------------|------|------------|--|--|--|--|
| VLDO3 linear regu | /LDO3 linear regulator | | | | | | | | | |
| V _{LDO34IN} | Operating input voltage • $1.8 \text{ V} \le \text{V}_{\text{LDO3NOM}} \le 2.5 \text{ V}$ • $2.6 \text{ V} \le \text{V}_{\text{LDO3NOM}} \le 3.3 \text{ V}$ | 2.8 V _{LDO3NOM} +0.250 | 1 1 | 3.6 3.6 | V | (47), (48) | | | | |
| V _{LDO3NOM} | Nominal output voltage | _ | Table 63 | - | V | | | | | |
| I _{LDO3} | Rated output load current | 100 | - | - | mA | | | | | |
| V _{LDO3TOL} | Output voltage tolerance, $V_{LDO34INMIN}$ < $V_{LDO34IN}$ < 4.5 V, 0.0 mA < I_{LDO3} < 100 mA, VLDO3 = 1.8 V to 3.3 V | -3.0 | _ | 3.0 | % | | | | | |
| I _{LDO3Q} | Quiescent current, no load, change in I_{VIN} and $I_{VLDO34IN},$ when V_{LDO3} enabled | _ | 13 | - | μΑ | | | | | |
| I _{LDO3LIM} | Current limit, I _{LDO3} when V _{LDO3} is forced to V _{LDO3NOM} /2 | 122 | 167 | 280 | mA | | | | | |

Notes

- 47. Beyond VLDO34IN rating, the ESD protection can be sensitive to voltage transients.
- 48. Minimum operating voltage is 2.8 V with a valid LICELL voltage (1.8 V to 3.3 V). Minimum operating voltage is 3.1 V when no voltage is applied at the LICELL pin. If operation down to 2.8 V is required for systems without a coin cell, connect the LICELL pin to any system voltage between 1.8 V and 3.3 V. This voltage can be an output from any PF3000 regulator, or external system supply.

Table 26. Dynamic electrical characteristics – VLDO3

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 3.6 V, $V_{LDO34IN}$ = 3.6 V, V_{LDO3} = 3.3 V, I_{LDO3} = 10 mA, typical external component values, unless otherwise noted. Typical values are characterized at V_{IN} = 3.6 V, $V_{LDO34IN}$ = 3.6 V, V_{LDO3} = 3.3 V, I_{LDO3} = 10 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes | | |
|------------------------|--|-------------|----------------------|----------------------|---------|-------|--|--|
| VLDO3 linear regulator | | | | | | | | |
| PSRR _{VLDO3} | PSRR, I _{LDO3} = 75 mA, 20 Hz to 20 kHz • VLDO3 = 1.8 V to 3.3 V, V _{LDO34IN} = V _{LDO34INMIN} + 100 mV • VLDO3 = 1.8 V to 3.3 V, V _{LDO34IN} = V _{LDO3NOM} + 1.0 V | 35 52 | 40 60 | - - | dB | | | |
| NOISE _{VLDO3} | Output noise density, V _{LDO34IN} = V _{LDO34INMIN} , I _{LDO3} = 75 mA • 100 Hz to <1.0 kHz • 1.0 kHz to <10 kHz • 10 kHz to 1.0 MHz | - - - | -114 -129 -135 | -102 -123 -130 | dBV/√Hz | | | |

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^{46.} When the LDO Output voltage is set above 2.6 V the minimum allowed input voltage need to be at least the output voltage plus 0.25 V for proper regulation due to the dropout voltage generated through the internal LDO transistor.

Table 26. Dynamic electrical characteristics – VLDO3 (continued)

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 3.6 V, $V_{LDO34IN}$ = 3.6 V, V_{LDO3} = 3.3 V, I_{LDO3} = 10 mA, typical external component values, unless otherwise noted. Typical values are characterized at V_{IN} = 3.6 V, $V_{LDO34IN}$ = 3.6 V, V_{LDO3} = 3.3 V, I_{LDO3} = 10 mA, and 25 °C, unless otherwise noted.

| Symbol | Parameter | | Тур. | Max. | Unit | Notes |
|------------------------------------|--|----|------|------|------|-------|
| VLDO3 linear regulator (continued) | | | | | | |
| t _{ONLDO3} | Turn-on time, enable to 90% of end value, $V_{LDO34IN} = V_{LDO34INMIN}$ to 4.5 V, I_{LDO3} = 0.0 mA | 60 | - | 500 | μs | |
| t _{OFFLDO3} | Turn-off time, disable to 10% of initial value, $V_{LDO34IN} = V_{LDO34INMIN}$, $I_{LDO3} = 0.0 \text{ mA}$ | | - | 10 | ms | |
| LDO3 _{OSHT} | Start-up overshoot, $V_{LDO34IN} = V_{LDO34IN2MIN}$ to 4.5 V, $I_{LDO3} = 0.0$ mA | - | 1.0 | 2.0 | % | |

Table 27. Static electrical characteristics - VLDO4

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 3.6 V, $V_{LDO34IN}$ = 3.6 V, V_{LDO4} = 3.3 V, I_{LDO4} = 10 mA, typical external component values, unless otherwise noted. Typical values are characterized at V_{IN} = 3.6 V, $V_{LDO34IN}$ = 3.6 V,

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes |
|-----------------------|---|---------------------------------------|----------|------------|------|------------|
| VLDO4 linear regu | ulator | | | | | |
| V _{LDO34IN} | Operating input voltage • $1.8 \text{ V} \le \text{V}_{\text{LDO4NOM}} \le 2.5 \text{ V}$ • $2.6 \text{ V} \le \text{V}_{\text{LDO4NOM}} \le 3.3 \text{ V}$ | 2.8 V _{LDO4NOM} +0.250 | - - | 3.6 3.6 | V | (49), (50) |
| V _{LDO4NOM} | Nominal output voltage | _ | Table 63 | _ | V | |
| I _{LDO4} | Rated output load current | 350 | 1 | _ | mA | |
| V _{LDO4TOL} | Output voltage tolerance, $V_{LDO34INMIN}$ < $V_{LDO34IN}$ < 4.5 V, 0.0 mA < I_{LDO3} < 100 mA, V_{LDO4} = 1.9 V to 3.3 V | -3.0 | _ | 3.0 | % | |
| I _{LDO4Q} | Quiescent current, no load, change in $\rm I_{VIN}$ and $\rm I_{VLDO34IN},$ when $\rm V_{LDO4}$ enabled | - | 13 | - | μА | |
| I _{LDO4LIM} | Current limit, I _{LDO4} when V _{LDO4} is forced to V _{LDO4NOM} /2 | 435 | 584.5 | 950 | mA | |
| PSRR _{VLDO4} | PSRR, I _{LDO4} = 262.5 mA, 20 Hz to 20 kHz • VLDO4 = 1.9 V to 3.3 V, V _{LDO34IN} = V _{LDO34INMIN} + 100 mV • VLDO4 = 1.9 V to 3.3 V, V _{LDO34IN} = V _{LDO4NOM} + 1.0 V | 35 52 | 40 60 | - - | dB | |

Notes

- 49. Beyond VLDO34IN rating, the ESD protection can be sensitive to voltage transients.
- 50. Minimum operating voltage is 2.8 V with a valid LICELL voltage (1.8 V to 3.3 V). Minimum operating voltage is 3.1 V when no voltage is applied at the LICELL pin. If operation down to 2.8 V is required for systems without a coin cell, connect the LICELL pin to any system voltage between 1.8 V and 3.3 V. This voltage can be an output from any PF3000 regulator, or external system supply.

Table 28. Dynamic electrical characteristics - VLDO4

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 3.6 V, $V_{LDO34IN}$ = 3.6 V, V_{LDO4} = 3.3 V, I_{LDO4} = 10 mA, typical external component values, unless otherwise noted. Typical values are characterized at V_{IN} = 3.6 V, $V_{LDO34IN}$ = 3.6 V,

| Symbol | Parameter | | Тур. | Max. | Unit | Notes |
|------------------------|--|-------------|----------------------|----------------------|---------|-------|
| VLDO4 linear regi | ulator | | | | | |
| NOISE _{VLDO4} | Output noise density, V _{LDO34IN2} = V _{LDO34INMIN} , I _{LDO4} = 262.5 mA • 100 Hz to <1.0 kHz • 1.0 kHz to <10 kHz • 10 kHz to 1.0 MHz | - - - | -114 -129 -135 | -102 -123 -130 | dBV/√Hz | |
| t _{ONLDO4} | Turn-on time, enable to 90% of end value, $V_{LDO34IN} = V_{LDO34INMIN}$, 4.5 V, $I_{LDO4} = 0.0$ mA | 60 | _ | 500 | μs | |
| t _{OFFLDO4} | Turn-off time, disable to 10% of initial value, $V_{LDO34IN} = V_{LDO34INMIN}$, $I_{LDO4} = 0.0 \text{ mA}$ | _ | _ | 10 | ms | |
| LDO4 _{OSHT} | Start-up overshoot, V _{LDO34IN} = V _{LDO34INMIN} , 4.5 V, I _{LDO4} = 0.0 mA | - | 1.0 | 2.0 | % | |

Table 29. Static electrical characteristics - coin cell

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 3.6 V, typical external component values, unless otherwise noted.

| Symbol | Parameter | | Тур | Max | Unit | Notes |
|----------------------|--|--------|----------|------|------|-------|
| Coin cell | | | | | | |
| V _{COINACC} | Charge voltage accuracy | -100 | - | -100 | mV | |
| I _{COINACC} | Charge current accuracy | -30 | _ | 30 | % | |
| I _{COIN} | Coin cell charge current • I _{COINHI} (in on mode) • I _{COINLO} (in on mode) | - - | 60 10 | - | μА | |

Table 30. Static electrical characteristics - VREFDDR

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 3.6 V, I_{REFDDR} = 0.0 mA, $V_{INREFDDR}$ = 1.5 V, and typical external component values, unless otherwise noted. Typical values are characterized at V_{IN} = 3.6 V, I_{REFDDR} = 0.0 mA, $V_{INREFDDR}$ = 1.5 V, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes |
|--------------------------|---|------|-------------------------|------|------|-------|
| VREFDDR linear regulator | | | | | | • |
| V _{INREFDDR} | Operating input voltage range | 1.2 | - | 1.65 | V | (51) |
| V _{REFDDR} | Output voltage, 1.2 V < V _{INREFDDR} < 1.65 V, 0.0 mA < I _{REFDDR} < 10 mA | - | V _{INREFDDR} / | - | V | |
| V _{REFDDRTOL} | Output voltage tolerance, as a percentage of V _{INREFDDR} , 1.2 V < V _{INREFDDR} < 1.65 V, 0.6 mA < I _{REFDDR} < 10 mA | 49.5 | 50 | 50.5 | % | |
| I _{REFDDR} | Rated output load current | 10 | _ | _ | mA | |
| I _{REFDDRQ} | Quiescent current | _ | 12 | _ | μΑ | (52) |
| I _{REFDDRLM} | Current limit, I _{REFDDR} when V _{REFDDR} is forced to V _{INREFDDR} /4 | 10.5 | 15 | 25 | mA | |

Notes

- 51. When using SW3 as input, the VINREFDDR input voltage range specification refers to the voltage set point of SW3 and not the absolute value
- 52. When VREFDDR is off there is a quiescent current of a typical 2.0 μ A.

Table 31. Dynamic electrical characteristics - VREFDDR

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 3.6 V, I_{REFDDR} = 0.0 mA, $V_{INREFDDR}$ = 1.5 V, and typical external component values, unless otherwise noted. Typical values are characterized at V_{IN} = 3.6 V, I_{REFDDR} = 0.0 mA, $V_{INREFDDR}$ = 1.5 V, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes |
|------------------------|---|------|------|------|------|-------|
| VREFDDR linear re | egulator | | | | | |
| tonrefddr | Turn-on time, enable to 90% of end value, $V_{INREFDDR}$ = 1.2 V to 1.65 V, I_{REFDDR} = 0.0 mA | - | - | 100 | μs | |
| t _{OFFREFDDR} | Turn-off time, disable to 10% of initial value, $V_{INREFDDR}$ = 1.2 V to 1.65 V, I_{REFDDR} = 0.0 mA | - | _ | 10 | ms | |
| V _{REFDDROSH} | Start-up overshoot, V _{INREFDDR} = 1.2 V to 1.65 V, I _{REFDDR} = 0.0 mA | _ | 1.0 | 6.0 | % | |

Table 32. Static electrical characteristics - Digital I/O

All parameters are specified at T_A = -40 °C to 105 °C, V_{DDIO} = 1.7 V to 3.6 V, V_{PWR} = 0 V (external FET not populated), and typical external component values and full load current range, unless otherwise noted.

| Pin name | Parameter | Load condition | Min | Max | Unit | Notes |
|-----------|---|---------------------------------|--------------------------------|--|------|-------|
| PWRON | • V _L • V _H | - - | 0.0 0.8 * V _{SNVS} | 0.2 * V _{SNVS} 3.6 | V | |
| RESETBMCU | • V _{OL} • V _{OH} | -2.0 mA Open drain | 0.0 0.7 * V _{DDIO} | 0.4 * V _{DDIO} V _{DDIO} | V | |
| SCL | • V _L • V _H | | 0.0 0.8 * V _{DDIO} | 0.2 * V _{DDIO} 3.6 | ٧ | |
| SDA | • V _L • V _H • V _{OL} • V _{OH} | – – -2.0 mA Open drain | 0.8 * V _{DDIO} | 0.4 * V _{DDIO} | ٧ | |
| INTB | • V _{OL} • V _{OH} | -2.0 mA Open drain | 0.0 0.7 * V _{DDIO} | 0.4 * V _{DDIO} V _{DDIO} | V | |
| STANDBY | • V _L • V _H | | 0.0 0.8 * V _{SNVS} | 0.2 * V _{SNVS} 3.6 | V | |
| SD_VSEL | • V _L • V _H | - | 0.0 0.8 * V _{DDIO} | 0.2 * V _{DDIO} 3.6 | V | |
| VDDOTP | • V _L • V _H | | 0.0 1.1 | 0.3 1.7 | V | |

Table 33. Static electrical characteristics - internal supplies

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 2.8 V to 4.5 V, LICELL = 1.8 V to 3.3 V, and typical external component values. Typical values are characterized at V_{IN} = 3.6 V, LICELL = 3.0 V, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes |
|--------------------------|--|--------|--------------|--------|------|-------|
| VCOREDIG (digita | l core supply) | | | | | • |
| V _{COREDIG} | Output voltage ON mode Coin cell mode and OFF mode | - - | 1.5 1.3 | _ _ | ٧ | (53) |
| VCORE (analog co | pre supply) | | • | | • | |
| V _{CORE} | Output voltage ON mode and charging Coin cell mode and OFF mode | _ _ | 2.775 0.0 | _ _ | ٧ | (53) |
| VCOREREF (band | gap regulator reference) | | | | | |
| V _{COREREF} | Output voltage at 25 °C | _ | 1.2 | _ | V | (53) |
| V _{COREREFACC} | Absolute trim accuracy | _ | 0.5 | _ | % | |
| V _{COREREFTACC} | Temperature Drift | _ | 0.25 | _ | % | |

Notes

Table 34. Static electrical characteristics - UVDET threshold

All parameters are specified at T_A = -40 °C to 105 °C, V_{IN} = 2.8 V to 4.5 V, LICELL = 1.8 V to 3.3 V, and typical external component values. Typical values are characterized at V_{IN} = 3.6 V, LICELL = 3.0 V, and 25 °C, unless otherwise noted.

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Notes |
|------------------------------|--------------------|----------|------|----------|------|-------|
| V _{IN} UVDET thresh | old | | | | | |
| V _{UVDET} | Rising Falling | - 2.5 | - | 3.1 _ | V | |

^{53.} $3.1 \text{ V} < V_{IN} < 4.5 \text{ V}$, no external loading on VCOREDIG, VCORE, or VCOREREF.

6 Functional description and application information

6.1 Introduction

The PF3000 is a highly integrated, low quiescent current power management IC featuring four buck regulators, one boost regulator, seven LDO regulators, and a DDR voltage reference. The PF3000 provides all the necessary rails to power a complete system including the application processor, memory and peripherals. The PF3000 operates from an input voltage of up to 5.5 V. Output voltage, startup sequence, and other functions are set using integrated one-time-programmable (OTP) memory, thus providing flexibility and reducing external component count.

6.2 Power generation

The buck regulators in the PF3000 provide supply to the processor cores and to other voltage domains, such as I/O and memory. Dynamic voltage scaling is provided to allow controlled supply rail adjustments for the processor cores and other circuitry. The SW1A and SW1B buck regulators can either be used as independent 1.0 A and 1.75 A regulators, or can be combined as a single 2.75 A regulator.

The linear regulators in the PF3000 can be used as general purpose regulators to power peripherals and lower power processor rails. The VCC_SD LDO regulator supports the dual voltage requirement by high speed SD card readers. Depending on the system power path configuration, the LDO regulators can be directly supplied from the main input supply or from the switching regulators to power peripherals, such as audio, camera, Bluetooth, and Wireless LAN, etc.

A specific V_{REFDDR} voltage reference is included to provide accurate reference voltage for DDR memories. The VSNVS block behaves as an LDO, or as a bypass switch to supply the SNVS/SRTC circuitry on the i.MX processors; V_{SNVS} may be powered from V_{IN} , or from a coin cell.

To accommodate applications that are powered by main supplies of voltages higher than 4.5 V and up to 5.5 V, the PF3000 incorporates a front-end LDO regulator using an external pass FET to keep the maximum regulator input voltage of the regulators at 4.5 V. Applications with an input voltage lower than 4.5 V can directly power the regulators without using the front-end LDO.

PF3000 shows a summary of the voltage regulators in the PF3000.

Table 35. PF3000 power tree

| Supply | Output voltage (V) | Programming Step size (mV) | Maximum load current (mA) |
|---------|------------------------------|----------------------------|---------------------------|
| SW1A | 0.70 to 1.425 1.8 to 3.3 | 25 (N/A) | 1000 |
| SW1B | 0.70 to 1.475 | 25 | 1750 |
| SW2 | 1.50 to 1.85 2.50 to 3.30 | 50 variable | 1250 |
| SW3 | 0.90 to 1.65 | 50 | 1500 |
| SWBST | 5.00 to 5.15 | 50 | 600 |
| VLDO1 | 1.8 to 3.3 | 50 | 100 |
| VLDO2 | 0.80 to 1.55 | 50 | 250 |
| VCC_SD | 2.85 to 3.30 1.80 to 1.85 | 150 50 | 100 |
| V33 | 2.85 to 3.30 | 150 | 350 |
| VLDO3 | 1.8 to 3.3 | 100 | 100 |
| VLDO4 | 1.8 to 3.3 | 100 | 350 |
| VSNVS | 3.0 | NA | 1.0 |
| VREFDDR | 0.5*SW3_OUT | NA | 10 |

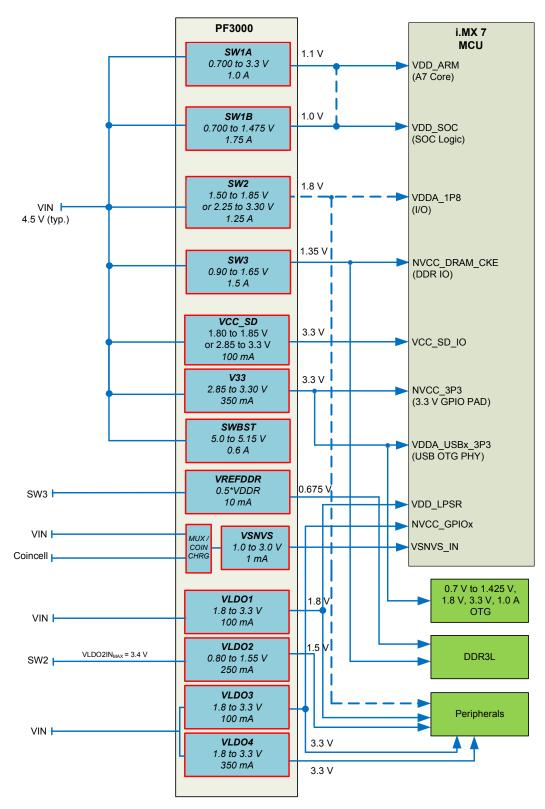


Figure 5. PF3000 typical power map

<u>Figure 5</u> shows a simplified power map with various recommended options to supply the different block within the PF3000, as well as the typical application voltage domain on the i.MX 7 processors. Note that each application power tree is dependent upon the system's voltage and current requirements, therefore a proper input voltage should be selected for the regulators.

6.3 Functional description

6.3.1 Control logic and interface signals

The PF3000 is fully programmable via the I²C interface. Additional communication is provided by direct logic interfacing including INTB, RESETBMCU, STANDBY, PWRON, and SD_VSEL. Refer to Table 30 for logic levels for these pins.

6.3.1.1 PWRON

PWRON is an input signal to the IC that generates a turn-on event. A turn-on event brings the PF3000 out of OFF and sleep modes and into the ON mode. Refer to Modes of operation for the various modes (states) of operation of the IC. The PWRON pin can be configured using OTP to detect a level, or an edge using the PWRON_CFG bit.

- If PWRON_CFG = 0, the PWRON signal is high and VIN > UVDET, the PMIC turns on; the interrupt and sense bits, PWRONI and PWRONS respectively, is set.
- If PWRON_CFG = 1, VIN > UVDET and PWRON transitions from high to low, the PMIC turns on; the interrupt and sense bits, PWRONI and PWRONS respectively, is set.

Any regulator enabled in the sleep mode remains enabled when transitioning from Sleep to ON, i.e., the regulator is not turned off and then on again to match the start-up sequence.

When PWRON_CFG = 1, the PWRON input can be a mechanical switch debounced through a programmable debouncer PWRONDBNC[1:0], to avoid a response to a very short key press. The interrupt is generated for both the falling and the rising edge of the PWRON pin. By default, a 31.25 ms interrupt debounce is applied to both falling and rising edges. The falling edge debounce timing can be extended with PWRONDBNC[1:0] as defined in the table below. The interrupt is cleared by software, or when cycling through the OFF mode.

Table 36. PWRON hardware debounce bit settings (54)

| Bits | State | Turn on debounce (ms) | Falling edge INT debounce (ms) | Rising edge INT debounce (ms) |
|----------------|-------|-----------------------|--------------------------------|-------------------------------|
| | 00 | 0.0 | 31.25 | 31.25 |
| PWRONDBNC[1:0] | 01 | 31.25 | 31.25 | 31.25 |
| T WINDING[1.0] | 10 | 125 | 125 | 31.25 |
| | 11 | 750 | 750 | 31.25 |

Notes

6.3.1.2 STANDBY

STANDBY is an input signal to the IC. When it is asserted the part enters standby mode and when de-asserted, the part exits standby mode. STANDBY can be configured as active high or active low using the STANDBYINV bit. See Standby mode for more details.

Note: When operating the PMIC at VIN \leq 2.85 V a coin cell must be present to provide V_{SNVS} , or the PMIC does not reliably enter and exit the STANDBY mode.

6.3.1.3 **RESETBMCU**

RESETBMCU is an open-drain, active low output OTP configurable for two modes of operation. In its default mode, it is de-asserted 2.0 ms after the last regulator in the start-up sequence is enabled. In this mode, the signal can be used to bring the processor out of reset (POR), or as an indicator that all supplies have been enabled; it is only asserted during a turn-off event. In the default mode, the RESETBMCU signal is internal timer based and does not monitor the regulators. When configured for its fault mode, RESETBMCU is deasserted after the start-up sequence is completed only if no faults occurred during start-up. At any time, if a fault occurs and persists for 1.8 ms, RESETBMCU is asserted LOW. The PF3000 is turned off if the fault persists for more than 100 ms. The PWRON signal can be used to restart the part, though if the fault persists, the sequence described above is repeated. To enter the fault mode, set bit OTP PG EN of register OTP PWRGD EN to "1" during OTP programming.

^{54.} The sense bit, PWRONS, is not debounced and follows the state of the PWRON pin.

6.3.1.4 INTB

INTB is an open drain, active low output. It is asserted when any fault occurs, provided that the fault interrupt is unmasked. INTB is deasserted after the fault interrupt is cleared by software, which requires writing a "1" to the fault interrupt bit.

6.3.1.5 SD_VSEL

SD_VSEL is an input pin that sets the output voltage range of the VCC_SD regulator. When SD_VSEL = HIGH, the VCC_SD regulator operates in the lower output voltage range. When SD_VSEL = LOW, the VCC_SD regulator operates in the higher output voltage range. The SD_VSEL input buffer is powered by the VDDIO supply. When a valid VDDIO voltage is not present, the output of the SD_VSEL buffer defaults to a logic high thus keeping the VCC_SD regulator output in the lower voltage range.

6.3.2 One-time-programmable memory

One-time-programmable memory is used to store key startup parameters and regulators' configuration information. This eliminates the need to set regulator voltage and sequence using external components. The following parameters are programmable in the PF3000.

General: I²C slave address, PWRON pin configuration, RESETBMCU configuration

Buck regulators: Output voltage, single phase or independent mode configuration for SW1A and SW1B regulators, switching frequency, regulator start-up sequence and timing

Boost regulator and LDOs: Output voltage, regulator start-up sequence and timing

The PF3000 starts up based on the contents of the TBBOTP registers. During power up, contents of the OTP memory are loaded on to the TBBOTP registers. There is an optional Try-before-buy mode of operation available which bypasses loading of the OTP memory onto the TBBOTP registers. Instead, regulators directly start up based on the current contents of the TBBOTP registers during this mode of operation. This mode is useful when trying to determine a suitable OTP configuration for the system. TBB mode can also be used in lieu of OTP programming provided a microcontroller can initiate the TBB sequence is available in the system.

6.3.2.1 Register naming convention

Register and bit names for the TBBOTP registers are prefixed with "OTP". This is to differentiate them from "functional registers" which are responsible for real-time control of regulator settings. For example, "OTP_SW1A_VOLT" refers to the TBBOTP register associated with the voltage setting for SW1A regulator. "SW1AVOLT" refers to the functional register which is fed into the SW1A regulator block. During power up, contents of the OTP fuses are copied onto the "OTP_SW1A_VOLT" register which is further copied on to the "SW1AVOLT" register. During normal operation, writes to the "OTP_SW1A_VOLT" register has no effect on the output voltage of the SW1A regulator. Writes to the "SW1AVOLT" register do have an effect.

6.3.2.2 Regulator startup sequence programming

Each regulator has 3-bits or 4-bits allocated to program its start-up time slot from a turn-on event; therefore, each can be placed from position one to seven or one to fifteen in the start-up sequence as shown in Table 37. When the sequence is code is set to 0, the regulator remains off during the startup sequence. It can be enabled using I²C after the start up sequence is completed. The delay between each position can be programmed to be 0.5 ms or 2.0 ms as shown in Table 38. The start-up sequence terminates at the last programmed regulator. RESETBMCU pin is de-asserted HIGH 2.0 ms after the last utilized startup slot.

Table 37. Start-up sequence

| OTP_SWx_SEQ[2:0]/ OTP_V33_SEQ[2:0]/ OTP_VCC_SD_SEQ[2:0] | OTP_VLDOx_SEQ[3:0]/ | Sequence |
|---|---------------------|-------------------|
| 000 | 0000 | Off |
| 001 | 0001 | SEQ_CLK_SPEED * 1 |
| 010 | 0010 | SEQ_CLK_SPEED * 2 |
| 011 | 0011 | SEQ_CLK_SPEED * 3 |
| 100 | 0100 | SEQ_CLK_SPEED * 4 |
| 101 | 0101 | SEQ_CLK_SPEED * 5 |
| 110 | 0110 | SEQ_CLK_SPEED * 6 |

Table 37. Start-up sequence (continued)

| OTP_SWx_SEQ[2:0]/ OTP_V33_SEQ[2:0]/ OTP_VCC_SD_SEQ[2:0] | OTP_VLDOx_SEQ[3:0]/ | Sequence | | | |
|---|---------------------|--------------------|--|--|--|
| 111 | 0111 | SEQ_CLK_SPEED * 7 | | | |
| _ | 1000 | SEQ_CLK_SPEED * 8 | | | |
| _ | 1001 | SEQ_CLK_SPEED * 9 | | | |
| _ | 1010 | SEQ_CLK_SPEED * 10 | | | |
| _ | 1011 | SEQ_CLK_SPEED * 11 | | | |
| _ | 1100 | SEQ_CLK_SPEED * 12 | | | |
| _ | 1101 | SEQ_CLK_SPEED * 13 | | | |
| _ | 1110 SEQ_CLK_SPE | | | | |
| _ | 1111 | SEQ_CLK_SPEED * 15 | | | |

Table 38. Start-up sequence clock speed

| SEQ_CLK_SPEED | Time (μs) |
|---------------|-----------|
| 0 | 500 |
| 1 | 2000 |

6.3.2.3 PWRON pin configuration

The PWRON pin can be configured as either a level sensitive input (PWRON_CFG = 0), or as an edge sensitive input (PWRON_CFG = 1). As a level sensitive input, an active high signal turns on the part and an active low signal turns off the part, or puts it into sleep mode. As an edge sensitive input, such as when connected to a mechanical switch, a falling edge turns on the part and if the switch is held low for greater than or equal to 4.0 seconds, the part turns off or enters sleep mode.

Table 39. PWRON configuration

| PWRON_CFG | Mode | | | |
|-----------|---|--|--|--|
| 0 | PWRON pin HIGH = ON PWRON pin LOW = OFF or sleep mode | | | |
| 1 | PWRON pin pulled LOW momentarily = ON PWRON pin LOW for 4.0 seconds = OFF or sleep mode | | | |

6.3.2.4 I²C address configuration

The I²C device address can be programmed from 0x08 to 0x0F. This allows flexibility to change the I²C address to avoid bus conflicts. Address bit, I2C_SLV_ADDR[3] in OTP_I2C_ADDR register is hard coded to "1" while the lower three LSBs of the I²C address (I2C_SLV_ADDR[2:0]) are programmable as shown in Table 40. The I²C address of the PF3000 immediately changes after write instructions to the OTP_I2C_ADDR register are complete. To continue using the default address of 0x08, set bit 7 (USE_DEFAULT_ADD) of the OTP_I2C_ADDR register.

Table 40. I²C address configuration

| I2C_SLV_ADDR[3] Hard Coded | I2C_SLV_ADDR[2:0] | I ² C Device Address (Hex) |
|-------------------------------|-------------------|---------------------------------------|
| 1 | 000 | 0x08 |
| 1 | 001 | 0x09 |
| 1 | 010 | 0x0A |
| 1 | 011 | 0x0B |
| 1 | 100 | 0x0C |

Table 40. I²C address configuration (continued)

| I2C_SLV_ADDR[3] Hard Coded | I2C_SLV_ADDR[2:0] | I ² C Device Address (Hex) |
|-------------------------------|-------------------|---------------------------------------|
| 1 | 101 | 0x0D |
| 1 | 110 | 0x0E |
| 1 | 111 | 0x0F |

6.3.2.5 Buck regulator soft start ramp rate

The start-up ramp rate ramp rate or soft start ramp rate of buck regulators can be chosen by using the SWDVS_CLK bit during OTP. Table 41 shows the startup ramp rate options for the buck regulators in the PF3000.

Table 41. DVS speed selection for SWx

| SWDVS_CLK | Function |
|-----------|------------------------|
| 0 | 25 mV step each 2.0 μs |
| 1 | 25 mV step each 4.0 μs |

6.3.3 Start-up

Regulators in the PF3000 start up based on the contents of the TBBOTP registers. During cold start, contents from the OTP memory are loaded into the TBBOTP registers when VIN > UVDET irrespective of whether the PMIC is powered using the VIN or the VPWR path. Contents of the TBBOTP registers are reloaded from the fuses during a turn-on event.

The PF3000 is available in a number of pre-programmed flavors to suit a wide variety of system configurations. Refer to Table 42 for programming details of the different flavors. Refer to Section 6.3.2 for a detailed explanation of the OTP block.

Table 42. Start-up configuration (55)

| OTP registers Default configuration All Devices | | Non- programmed | Pre-programmed OTP configuration | | | | | | | |
|---|--|--|---|---|---|---|---|---|---|---|
| | Α0 | A1 | A2 | А3 | A4 | A5 | A6 | A7 | A8 | |
| Default I ² C Address | 0x08 | 0x08 | 0x08 | 0x08 | 80x0 | 0x08 | 0x08 | 0x08 | 80x0 | 0x08 |
| OTP_VSNVS_VOLT | 3.0 V | 1.0 V | 3.0 V | 3.0 V | 3.0 V | 3.0 V | 3.0 V | 3.0 V | 3.0 V | 3.0 V |
| OTP_SW1A_VOLT | 1.15 V | 0.7 V | 1.10 V | 1.10 V | 1.375 V | 1.375 V | 1.375 V | 3.3 V | 3.3 V | 3.3 V |
| OTP_SW1A_SEQ | 1 | OFF | 1 | 1 | 2 | 1 | 1 | 3 | 3 | 3 |
| OTP_SW1B_VOT | 1.15 V | 0.7 V | 1.0 V | 1.0 V | 1.375 V | 1.375 V | 1.375 V | 1.4 V | 1.4 V | 1.4 V |
| OTP_SW1B_SEQ | 1 | OFF | 1 | 1 | 2 | 1 | 1 | 3 | 3 | 3 |
| OTP_SW2_VOLT | 1.8 V | 1.5 V | 1.8 V | 1.8 V | 3.3 V | 3.3 V | 3.15 V | 3.3 V | 3.3 V | 3.3 V |
| OTP_SW2_SEQ | 2 | OFF | 2 | 2 | 4 | 2 | 2 | 3 | 3 | 3 |
| OTP_SW3_VOLT | 1.2 V | 0.9 V | 1.35 V | 1.2 V | 1.35 V | 1.5 V | 1.2 V | 1.2 V | 1.35 V | 1.5 V |
| OTP_SW3_SEQ | 3 | OFF | 5 | 5 | 3 | 3 | 4 | 3 | 3 | 3 |
| OTP_SWBST_VOLT | 5.0 V | 5.0 V | 5.0 V | 5.0 V | 5.0 V | 5.0 V | 5.0 V | 5.0 V | 5.0 V | 5.0 V |
| OTP_SWBST_SEQ | OFF | OFF | OFF | OFF | OFF | OFF | 6 | OFF | OFF | OFF |
| OTP_VLDO1_VOLT | 1.8 V | 1.8 V | 1.8 V | 1.8 V | 3.3 V | 1.8 V | 1.8 V | 3.3 V | 3.3 V | 3.3 V |
| OTP_VLDO1_SEQ | 2 | OFF | 4 | 4 | OFF | OFF | 3 | 3 | 3 | 3 |
| OTP_VLDO2_VOLT | 1.2 V | 0.8 V | 1.5 V | 1.5 V | 1.5 V | 1.2 V | 1.5 V | 1.5 V | 1.5 V | 1.5 V |
| OTP_VLDO2_SEQ | OFF | OFF | 4 | 4 | OFF | 3 | OFF | OFF | OFF | OFF |
| OTP_VLDO3_VOLT | 1.8 V | 1.8 V | 3.3 V | 3.3 V | 2.5 V | 1.8 V | 3.1 V | 1.8 V | 1.8 V | 1.8 V |
| OTP_VLDO3_SEQ | 2 | OFF | 3 | 3 | OFF | OFF | 2 | 3 | 3 | 3 |
| OTP_VLDO4_VOLT | 1.8 V | 1.8 V | 3.3 V | 3.3 V | 1.8 V |
| OTP_VLDO4_SEQ | OFF | OFF | 3 | 3 | 4 | 3 | 3 | 3 | 3 | 3 |
| OTP_V33_VOLT | 3.15 V | 2.85 V | 3.3 V | 3.3 V | 3.0 V | 3.3 V | 2.85 V | 3.3 V | 3.3 V | 3.3 V |
| OTP_V33_SEQ | 2 | OFF | 3 | 3 | 1 | 2 | OFF | 2 | 2 | 2 |
| OTP_VCC_SD_VOLT | 3.15 V/1.80 V | 2.85 V/1.80 V | 3.3 V/1.85 V | 3.3 V/1.85 V | 3.3 V/1.85 V | 3.0 V/1.80 V | 3.15 V/1.80 V | 3.3 V/1.85 V | 3.3 V/1.85 V | 3.3 V/1.85 V |
| OTP_VCC_SD_SEQ | 3 | OFF | 4 | 4 | 5 | 3 | 2 | 3 | 3 | 3 |
| OTP_SEQ_CLK_SPEED | 500 μs | 500 μs | 2000 μs | 2000 μs | 500 µs | 2000 µs | 2000 µs | 2000 µs | 2000 µs | 2000 µs |
| OTP_SWDVS_CLK | 6.25 mV/μs | 12.5 mV/μs | 12.5 mV/ µs | 12.5 mV/µs | 6.25 mV/μs | 12.5 mV/µs | 12.5 mV/µs | 12.5 mV/μs | 12.5 mV/μs | 12.5 mV/μs |
| OTP_PWRON_CFG | Level sensitive | Level sensitive | Level sensitive | Level sensitive | Level sensitive | Level sensitive | Level sensitive | Level sensitive | Level sensitive | Level sensitive |
| OTP_SW1_CONFIG | SW1A, SW1B Independent Mode, 2.0 MHz | SW1A, SW1B Independent Mode, 1.0 MHz | SW1A, SW1B Independe nt Mode, 2.0 MHz |
| OTP_SW2_FREQ | 2.0 MHz | 1.0 MHz | 2.0 MHz | 2.0 MHz | 2.0 MHz | 2.0 MHz | 2.0 MHz | 2.0 MHz | 2.0 MHz | 2.0 MHz |
| OTP_SW3_FREQ | 2.0 MHz | 1.0 MHz | 2.0 MHz | 2.0 MHz | 2.0 MHz | 2.0 MHz | 2.0 MHz | 2.0 MHz | 2.0 MHz | 2.0 MHz |
| OTP_PG_EN | RESETBMCU in Default Mode | RESETBMCU in Default Mode | RESETBM CU in Default Mode |

Notes

^{55.} This table specifies the default output voltage of the LDOs and SWx after start-up and/or when the LDOs and SWx are enabled. VREFDDR_SEQ is internally fixed to be same as SW3_SEQ. VCC_SD voltage depends on the state of the SD_VSEL pin.

6.3.3.1 Start-up timing diagram

The startup timing of the regulators is programmable through OTP and seq_clk_speed. Figure 6 shows the startup timing of the regulators as determined by their OTP sequence. The trimmed 32 kHz clock controls all the start up timing.

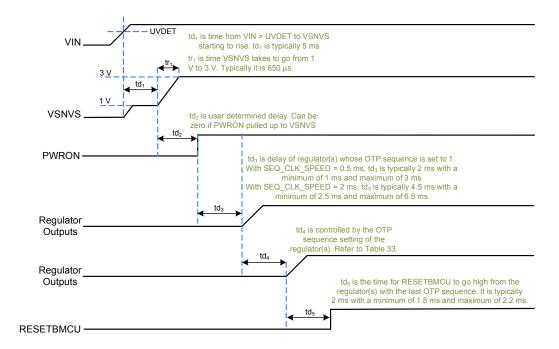


Figure 6. Startup timing diagram

6.3.4 16 MHz and 32 kHz clocks

The PF3000 incorporates two clocks: a trimmed 16 MHz RC oscillator and an untrimmed 32 kHz RC oscillator. The 32 kHz untrimmed clock is only used in the following conditions:

- V_{IN} < UVDET
- · All regulators are in sleep mode
- · All regulators are in PFM switching mode

A 32 kHz clock, derived from the 16 MHz trimmed clock, is used when accurate timing is needed under the following conditions:

- During start-up, V_{IN} > UVDET
- PWRON_CFG = 1, for power button debounce timing

When the 16 MHz is active in the ON mode, the debounce times are referenced to the 32 kHz derived from the 16 MHz clock. The exceptions are the LOWVINI and PWRONI interrupts, which are referenced to the 32 kHz untrimmed clock. Switching frequency of the switching regulators is derived from the trimmed 16 MHz clock.

The 16 MHz clock and hence the switching frequency of the regulators, can be adjusted to improve the noise integrity of the system. By changing the factory trim values of the 16 MHz clock, the user may add an offset as small as $\pm 3.0\%$ of the nominal frequency. Contact your NXP representative for detailed information on this feature.

6.3.5 Optional front-end input LDO regulator

6.3.5.1 LDO regulator description

This section describes the optional front-end LDO regulator provided by the PF3000 in order to facilitate the operation with supply voltages higher than 4.5 V and up to 5.5 V.

For non-battery operated applications, when the input supply voltage exceeds 4.5 V, the front-end LDO can be activated by populating the external PMOS pass FET MP1 in Figure 7 and connecting the VPWR pin to the main supply. Under this condition, the LDO control block self-starts with a local bandgap reference. When the VIN pin reaches UVDET rising threshold, the reference is switched to the main trimmed bandgap reference to maintain the required VIN accuracy. In applications using an input supply voltage of 4.5 V or lower, the PMOS pass FET should not be populated, VPWR pin should be grounded externally and the VIN pin should be used instead as the main supply input pin. The input pins of the switching regulators should always be connected to the VIN net.

The main components of the LDO regulator are an external power P-channel MOSFET and an internal differential error amplifier. One input of the amplifier monitors a fraction of the output voltage at VIN determined by the resistor ratio of R1 and R2 as shown in <u>Figure 7</u>. The second input to the differential amplifier is from a stable bandgap voltage reference. If the output voltage rises too high relative to the reference voltage, the gate voltage of the power FET is changed to maintain a constant output voltage.

In order to maintain the power consumption at reasonable levels during PF3000 standby and sleep modes, the LDO circuit enters low-power mode of operation using an embedded pass FET while the external pass FET is kept off. When the STBY_LOWPOWER_B bit in register LDOGCTL is set the activation of the low-power mode during IC standby mode is disabled; however the LDO low-power mode is always activated during the IC sleep mode. Moreover, during IC Off mode, an even simpler internal circuit is used to further reduce the power consumption. Refer to Modes of operation for different modes of operation of the IC.

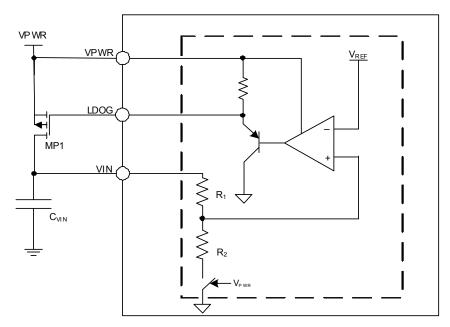


Figure 7. Front-end LDO block diagram

6.3.5.2 Undervoltage/short-circuit and overvoltage detection

Short-circuit to GND at VIN is detected using an under voltage monitor at VIN that would sense excessive droop on the VIN line and consequently turn off (disable) the external PMOS pass FET. Overvoltage at VPWR is detected if VPWR exceeds the V_{PWROV} threshold (typically 6.0 V). Upon the detection of an overvoltage event an interrupt is generated and bit 2 is set in INTSTAT3 register. The INTB pin is pulled low if the VPWROVM mask bit is cleared. The interrupt is filtered using a 122 μ s debouncing circuit. The VPWROV interrupt is not asserted if the overvoltage event occurs during start up. The VPWROVS bit can be read using I²C to detect an overvoltage condition.

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6.3.5.3 External components

Table 43 lists the typical component values for the general purpose LDO regulators.

Table 43. Input LDO external components

| Component | Value |
|--------------------------------------|---|
| Minimum output capacitor on VIN rail | 100 μF ⁽⁵⁶⁾ |
| MP1 | Fairchild FDMA908PZ, Vishay SiA447DJ, or comparable |

Notes

56. Use X5R/X7R ceramic capacitors with a voltage rating at least two times the nominal voltage. The 100 μF capacitance is the total capacitance on the VIN rail including the capacitance at the various regulator inputs. For example, 2 x 22 μF capacitors can be used along with 10 μF capacitors at all the SWx and LDOx inputs to achieve a total of 100 μF capacitance.

6.3.6 Internal core voltages

All regulators use the main bandgap as the reference. The main bandgap is bypassed with a capacitor at VCOREREF. VCOREDIG is a 1.5 V regulator that powers all the digital logic in the PF3000. VCOREDIG is regulated at 1.28 V in Off and coin cell modes. The VCORE supply is used to bias internal analog rails and the OTP fuses. No external DC loading is allowed on VCORE, VCOREDIG, or VCOREREF. VCOREDIG is kept powered as long as there is a valid supply and/or valid coin cell.

6.3.7 VREFDDR voltage reference

VREFDDR is an internal PMOS half supply voltage follower capable of supplying up to 10 mA. The output voltage is at one half the input voltage. It is typically used as the reference voltage for DDR memories. A filtered resistor divider is utilized to create a low frequency pole. This divider then uses a voltage follower to drive the load.

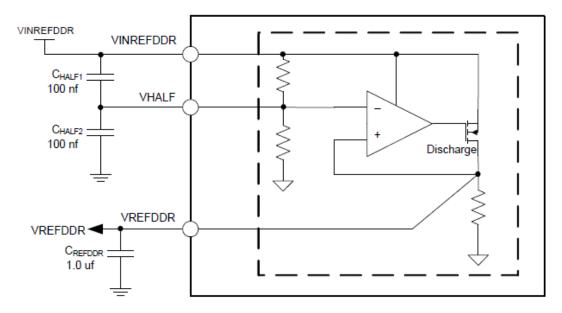


Figure 8. VREFDDR block diagram

6.3.7.1 VREFDDR external components

Table 44. VREFDDR external components (57)

| Capacitor | Capacitance (μF) |
|-------------------------|------------------|
| VINREFDDR (58) to VHALF | 0.1 |
| VHALF to GND | 0.1 |
| VREFDDR | 1.0 |

Notes

- 57. Use X5R or X7R capacitors.
- 58. VINREFDDR to GND, 1.0 μF minimum capacitance is provided by buck regulator output.

6.3.8 Buck regulators

The PF3000 integrates four independent buck regulators: SW1A, SW1B, SW2, and SW3. Regulators SW1A and SW1B regulators can be configured as a single regulator through OTP. Output of the buck regulators during start up is programmable through OTP. Each regulator has associated registers that control its output voltage during On, standby, and sleep modes. During start-up, contents of the OTP_SWx_VOLT register is copied onto the SWxVOLT[4:0], SWxSTBY[4:0] and SWxOFF[4:0]. After boot up, contents of the SWxVOLT, SWxSTBY and SWxOFF registers can be set through I²C to set the output voltage during On, standby, and sleep modes respectively.

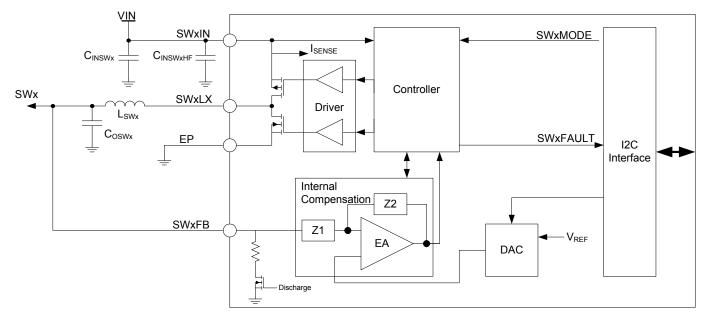


Figure 9. Generic SWx block diagram

Table 45. SWx regulators external components

| Components | Description | Values |
|------------|--------------------------------|---|
| CINSWx | SWx input capacitor | 4.7 μF |
| CINSWxHF | SWx decoupling input capacitor | 0.1 μF |
| COSWx | SWx output capacitor | 2 x 22 μF (10 V or higher voltage rated capacitors) or 3 x 22 μF (6.3 V rated capacitors) |
| LSWx | SWx inductor | 1.5 μΗ |

Use X5R or X7R capacitors with voltage rating at least two times the nominal voltage.

6.3.8.1 Switching modes

To improve system efficiency the buck regulators can operate in different switching modes. Changing between switching modes can occur by any of the following means: I²C programming, exiting/entering the standby mode, exiting/entering sleep mode, and load current variation. Available switching modes for buck regulators are presented in Table 45.

Table 46. Switching mode description

| Mode | Description | |
|------|--|--|
| OFF | The regulator is switched off and the output voltage is discharged using an internal resistor | |
| PFM | In this mode, the regulator operates in forced PFM mode. The main error amplifier is turned off and a hysteretic comparator is used to regulate output voltage. Use this mode for load currents less than 50 mA. | |
| PWM | In this mode, the regulator operates in forced PWM mode. | |
| APS | In this mode, the regulator operates in pulse skipping mode at light loads and switches over to PWM modes for heavier load conditions. This is the default mode in which the regulators power up during a turn-on event. | |

During soft-start of the buck regulators, the controller transitions through the PFM, APS, and PWM switching modes. 3.0 ms after the output voltage reaches regulation, the controller transitions to the selected switching mode. Depending on the particular switching mode selected, additional ripple may be observed on the output voltage rail as the controller transitions between switching modes. The operating mode of the regulator in On and standby modes is controlled using the SWxMODE[3:0] bits associated with each regulator. Table 46 summarizes the buck regulator programmability for normal and standby modes.

Table 47. Regulator mode control

| SWxMODE[3:0] | Normal mode | Standby mode |
|----------------|-------------------|--------------|
| 0000 | Off | Off |
| 0001 | PWM | Off |
| 0010 | Reserved | Reserved |
| 0011 | PFM | Off |
| 0100 | APS | Off |
| 0101 | PWM | PWM |
| 0110 | PWM | APS |
| 0111 | Reserved | Reserved |
| 1000 (default) | APS | APS |
| 1001 | Reserved | Reserved |
| 1010 | Reserved | Reserved |
| 1011 | Reserved | Reserved |
| 1100 | APS | PFM |
| 1101 | PWM | PFM |
| 1110 | Reserved | Reserved |
| 1111 | Reserved Reserved | |

Transitioning between normal and standby modes can affect a change in switching modes as well as output voltage. When in standby mode, the regulator outputs the voltage programmed in its standby voltage register and operates in the mode selected by the SWxMODE[3:0] bits. Upon exiting standby mode, the regulator returns to its normal switching mode and its output voltage programmed in its voltage register.

Any regulators whose SWxOMODE bit is set to "1" enters sleep mode if a PWRON turn-off event occurs, and any regulator whose SWxOMODE bit is set to "0" is turned off. In sleep mode, the regulator outputs the voltage programmed in SWxOFF registers and operates in the PFM mode. The regulator exits the sleep mode when a turn-on event occurs. Any regulator whose SWxOMODE bit is set to "1" remains on and changes to its normal configuration settings when exiting the Sleep state to the ON state. Any regulator whose SWxOMODE bit is set to "0" is powered up with the same delay in the start-up sequence as when powering ON from Off. At this point, the regulator returns to its default ON state output voltage and switch mode settings.

When sleep mode is activated by the SWxOMODE bit, the regulator uses the set point as programmed by SW1xOFF[4:0] for SW1A/B and by SW2OFF[2:0] for SW2, and SW3OFF[3:0] for SW3.

6.3.8.2 Dynamic voltage scaling

To reduce overall power consumption, processor core voltages can be varied depending on the mode or activity level of the processor.

- 1. Normal operation: The output voltage is selected by I²C bits SW1x[4:0] for SW1A/B and SW2[2:0] for SW2, and SW3[3:0] for SW3. A voltage transition initiated by I²C is governed by the DVS stepping rates shown in Table 48.
- 2. Standby mode: The output voltage can be selected by I²C bits SW1xSTBY[4:0] for SW1A/B and by bits SW2STBY[2:0] for SW2, and SW3STBY[3:0] for SW3. Voltage transitions initiated by a Standby event are governed by the DVS stepping rates shown in Table 48.
- 3. Sleep mode: The output voltage can be higher or lower than in normal operation, but is typically selected to be the lowest state retention voltage of a given processor; it is selected by I²C bits SW1xOFF[4:0] for SW1A/B and by bits SW2OFF[2:0] for SW2, and SW3OFF[3:0] for SW3. Voltage transitions initiated by a turn-off event are governed by the DVS stepping rates shown in Table 48.

Table 48. DVS speed selection for SWx

| SWxDVSSPEED | Function |
|-------------|------------------------|
| 0 | 25 mV step each 2.0 μs |
| 1 | 25 mV step each 4.0 μs |

The regulators have a strong sourcing capability and sinking capability in PWM mode, therefore the fastest rising and falling slopes are determined by the regulator in PWM mode. However, if the regulators are programmed in PFM or APS mode during a DVS transition, the falling slope can be influenced by the load. Additionally, as the current capability in PFM mode is reduced, controlled DVS transitions in PFM mode could be affected. Critically timed DVS transitions are best assured with PWM mode operation.

<u>Figure 10</u> shows the general behavior for the regulators when initiated with I²C programming, or standby control. During the DVS period the overcurrent condition on the regulator should be masked.

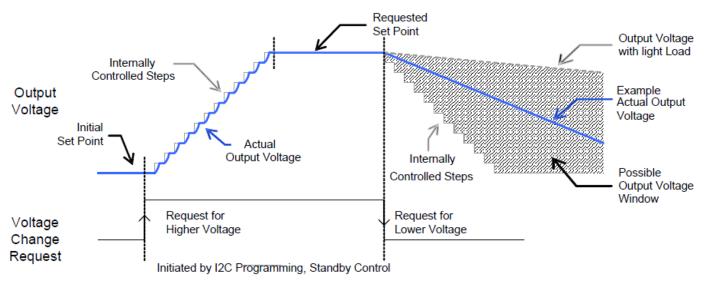


Figure 10. Voltage stepping with DVS

Note: In SW1A independent and SW1AB single phase modes, DVS to and from the 1.8 V and 3.3 V output voltage settings is not allowed.

6.3.8.3 Regulator phase clock

The SWxPHASE[1:0] bits select the phase of the regulator clock as shown in Table 49. By default, each regulator is initialized at 90 ° out of phase with respect to each other. For example, SW1x is set to 0 °, SW2 is set to 90 °, and SW3 is set to 180 ° by default at power up.

Table 49. Regulator phase clock selection

| SWxPHASE[1:0] | Phase of clock sent to regulator (degrees) |
|---------------|--|
| 00 | 0 |
| 01 | 90 |
| 10 | 90 |
| 11 | 270 |

The SWxFREQ[1:0] register is used to set the desired switching frequency for each one of the buck regulators. Table 51 shows the selectable options for SWxFREQ[1:0]. For each frequency, all phases are available, this allows regulators operating at different frequencies to have different relative switching phases. However, not all combinations are practical. For example, 2.0 MHz, 90 ° and 4.0 MHz, 180 ° are the same in terms of phasing. Table 50 shows the optimum phasing when using more than one switching frequency.

Table 50. Optimum phasing

| Frequencies | Optimum Phasing |
|-------------|-----------------|
| 1.0 MHz | 0° |
| 2.0 MHz | 180° |
| 1.0 MHz | 0° |
| 4.0 MHz | 180° |
| 2.0 MHz | 0° |
| 4.0 MHz | 180° |
| 1.0 MHz | 0° |
| 2.0 MHz | 90° |
| 4.0 MHz | 90° |

Table 51. Regulator frequency configuration

| SWxFREQ[1:0] | Frequency |
|--------------|-------------------|
| 00 | 1.0 MHz |
| 01 | 2.0 MHz (default) |
| 10 | 4.0 MHz |
| 11 | Reserved |

6.3.8.4 SW1A/B

SW1A/B are 1 to 2.75 A buck regulators that can be configured in various phasing schemes, depending on the desired cost/performance trade-offs. The following configurations are available:

- · SW1A/B single phase with one inductor
- · SW1A in independent with one inductor and SW1B in independent mode with a second inductor

The desired configuration is programmed by OTP by using OTP_SW1_CONFIG[1:0] bits in the register map, as shown below in Table 52.

Table 52. SW1 configuration

| OTP_SW1_CONFIG[1:0] | Description |
|---------------------|--|
| 00 | Unused |
| 01 | A/B Single Phase |
| 10 | Unused |
| 11 | A Independent mode B Independent mode |

6.3.8.5 SW1A/B single phase

In this configuration, the phases SW1ALX, and SW1BLX, are connected together to a single inductor, thus, providing up to 2.75 A current capability for high current applications. The feedback and all other controls are accomplished by use of pin SW1AFB and SW1A control registers, respectively. However, the same configuration settings for frequency, phase, and DVS speed setting on SW1B registers should be used. The SW1BFB pin should be left floating in this configuration.

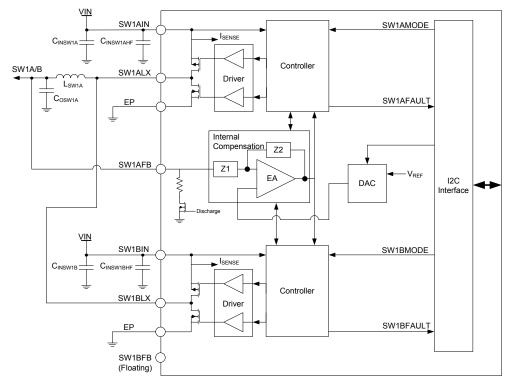


Figure 11. SW1A/B single phase diagram

6.3.8.6 SW1A - SW1B

Independent mode In this configuration, SW1A is connected as an independent output with a single inductor, while SW1B is used as another independent output, using another inductor and configuration parameters. They can be operated with a different voltage set point for normal, standby, and sleep modes, as well as switching mode selection and on/off control.

6.3.8.7 SW1A/B setup and control registers

SW1A and SW1AB output voltages are programmable from 0.700 V to 1.425 V in steps of 25 mV. They can additionally be programmed at 1.8 V or 3.3 V. SW1B output voltage is programmable from 0.700 V to 1.475 V in steps of 25 mV. The output voltage set point is independently programmed for normal, standby, and sleep mode by setting the SW1x[4:0], SW1xSTBY[4:0], and SW1xOFF[4:0] bits respectively. Table 53 shows the output voltage coding for SW1A, SW1B or SW1A/B. Values shown in Table 53 are also to be used during OTP programming by setting the OTP_SW1A_VOLT and OTP_SW1B_VOLT registers appropriately.

Table 53. SW1A/B output voltage configuration

| Set point | SW1x[4:0] SW1xSTBY[4:0] SW1xOFF[4:0] | SW1x output (V) | Set point | SW1x[4:0] SW1xSTBY[4:0] SW1xOFF[4:0] | SW1x output (V) |
|-----------|--|-----------------|-----------|--|-----------------------------------|
| 0 | 00000 | 0.700 | 16 | 10000 | 1.100 |
| 1 | 00001 | 0.725 | 17 | 10001 | 1.125 |
| 2 | 00010 | 0.750 | 18 | 10010 | 1.150 |
| 3 | 00011 | 0.775 | 19 | 10011 | 1.175 |
| 4 | 00100 | 0.800 | 20 | 10100 | 1.200 |
| 5 | 00101 | 0.825 | 21 | 10101 | 1.225 |
| 6 | 00110 | 0.850 | 22 | 10110 | 1.250 |
| 7 | 00111 | 0.875 | 23 | 10111 | 1.275 |
| 8 | 01000 | 0.900 | 24 | 11000 | 1.300 |
| 9 | 01001 | 0.925 | 25 | 11001 | 1.325 |
| 10 | 01010 | 0.950 | 26 | 11010 | 1.350 |
| 11 | 01011 | 0.975 | 27 | 11011 | 1.375 |
| 12 | 01100 | 1.000 | 28 | 11100 | 1.400 |
| 13 | 01101 | 1.025 | 29 | 11101 | 1.425 |
| 14 | 01110 | 1.050 | 30 | 11110 | 1.450 (SW1B), 1.8 (SW1A/SW1AB) |
| 15 | 01111 | 1.075 | 31 | 11111 | 1.475 (SW1B), 3.3 (SW1A/SW1AB) |

Table 54 provides a list of registers used to configure and operate SW1A/B regulator(s).

Table 54. SW1A/B register summary

| Register | Address | Output |
|----------|---------|---|
| SW1AVOLT | 0x20 | SW1A output voltage set point in normal operation |
| SW1ASTBY | 0x21 | SW1A output voltage set point on standby |
| SW1AOFF | 0x22 | SW1A output voltage set point on sleep |
| SW1AMODE | 0x23 | SW1A switching mode selector register |
| SW1ACONF | 0x24 | SW1A DVS, phase, and frequency configuration |
| SW1BVOLT | 0x2E | SW1B output voltage set point in normal operation |
| SW1BSTBY | 0x2F | SW1B output voltage set point in standby |
| SW1BOFF | 0x30 | SW1B output voltage set point in sleep |
| SW1BMODE | 0x31 | SW1B switching mode selector register |
| SW1BCONF | 0x32 | SW1B DVS, phase, and frequency configuration |

6.3.8.8 SW2 setup and control registers

SW2 is a single phase, 1.25 A rated buck regulator. SW2 output voltage is programmable from 1.500 V to 1.850 V in 50 mV steps if the OTP_SW2_HI bit is low or from 2.500 V to 3.300 V in 150 mV steps if the bit OTP_SW2_HI is set high. During normal operation, output voltage of the SW2 regulator can be changed through I²C only within the range set by the OTP_SW2_HI bit. The output voltage set point is independently programmed for normal, standby, and sleep mode by setting the SW2[2:0], SW2STBY[2:0] and SW2OFF[2:0] bits, respectively. Table 55 shows the output voltage coding valid for SW2.

Table 55. SW2 output voltage configuration

| Low output voltage range (OTP_SW2_HI= 0) | | High output voltage range (OTP_SW2_HI=1) | |
|--|------------|---|------------|
| SW2[2:0] SW2STBY[2:0] SW2OFF[2:0] | SW2 output | SW2[2:0] SW2STBY[2:0] SW2OFF[2:0] | SW2 output |
| 000 | 1.500 | 000 | 2.500 |
| 001 | 1.550 | 001 | 2.800 |
| 010 | 1.600 | 010 | 2.850 |
| 011 | 1.650 | 011 | 3.000 |
| 100 | 1.700 | 100 | 3.100 |
| 101 | 1.750 | 101 | 3.150 |
| 110 | 1.800 | 110 | 3.200 |
| 111 | 1.850 | 111 | 3.300 |

Setup and control of SW2 is done through the I²C registers listed in Table 56.

Table 56. SW2 register summary

| Register | Address | Description |
|----------|---------|---|
| SW2VOLT | 0x35 | Output voltage set point on normal operation |
| SW2STBY | 0x36 | Output voltage set point on Standby |
| SW2OFF | 0x37 | Output voltage set point on Sleep |
| SW2MODE | 0x38 | Switching mode selector register |
| SW2CONF | 0x39 | DVS, phase, frequency, and ILIM configuration |

6.3.8.9 SW3 setup and control registers

SW3 output voltage is programmable from 0.90 V to 1.65 V in 50 mV steps to support different types of DDR memory as listed in Table 57.

Table 57. SW3 output voltage configuration

| SW3[3:0] | SW3 Output (V) | SW3[3:0] | SW3 Output (V) |
|----------|----------------|----------|----------------|
| 0000 | 0.90 | 1000 | 1.30 |
| 0001 | 0.95 | 1001 | 1.35 |
| 0010 | 1.00 | 1010 | 1.40 |
| 0011 | 1.05 | 1011 | 1.45 |
| 0100 | 1.10 | 1100 | 1.50 |
| 0101 | 1.15 | 1101 | 1.55 |
| 0110 | 1.20 | 1110 | 1.60 |
| 0111 | 1.25 | 1111 | 1.65 |

Table 58 provides a list of registers used to configure and operate SW3.

Table 58. SW3 register summary

| Register | Address | Output | |
|----------|---------|--|--|
| SW3VOLT | 0x3C | SW3 output voltage set point on normal operation | |
| SW3STBY | 0x3D | SW3 output voltage set point on Standby | |
| SW3OFF | 0x3E | SW3 output voltage set point on Sleep | |
| SW3MODE | 0x3F | SW3 switching mode selector register | |
| SW3CONF | 0x40 | SW3 DVS, phase, frequency and ILIM configuration | |

6.3.9 Boost regulator

SWBST is a boost regulator with a programmable output from 5.0 V to 5.15 V. SWBST can supply the VUSB regulator for the USB PHY in OTG mode, as well as the VBUS voltage. Note that the parasitic leakage path for a boost regulator causes the SWBSTOUT and SWBSTFB voltage to be a Schottky drop below the input voltage whenever SWBST is disabled. A load switch is recommended on the output path to isolate the output for applications where this is not desired. The switching NMOS transistor is integrated on-chip. Figure 12 shows the block diagram and component connection for the boost regulator.

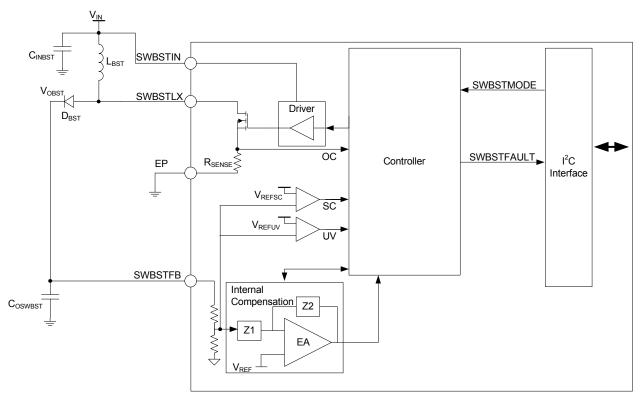


Figure 12. Boost regulator architecture

6.3.9.1 SWBST setup and control

Boost regulator control is done through a single register SWBSTCTL described in Table 59. SWBST is included in the power-up sequence if its OTP power-up timing bits, OTP SWBST SEQ[2:0], are not all zeros.

Table 59. Register SWBSTCTL - ADDR 0x66

| Name | Bit # | R/W | Default | Description |
|----------------|-------|-----|---------|---|
| SWBST1VOLT | 1:0 | R/W | 0b00 | Set the output voltage for SWBST 00 = 5.000 V 01 = 5.050 V 10 = 5.100 V 11 = 5.150 V |
| SWBST1MODE | 3:2 | R | 0b10 | Set the switching mode on normal operation 00 = OFF 01 = PFM 10 = Auto (Default) (59) 11 = APS |
| Unused | 4 | - | 0b0 | Unused |
| SWBST1STBYMODE | 6:5 | R/W | 0b10 | Set the switching mode on standby $00 = OFF$ $01 = PFM$ $10 = Auto \ (Default)^{(59)}$ $11 = APS$ |
| Unused | 7 | _ | 0b0 | Unused |

Notes

6.3.9.2 SWBST external components

Table 60. SWBST external component requirements

| Components | Description | Values |
|---------------------------|----------------------------------|----------------------|
| C _{INBST} (60) | SWBST input capacitor | 10 μF |
| C _{INBSTHF} (60) | SWBST decoupling input capacitor | 0.1 μF |
| C _{OSWBST} (60) | SWBST output capacitor | 2 x 22 μF |
| L _{SBST} | SWBST inductor | 2.2 μΗ |
| D _{BST} | SWBST boost diode | 1.0 A, 20 V Schottky |

Notes

60. Use X5R or X7R capacitors.

^{59.} In auto mode, the controller automatically switches between PFM and APS modes depending on the load current. Regulator switches in auto mode if enabled in the startup sequence.

6.3.10 LDO Regulators Description

This section describes the LDO regulators provided by the PF3000. All regulators use the main bandgap as reference. When a regulator is disabled, the output is discharged by an internal pull-down resistor.

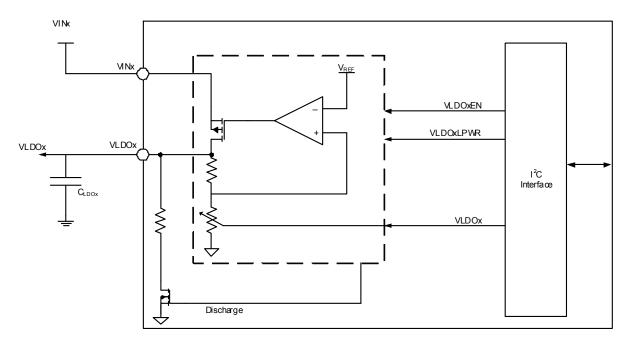


Figure 13. General LDO block diagram

6.3.10.1 External components

Table 61 lists the typical component values for the general purpose LDO regulators.

Table 61. LDO External Components

| Regulator | Output capacitor (μF) ⁽⁶¹⁾ |
|-----------|---------------------------------------|
| VLDO1 | 2.2 |
| VLDO2 | 4.7 |
| VLDO3 | 2.2 |
| VLDO4 | 4.7 |
| V33 | 4.7 |
| VCC_SD | 2.2 |

Notes

61. Use X5R/X7R ceramic capacitors.

6.3.10.2 Current limit protection

All the LDO regulators in the PF3000 have current limit protection. In the event of an overload condition, the regulators transitions from a voltage regulator to a current regulator that regulates output current per the current limit threshold.

Additionally, if the REGSCPEN bit in Table 124 is set, the LDO is turned off if the current limit event lasts for more than 8.0 ms. The LDO is disabled by resetting its VLDOxEN bit, while at the same time, an interrupt VLDOxFAULTI is generated to flag the fault to the system processor. The VLDOxFAULTI interrupt is maskable through the VLDOxFAULTM mask bit. By default, the REGSCPEN is not set; therefore, at start-up none of the regulators is disabled if an overloaded condition occurs. A fault interrupt, VLDOxFAULTI, is generated in an overload condition regardless of the state of the REGSCPEN bit.

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6.3.10.3 LDO voltage control

Each LDO is fully controlled through its respective VLDOxCTL register. This register enables the user to set the LDO output voltage according to Table 62 for VLDO1 and VLDO2; and uses the voltage set point on Table 63 for VLDO3 and VLDO4. Table 64 lists the voltage set points for the V33 LDO and Table 65 provides the output voltage set points for the VCC_SD LDO based on SD_VSEL control signal. During power-up, contents of the OTP_VLDO_VOLT register is copied to the VLDOxCTL registers.

Table 62. VLDO1, VLDO2 output voltage configuration

| VLDO1[3:0] VLDO2[3:0] | VLDO1 Output (V) | VLDO2 Output (V) |
|--------------------------|------------------|------------------|
| 0000 | 1.80 | 0.80 |
| 0001 | 1.90 | 0.85 |
| 0010 | 2.00 | 0.90 |
| 0011 | 2.10 | 0.95 |
| 0100 | 2.20 | 1.00 |
| 0101 | 2.30 | 1.05 |
| 0110 | 2.40 | 1.10 |
| 0111 | 2.50 | 1.15 |
| 1000 | 2.60 | 1.20 |
| 1001 | 2.70 | 1.25 |
| 1010 | 2.80 | 1.30 |
| 1011 | 2.90 | 1.35 |
| 1100 | 3.00 | 1.40 |
| 1101 | 3.10 | 1.45 |
| 1110 | 3.20 | 1.50 |
| 1111 | 3.30 | 1.55 |

Table 63. VLDO3, VLDO4 output voltage configuration

| VLDO3[3:0] VLDO4[3:0] | VLDO3 or VLDO4 output (V) |
|--------------------------|---------------------------|
| 0000 | 1.80 |
| 0001 | 1.90 |
| 0010 | 2.00 |
| 0011 | 2.10 |
| 0100 | 2.20 |
| 0101 | 2.30 |
| 0110 | 2.40 |
| 0111 | 2.50 |
| 1000 | 2.60 |
| 1001 | 2.70 |
| 1010 | 2.80 |
| 1011 | 2.90 |
| 1100 | 3.00 |
| 1101 | 3.10 |
| 1110 | 3.20 |
| 1111 | 3.30 |

Table 64. V33 output voltage configuration

| V33[1:0] | V33 Output (V) |
|----------|----------------|
| 00 | 2.85 |
| 01 | 3.00 |
| 10 | 3.15 |
| 11 | 3.30 |

Table 65. VCC SD output voltage configuration

| VCC_SD[1:0] | VCC_SD output (V) VSD_VSEL= 0 | VCC_SD output (V) VSD_VSEL= 1 |
|-------------|-------------------------------|-------------------------------|
| 00 | 2.85 | 1.80 |
| 01 | 3.00 | 1.80 |
| 10 | 3.15 | 1.80 |
| 11 | 3.30 | 1.85 |

Along with the output voltage configuration, the LDOs can be enabled or disabled at anytime during normal mode operation, as well as programmed to stay "ON" or be disabled when the PMIC enters standby mode. Each regulator has associated I²C bits for this. Table 66 presents a summary of all valid combinations of the control bits on VLDOxCTL register and the expected behavior of the LDO output.

Table 66. LDO control

| VLDOxEN/ V33EN/ VCC_SDEN | VLDOxLPWR/ V33LPWR/ VCC_SDLPWR | VLDOxSTBY/ V33STBY/ VCC_SDSTBY | STANDBY (62) | VLDOxOUT |
|--------------------------------|--------------------------------------|--------------------------------------|--------------|-----------|
| 0 | Х | Х | Х | Off |
| 1 | 0 | 0 | Х | On |
| 1 | 1 | 0 | Х | Low Power |
| 1 | Х | 1 | 0 | On |
| 1 | 0 | 1 | 1 | Off |
| 1 | 1 | 1 | 1 | Low Power |

Notes

62. STANDBY refers to a standby event as described earlier.

6.3.11 VSNVS LDO/switch

VSNVS powers the low-power, SNVS/RTC domain on the processor. It derives its power from either VIN, or coin cell, and cannot be disabled. When powered by both, V_{IN} takes precedence when above the appropriate comparator threshold. When powered by V_{IN} , VSNVS is an LDO capable of supplying 3.0 V. When powered by coin cell, the VSNVS output tracks the coin cell voltage by means of a switch, whose maximum resistance is 100 Ω . In this case, the V_{SNVS} voltage is simply the coin cell voltage minus the voltage drop across the switch, which is 100 mV at a rated maximum load current of 1000 μ A.

When the coin cell is applied for the very first time, VSNVS outputs 1.0 V. Only when V_{IN} is applied thereafter does V_{SNVS} transition to its default value. Upon subsequent removal of V_{IN} , with the coin cell attached, V_{SNVS} changes configuration from an LDO to a switch, provided certain conditions are met as described in Table 67.

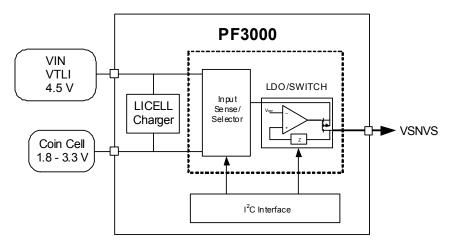


Figure 14. VSNVS supply switch architecture

Table 67 provides a summary of the V_{SNVS} operation at different input voltage V_{IN} and with or without coin cell connected to the system.

Table 67. SNVS modes of operation

| VSNVSVOLT[2:0] | VIN | MODE |
|----------------|--------|------------------|
| 110 | > VTH1 | VIN LDO 3.0 V |
| 110 | < VTL1 | Coin cell switch |

6.3.11.1 VSNVS control

The V_{SNVS} output level is configured through the VSNVSVOLT[2:0] bits on VSNVSCTL register as shown in table Table 68.

Table 68. Register VSNVSCTL - ADDR 0x6B

| Name | Bit# | R/W | Default | Description |
|-----------|------|-----|---------|--|
| VSNVSVOLT | 2:0 | R/W | 0Ь000 | Configures VSNVS output voltage. (63) 000 = RSVD 001 = RSVD 010 = RSVD 011 = RSVD 100 = RSVD 101 = RSVD 101 = RSVD 111 = RSVD 110 = 3.0 V (default) 111 = RSVD |
| Unused | 7:3 | - | 0b00000 | Unused |

Notes

63. Only valid when a valid input voltage is present.

6.3.11.2 VSNVS external components

Table 69. VSNVS external components

| Capacitor | Value (μF) |
|-----------|------------|
| VSNVS | 0.47 |

6.3.11.3 Coin cell battery backup

The LICELL pin provides for a connection of a coin cell backup battery or a "super" capacitor. If the voltage at VIN goes below the V_{IN} threshold (VTL1), contact-bounced, or removed, the coin cell maintained logic is powered by the voltage applied to LICELL. The supply for internal logic and the VSNVS rail switches over to the LICELL pin when V_{IN} goes below VTL1, even in the absence of a voltage at the LICELL pin, resulting in clearing of memory and turning off VSNVS. Applications concerned about this behavior can tie the LICELL pin to any system voltage between 1.8 V and 3.0 V. A 0.47 μ F capacitor should be placed from LICELL to ground under all circumstances.

6.3.11.4 Coin cell charger control

The coin cell charger circuit functions as a current-limited voltage source, resulting in the CC/CV taper characteristic typically used for rechargeable Lithium-Ion batteries. The coin cell charger is enabled via the COINCHEN bit while the coin cell voltage is programmable through the VCOIN[2:0] bits on register COINCTL on Table 70. The coin cell charger voltage is programmable. In the ON state, the charger current is fixed at ICOINHI. In sleep and standby modes, the charger current is reduced to a typical 10 μ A. In the OFF state, coin cell charging is not available as the main battery could be depleted unnecessarily. The coin cell charging is stopped when V_{IN} is below UVDET.

Table 70. Coin cell charger voltage

| VCOIN[2:0] | V _{COIN} (V) ⁽⁶⁴⁾ |
|------------|---------------------------------------|
| 000 | 2.50 |
| 001 | 2.70 |
| 010 | 2.80 |
| 011 | 2.90 |
| 100 | 3.00 |
| 101 | 3.10 |
| 110 | 3.20 |
| 111 | 3.30 |

Notes

Table 71. Register COINCTL - ADDR 0x1A

| Name | Bit# | R/W | Default | Description |
|----------|------|-----|---------|---|
| VCOIN | 2:0 | R/W | 0x00 | Coin cell charger output voltage selection. See Table 70 for all options selectable through these bits. |
| COINCHEN | 3 | R/W | 0x00 | Enable or disable the coin cell charger |
| Unused | 7:4 | _ | 0x00 | Unused |

6.3.11.5 External components

Table 72. Coin cell charger external components

| Component | Value | Units |
|-------------------------|-------|-------|
| LICELL bypass capacitor | 100 | nF |

^{64.} Coin cell voltages selected based on the type of LICELL used on the system.

6.4 Power dissipation

During operation, the temperature of the die should not exceed the operating junction temperature noted in Table 4. To optimize the thermal management and to avoid overheating, the PF3000 provides thermal protection. An internal comparator monitors the die temperature. Interrupts THERM110, THERM120, THERM125, and THERM130 is generated when the respective thresholds specified in Table 73 are crossed in either direction. The temperature range can be determined by reading the THERMxxxS bits in register INTSENSE0.

In the event of excessive power dissipation, thermal protection circuitry shuts down the PF3000. This thermal protection acts above the thermal protection threshold listed in Table 73. To avoid any unwanted power downs resulting from internal noise, the protection is debounced for 8.0 ms. This protection should be considered as a fail-safe mechanism and therefore the system should be configured such that this protection is not tripped under normal conditions.

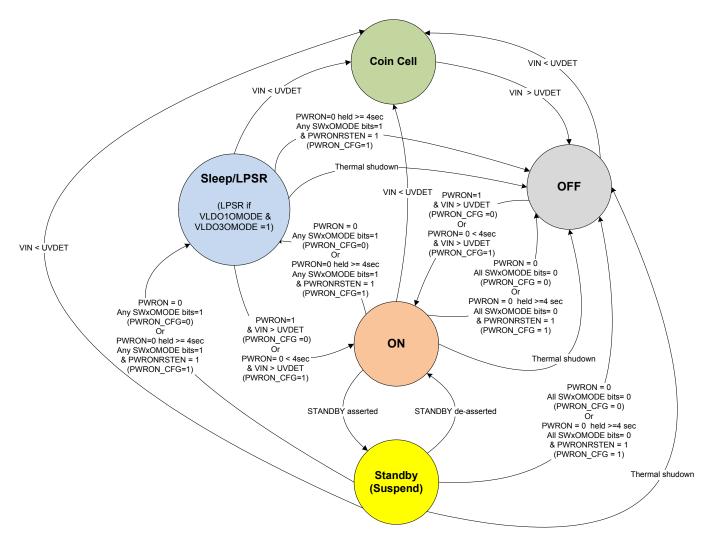
Table 73. Thermal protection thresholds

| Parameter | Min. | Тур. | Max. | Units |
|-------------------------------------|------|------|------|-------|
| Thermal 110 °C threshold (THERM110) | 100 | 110 | 120 | °C |
| Thermal 120 °C threshold (THERM120) | 110 | 120 | 130 | °C |
| Thermal 125 °C threshold (THERM125) | 115 | 125 | 135 | °C |
| Thermal 130 °C threshold (THERM130) | 120 | 130 | 140 | °C |
| Thermal warning hysteresis | 2.0 | - | 4.0 | °C |
| Thermal protection threshold | 130 | 140 | 150 | °C |

6.5 Modes of operation

6.5.1 State diagram

The operation of the PF3000 can be reduced to five states, or modes: ON, OFF, Sleep, Standby, and Coin Cell. <u>Figure 15</u> shows the state diagram of the PF3000, along with the conditions to enter and exit from each state.



^{*} VIN should be above UVDET to allow a power up and VIN must have crossed above the UVDET rising threshold without decaying below the UVDET falling threshold.

Figure 15. State diagram

To complement the state diagram in Figure 15, a description of the states is provided in following sections. Note that V_{IN} must exceed the rising UVDET threshold to allow a power up. Refer to Table 32 for the UVDET thresholds. Additionally, I²C control is not possible in the coin cell mode and the interrupt signal, INTB, is only active in sleep, standby, and ON states.

6.5.1.1 ON mode

The PF3000 enters the On mode after a turn-on event. RESETBMCU is de-asserted, and pulled high via an external pull-up resistor, in this mode of operation. To enter the On mode, V_{IN} voltage must surpass the rising UVDET threshold and PWRON must be asserted. From the On mode, when the voltage at V_{IN} drops below the undervoltage falling threshold, UVDET, the state machine transitions to the coin cell mode.

6.5.1.2 OFF mode

The PF3000 enters the Off mode after a turn-off event. Only VCOREDIG and VSNVS are powered in the mode of operation. To exit the Off mode, a valid turn-on event is required. RESETBMCU is asserted, LOW, in this mode. Turn off events can be achieved using the PWRON pin, thermal protection, as described below.

6.5.1.3 **PWRON** pin

The PWRON pin is used to power off the PF3000. The PWRON pin can be configured with OTP to power off the PMIC under the following two conditions:

- 1. PWRON CFG bit = 0, SWxOMODE bit = 0 and PWRON pin is low.
- 2. PWRON_CFG bit = 1, SWxOMODE bit = 0, PWRONRSTEN = 1 and PWRON is held low for longer than 4.0 seconds. Alternatively, the system can be configured to restart automatically by setting the RESTARTEN bit.

6.5.1.4 Thermal protection

If the die temperature surpasses a given threshold, the thermal protection circuit powers off the PMIC to avoid damage. A turn-on event does not power on the PMIC while it is in thermal protection. The part remains in Off mode until the die temperature decreases below a given threshold. See Power dissipation section for more detailed information.

6.5.1.5 Standby mode

- Depending on STANDBY pin configuration, Standby is entered when the STANDBY pin is asserted. This is typically used for low-power mode of operation.
- · When STANDBY is de-asserted, standby mode is exited.

A product may be designed to go into a low-power mode after periods of inactivity. The STANDBY pin is provided for board level control of going in and out of such deep sleep modes (DSM). When a product is in DSM, it may be able to reduce the overall platform current by lowering the regulator output voltage, changing the operating mode of the regulators or disabling some regulators. The configuration of the regulators in standby is pre-programmed through the I²C interface. Note that the STANDBY pin is programmable for Active High or Active Low polarity, and that decoding of a standby event takes into account the programmed input polarity as shown in Table 74. When the PF3000 is powered up first, regulator settings for the standby mode are mirrored from the regulator settings for the ON mode. To change the STANDBY pin polarity to Active Low, set the STANDBYINV bit via software first, and then change the regulator settings for standby mode as required. For simplicity, STANDBY is generally be referred to as active high throughout this document.

Table 74. Standby pin and polarity control

| STANDBY (Pin) (66) | STANDBYINV (I ² C bit) (67) | STANDBY Control (65) |
|--------------------|--|----------------------|
| 0 | 0 | 0 |
| 0 | 1 | 1 |
| 1 | 0 | 1 |
| 1 | 1 | 0 |

Notes

- 65. STANDBY = 0: System is not in standby, STANDBY = 1: system is in standby
- 66. The state of the STANDBY pin only has influence in On mode.
- 67. Bit 6 in Power Control register (ADDR 0x1B)

Since STANDBY pin activity is driven asynchronously to the system, a finite time is required for the internal logic to qualify and respond to the pin level changes. A programmable delay is provided to hold off the system response to a standby event. This allows the processor and peripherals some time after a standby instruction has been received to terminate processes to facilitate seamless entering into standby mode.

When enabled (STBYDLY = 01, 10, or 11) per Table 75, STBYDLY delays the standby initiated response for the entire IC, until the STBYDLY counter expires. An allowance should be made for three additional 32 kHz cycles required to synchronize the standby event.

Table 75. STANDBY delay - initiated response

| STBYDLY[1:0] (68) | Function |
|-------------------|-----------------------------|
| 00 No delay | |
| 01 | One 32 kHz period (default) |
| 10 | Two 32 kHz periods |
| 11 | Three 32 kHz periods |

Notes

68. Bits [5:4] in Power Control register (ADDR - 0x1B)

6.5.1.6 Sleep/LPSR mode

- · Depending on PWRON pin configuration, sleep mode is entered when PWRON is de-asserted and SWxOMODE bit is set.
- · To exit sleep mode, assert the PWRON pin.

In the sleep mode, the regulator uses the set point as programmed by SW1xOFF[3:0] for SW1A/B and by SWxOFF[2:0] for SW2 and SW3. The activated regulators maintains settings for this mode and voltage until the next turn-on event. Table 76 shows the control bits in sleep mode. During sleep mode, interrupts are active and the INTB pin reports any unmasked fault event. If LPSR is activated by requesting VDD_LPSR and VCC_GPIO to stay ON, LDO1 and LDO3 enables in low-power mode.

Table 76. Regulator mode control

| SWxOMODE | Off operational mode (sleep) ⁽⁶⁹⁾ |
|----------|--|
| 0 | Off |
| 1 | PFM |

Notes

 For sleep mode, activated switching regulators, should use the Off mode set point as programmed by SW1xOFF[4:0] for SW1A/B and SW2OFF[2:0] for SW2, and SW3OFF[3:0] for SW3.

6.5.1.7 Coin cell mode

In the Coin Cell state, the coin cell is the only valid power source to the PMIC. No turn-on event is accepted in the Coin Cell state. Transition to the OFF state requires that V_{IN} surpasses UVDET threshold. RESETBMCU is held low in this mode. If the coin cell is depleted, a complete system reset occurs. At the next application of power and the detection of a turn-on event, the system re-initializes with all I²C bits including, those that reset on COINPORB are restored to their default states.

6.5.2 State machine flow summary

Table 77 provides a summary matrix of the PF3000 flow diagram to show the conditions needed to transition from one state to another.

Table 77. State machine flow summary

| | | | | Next state | | |
|---------------|----------------|---|-------------------------|---|------------------|--|
| S | STATE | OFF | Coin cell | Sleep | Standby | ON |
| | OFF | X | V _{IN} < UVDET | Х | Х | PWRON_CFG = 0 PWRON = 1 & V _{IN} > UVDET or PWRON_CFG = 1 PWRON = 0 < 4.0 s & V _{IN} > UNDET |
| | Coin cell | V _{IN} > UVDET | Х | Х | Х | Х |
| | | Thermal shutdown | | Х | | |
| ate | Sleep/ LPSR | PWRON_CFG = 1 PWRON = 0 ≥ 4.0 s Any SWxOMODE = 1 & PWRONRSTEN = 1 | V _{IN} < UVDET | LPSR (LDO1 & LDO3 or V33 Enabled) if VLDO1OMODE =1 & VLDO3OMODE=1 or V33OMODE=1 | х | PWRON_CFG = 0 PWRON = 1 & V _{IN} > UVDET or PWRON_CFG = 1 PWRON = 0 < 4.0 s & V _{IN} > UNDET |
| Initial state | Standby | Thermal shutdown PWRON_CFG = 0 PWRON = 0 All SWxOMODE = 0 or PWRON_CFG = 1 PWRON = 0 ≥ 4.0 s All SWxOMODE = 0 & PWRONRSTEN = 1 | V _{IN} < UVDET | PWRON_CFG = 0 PWRON = 0 Any SWxOMODE = 1 or PWRON_CFG = 1 PWRON = 0 ≥ 4.0 s Any SWxOMODE = 1 & PWRONRSTEN = 1 | X | Standby de-asserted |
| | ON | Thermal shutdown PWRON_CFG = 0 PWRON = 0 All SWxOMODE = 0 or PWRON_CFG = 1 PWRON = 0 ≥ 4.0 s All SWxOMODE = 0 & PWRONRSTEN = 1 | V _{IN} < UVDET | PWRON_CFG = 0 PWRON = 0 Any SWxOMODE = 1 or PWRON_CFG = 1 PWRON = 0 ≥ 4.0 s Any SWxOMODE = 1 & PWRONRSTEN = 1 | Standby asserted | X |

6.5.3 Performance characteristics curves

 $(V_{IN} = 3.6 \text{ V}, \text{SW1A}_{OUT} = 1.0 \text{ V}; \text{SW1B}_{OUT} = 1.0 \text{ V}, \text{SW2}_{OUT} = 1.8 \text{ V}, \text{SW3}_{OUT} = 1 \text{ V}, \text{SWBST}_{OUT} = 5.0 \text{ V}$ Switching frequency = 2.0 MHz, Mode = APS; LDO1_{OUT} = 1.8 V, LDO2_{OUT} = 1.0 V, LDO3_{OUT} = 1.8 V, LDO4_{OUT} = 1.8 V, V33_{OUT} = 3.3 V, VCC_SD_{OUT} = 3.3 V, unless otherwise noted)

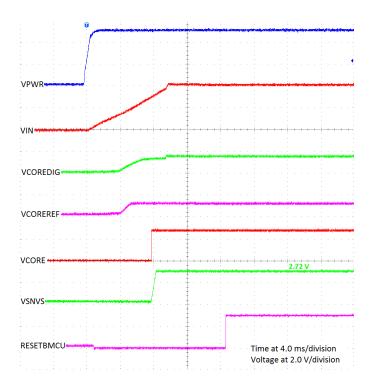


Figure 16. Typical startup waveforms

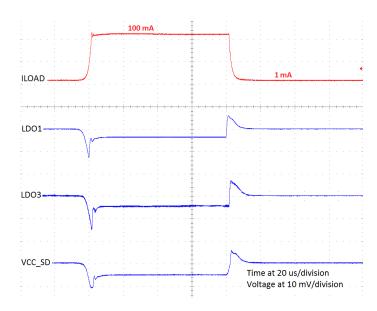


Figure 17. Load transient response - LDO1, LDO3 and VCC_SD

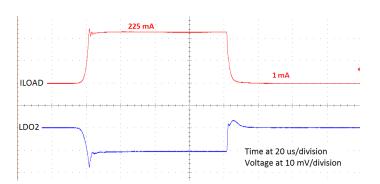


Figure 18. Load transient response - LDO2

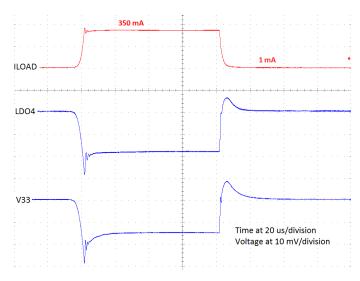


Figure 19. Load transient response - LDO4 and V33

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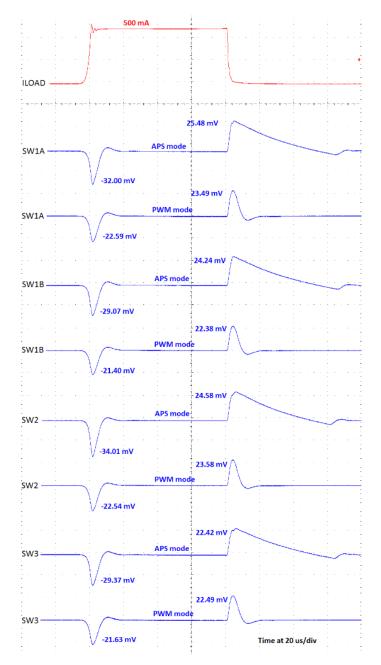


Figure 20. Load transient response - buck regulators

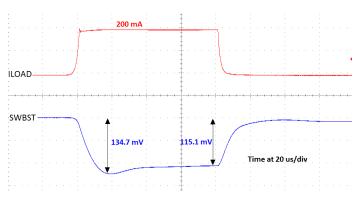


Figure 21. Load transient response - SWBST

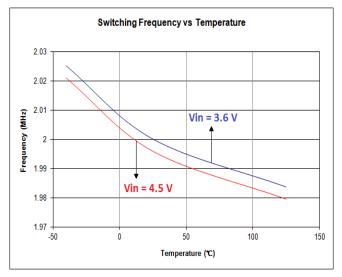


Figure 22. Switching frequency vs. temperature

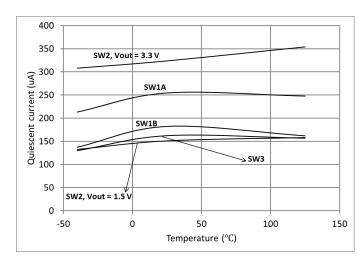


Figure 23. Quiescent current - buck regulators in APS mode

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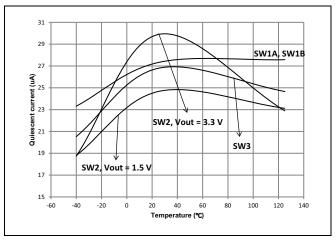


Figure 24. Quiescent current - buck regulators in PFM mode

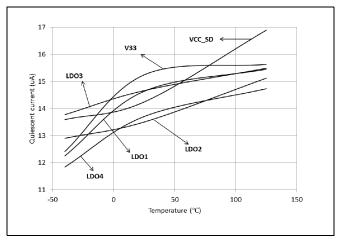


Figure 25. Quiescent current - LDOs

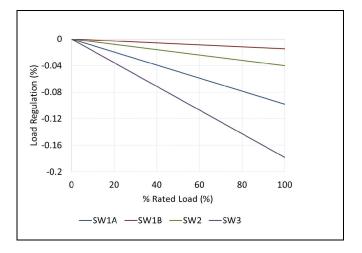


Figure 26. Load regulation - buck regulators

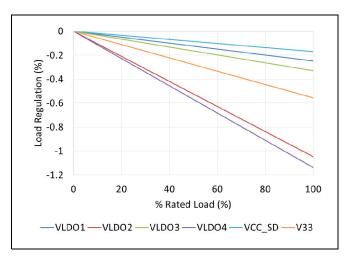


Figure 27. Load regulation - LDOs

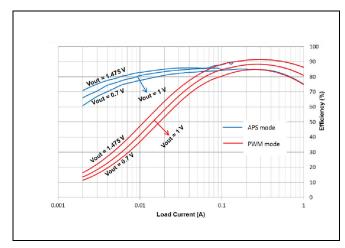


Figure 28. SW1A efficiency - APS and PWM modes

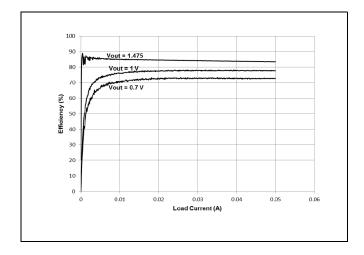


Figure 29. SW1A efficiency - PFM mode

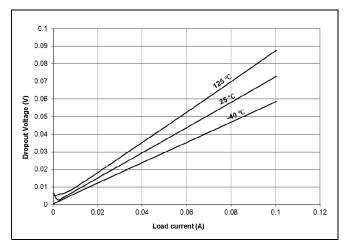


Figure 30. Dropout voltage - VLDO1, VLDO3, VCC_SD - V_{OUT} = 3.3 V

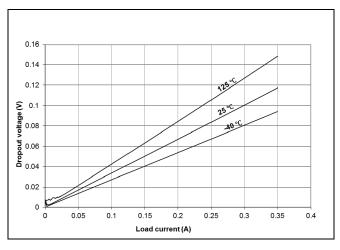


Figure 32. Dropout voltage - VLDO4, V33 - V_{OUT} = 3.3 V

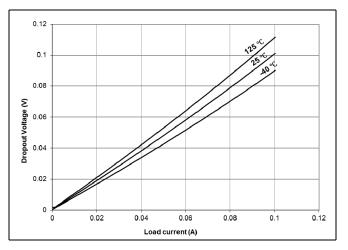


Figure 31. Dropout voltage - VLDO1, VLDO3, VCC_SD - V_{OUT} = 1.8 V

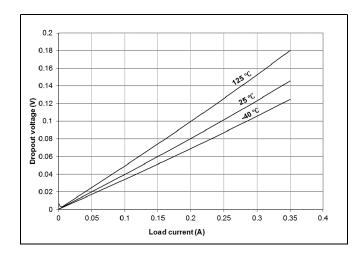


Figure 33. Dropout voltage - VLDO4 - V_{OUT} = 1.8 V

6.6 Control Interface I²C block description

The PF3000 contains an I^2C interface port which allows access by a processor, or any I^2C master, to the register set. Via these registers the resources of the IC can be controlled. The registers also provide status information about how the IC is operating.

The SCL and SDA lines should be routed away from noisy signals and planes to minimize noise pick up. To prevent reflections in the SCL and SDA traces from creating false pulses, the rise and fall times of the SCL and SDA signals must be greater than 20 ns. This can be accomplished by reducing the drive strength of the I^2 C master via software. It is recommended to use a drive strength of 80 Ω or higher to increase the edge times. Alternatively, this can be accomplished by using small capacitors from SCL and SDA to ground. For example, use 5.1 pF capacitors from SCL and SDA to ground for bus pull-up resistors of 4.8 k Ω .

6.6.1 I²C device ID

I²C interface protocol requires a device ID for addressing the target IC on a multi-device bus. The I²C address is set to 0x08.

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6.6.2 I²C operation

The I²C mode of the interface is implemented generally following the fast mode definition which supports up to 400 kbits/s operation (exceptions to the standard are noted to be 7-bit only addressing and no support for general call addressing.)

The I2C interface is configured as "Slave".

Timing diagrams, electrical specifications, and further details can be found in the I²C specification, which is available for download at: http://www.nxp.com/acrobat_download/literature/9398/39340011.pdf

 I^2 C read operations are also performed in byte increments separated by an ACK. Read operations also begin with the MSB and each byte is sent out unless a STOP command or NACK is received prior to completion.

PF3000 only supports single-byte I²C transactions for read and write. The host initiates and terminates all communication. The host sends a master command packet after driving the start condition. The device responds to the host if the master command packet contains the corresponding slave address. In the following examples, the device is shown always responding with an ACK to transmissions from the host. If at any time a NACK is received, the host should terminate the current transaction and retry the transaction.

PF3000 uses the "repeated start" operation for reads as shown in Figure 35

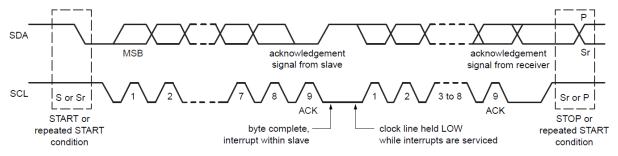


Figure 34. Data transfer on the I²C bus

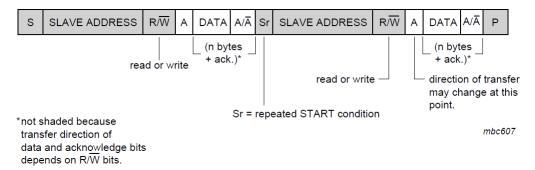


Figure 35. Read operation

6.6.3 Interrupt handling

The system is informed about important events based on interrupts. Unmasked interrupt events are signaled to the processor by driving the INTB pin low. Each interrupt is latched so that even if the interrupt source becomes inactive, the interrupt remains set until cleared. Each interrupt can be cleared by writing a "1" to the appropriate bit in the Interrupt Status register; this causes the INTB pin to go high. If there are multiple interrupt bits set the INTB pin remains low until all are either masked or cleared. If a new interrupt occurs while the processor clears an existing interrupt bit, the INTB pin remains low.

Each interrupt can be masked by setting the corresponding mask bit to a 1. As a result, when a masked interrupt bit goes high, the INTB pin does not go low. A masked interrupt can still be read from the Interrupt Status register. This gives the processor the option of polling for status from the IC. The IC powers up with all interrupts masked, so the processor must initially poll the device to determine if any interrupts are active. Alternatively, the processor can unmask the interrupt bits of interest. If a masked interrupt bit was already high, the INTB pin goes low after unmasking.

The sense registers contain status and input sense bits so the system processor can poll the current state of interrupt sources. They are read only, and not latched or clearable. Interrupts generated by external events are debounced; therefore, the event needs to be stable throughout the debounce period before an interrupt is generated. Nominal debounce periods for each event are documented in the INT summary Table 78. Due to the asynchronous nature of the debounce timer, the effective debounce time can vary slightly.

6.6.4 Interrupt bit summary

Table 78 summarizes all interrupt, mask, and sense bits associated with INTB control. For more detailed behavioral descriptions, refer to the related chapters.

Table 78. Interrupt, mask, and sense bits

| Interrupt | Mask | Sense | Purpose | Trigger | Debounce time (ms) |
|--------------|--------------|--------------|--|---------|-----------------------|
| LOWVINI | LOWVINM | LOWVINS | Low input voltage detect Sense is 1 if below 2.70 V threshold | H to L | 3.9 (70) |
| PWRONI | PWRONM | PWRONS | Power on button event | H to L | 31.25 ⁽⁷⁰⁾ |
| FWRON | FWRONIVI | FWRONS | Sense is 1 if PWRON is high. | L to H | 31.25 |
| THERM110 | THERM110M | THERM110S | Thermal 110 °C threshold Sense is 1 if above threshold | Dual | 3.9 |
| THERM120 | THERM120M | THERM120S | Thermal 120 °C threshold Sense is 1 if above threshold | Dual | 3.9 |
| THERM125 | THERM125M | THERM125S | Thermal 125 °C threshold Sense is 1 if above threshold | Dual | 3.9 |
| THERM130 | THERM130M | THERM130S | Thermal 130 °C threshold Sense is 1 if above threshold | Dual | 3.9 |
| SW1AFAULTI | SW1AFAULTM | SW1AFAULTS | Regulator 1A overcurrent limit Sense is 1 if above current limit | L to H | 8.0 |
| SW1BFAULTI | SW1BFAULTM | SW1BFAULTS | Regulator 1C overcurrent limit Sense is 1 if above current limit | L to H | 8.0 |
| SW2FAULTI | SW2FAULTM | SW2FAULTS | Regulator 2 overcurrent limit Sense is 1 if above current limit | L to H | 8.0 |
| SW3FAULTI | SW3FAULTM | SW3FAULTS | Regulator 3 overcurrent limit Sense is 1 if above current limit | L to H | 8.0 |
| SWBSTFAULTI | SWBSTFAULTM | SWBSTFAULTS | SWBST overcurrent limit Sense is 1 if above current limit | L to H | 8.0 |
| VLDO1FAULTI | VLDO1FAULTM | VLDO1FAULTS | VLDO1 overcurrent limit Sense is 1 if above current limit | L to H | 8.0 |
| VLDO2FAULTI | VLDO2FAULTM | VLDO2FAULTS | VLDO2 overcurrent limit Sense is 1 if above current limit | L to H | 8.0 |
| VCC_SDFAULTI | VCC_SDFAULTM | VCC_SDFAULTS | VCC_SD overcurrent limit Sense is 1 if above current limit | L to H | 8.0 |

Table 78. Interrupt, mask, and sense bits (continued)

| Interrupt | Mask | Sense | Purpose | Trigger | Debounce time (ms) |
|---------------|----------------|----------------|--|---------|--------------------|
| V33FAULTI | V33FAULTM | V33FAULTS | V33 overcurrent limit Sense is 1 if above current limit | L to H | 8.0 |
| VLDO3FAULTI | VLDO3FAULTM | VLDO1FAULTS | VLDO3 overcurrent limit Sense is 1 if above current limit | L to H | 8.0 |
| VLDO4FAULTI | VLDO4FAULTM | VLDO4FAULTS | VLDO4 overcurrent limit Sense is 1 if above current limit | L to H | 8.0 |
| OTP_ECCI | OTP_ECCM | OTP_ECCS | 1 or 2 bit error detected in OTP registers Sense is 1 if error detected | L to H | - |
| OTP_AUTO_BLOW | OTP_AUTO_BLOWM | OTP_AUTO_BLOWS | Interrupt to indicate completion of fuse auto blow | L to H | - |
| VPWROVI | VPWROVM | VPWROVS | VPWR pin overvoltage interrupt | L to H | 0.122 |

Notes

A full description of all interrupt, mask, and sense registers is provided in Table 79 to Table 90.

Table 79. Register INTSTAT0 - ADDR 0x05

| Name | Bit# | R/W | Default | Description |
|-----------|------|-------|---------|------------------------------|
| PWRONI | 0 | R/W1C | 0 | Power on interrupt bit |
| LOWVINI | 1 | R/W1C | 0 | Low-voltage interrupt bit |
| THERM110I | 2 | R/W1C | 0 | 110 °C Thermal interrupt bit |
| THERM120I | 3 | R/W1C | 0 | 120 °C Thermal interrupt bit |
| THERM125I | 4 | R/W1C | 0 | 125 °C Thermal interrupt bit |
| THERM130I | 5 | R/W1C | 0 | 130 °C Thermal interrupt bit |
| Unused | 7:6 | _ | 0b00 | Unused |

Table 80. Register INTMASK0 - ADDR 0x06

| Name | Bit# | R/W | Default | Description |
|-----------|------|-------|---------|-----------------------------------|
| PWRONM | 0 | R/W1C | 1 | Power on interrupt mask bit |
| LOWVINM | 1 | R/W1C | 1 | Low-voltage interrupt mask bit |
| THERM110M | 2 | R/W1C | 1 | 110 °C thermal interrupt mask bit |
| THERM120M | 3 | R/W1C | 1 | 120 °C thermal interrupt mask bit |
| THERM125M | 4 | R/W1C | 1 | 125 °C thermal interrupt mask bit |
| THERM130M | 5 | R/W1C | 1 | 130 °C thermal interrupt mask bit |
| Unused | 7:6 | _ | 0b00 | Unused |

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^{70.} Debounce timing for the falling edge can be extended with PWRONDBNC[1:0].

Table 81. Register INTSENSE0 - ADDR 0x07

| Name | Bit# | R/W | Default | Description |
|-----------|------|-----|---------|---|
| PWRONS | 0 | R | 0 | Power on sense bit 0 = PWRON low 1 = PWRON high |
| LOWVINS | 1 | R | 0 | Low-voltage sense bit 0 = VIN > 2.7 V 1 = VIN ≤ 2.7 V |
| THERM110S | 2 | R | 0 | 110 °C thermal sense bit 0 = Below threshold 1 = Above threshold |
| THERM120S | 3 | R | 0 | 120 °C thermal sense bit 0 = Below threshold 1 = Above threshold |
| THERM125S | 4 | R | 0 | 125 °C thermal sense bit 0 = Below threshold 1 = Above threshold |
| THERM130S | 5 | R | 0 | 130 °C thermal sense bit 0 = Below threshold 1 = Above threshold |
| ICTESTS | 6 | R | 0 | 0 = ICTEST pin is grounded 1 = ICTEST to VCOREDIG or greater |
| VDDOTPS | 7 | R | 0 | Additional VDDOTP voltage sense pin 0 = VDDOTP grounded 1 = VDDOTP to VCOREDIG or greater |

Table 82. Register INTSTAT1 - ADDR 0x08

| Name | Bit # | R/W | Default | Description |
|------------|-------|-------|---------|--------------------------------|
| SW1AFAULTI | 0 | R/W1C | 0 | SW1A overcurrent interrupt bit |
| SW1BFAULTI | 1 | R/W1C | 0 | SW1B overcurrent interrupt bit |
| Unused | 2 | R/W1C | 0 | Unused |
| SW2FAULTI | 3 | R/W1C | 0 | SW2 Overcurrent interrupt bit |
| SW3FAULTI | 4 | R/W1C | 0 | SW3 Overcurrent interrupt bit |
| Unused | 5 | R/W1C | 0 | Unused |
| Unused | 6 | R/W1C | 0 | Unused |
| Unused | 7 | - | 0 | Unused |

Table 83. Register INTMASK1 - ADDR 0x09

| Name | Bit# | R/W | Default | Description |
|------------|------|-----|---------|-------------------------------------|
| SW1AFAULTM | 0 | R/W | 1 | SW1A overcurrent interrupt mask bit |
| SW1BFAULTM | 1 | R/W | 1 | SW1B overcurrent interrupt mask bit |
| Unused | 2 | R/W | 1 | Unused |
| SW2FAULTM | 3 | R/W | 1 | SW2 overcurrent interrupt mask bit |
| SW3FAULTM | 4 | R/W | 1 | SW3 overcurrent interrupt mask bit |
| Unused | 5 | R/W | 1 | Unused |
| Unused | 6 | R/W | 1 | Unused |
| Unused | 7 | _ | 0 | Unused |

Table 84. Register INTSENSE1 - ADDR 0x0A

| Name | Bit# | R/W | Default | Description |
|------------|------|-----|---------|---|
| SW1AFAULTS | 0 | R | 0 | SW1A overcurrent sense bit 0 = Normal operation 1 = Above current limit |
| Unused | 1 | R | 0 | Unused |
| SW1BFAULTS | 2 | R | 0 | SW1B overcurrent sense bit 0 = Normal operation 1 = Above current limit |
| SW2FAULTS | 3 | R | 0 | SW2 overcurrent sense bit 0 = Normal operation 1 = Above current limit |
| SW3FAULTS | 4 | R | 0 | SW3 overcurrent sense bit 0 = Normal operation 1 = Above current limit |
| Unused | 5 | R | 0 | Unused |
| Unused | 6 | R | 0 | Unused |
| Unused | 7 | - | 0 | Unused |

Table 85. Register INTSTAT3 - ADDR 0x0E

| Name | Bit# | R/W | Default | Description |
|---------------|------|-------|---------|--|
| SWBSTFAULTI | 0 | R/W1C | 0 | SWBST overcurrent limit interrupt bit |
| Unused | 1 | _ | 0b0 | Unused |
| VPWROVI | 2 | R/W1C | 0b0 | High when overvoltage event is detected in the front-end LDO circuit. This bit defaults to 0b1 when VPWR is grounded and the VIN path is used to power the PF3000. |
| Unused | 5:3 | _ | 0b0 | Unused |
| OTP AUTO BLOW | 6 | R/W1C | 0b0 | High after auto fuse blow sequence is completed |
| OTP_ECCI | 7 | R/W1C | 0 | OTP error interrupt bit |

Table 86. Register INTMASK3 - ADDR 0x0F

| Name | Bit# | R/W | Default | Description |
|--------------------------|------|-----|---------|--|
| SWBSTFAULTM | 0 | R/W | 1 | SWBST overcurrent limit interrupt mask bit |
| Unused | 1 | _ | 0 | Unused |
| VPWROVM | 2 | R/W | 1 | VPWR overvoltage interrupt mask bit |
| Unused | 5:3 | _ | 0b000 | Unused |
| OTP_AUTO_BLOW_ DONE_M | 6 | R/W | 1 | OTP auto blow mask bit |
| OTP_ECCM | 7 | R/W | 1 | OTP error interrupt mask bit |

Table 87. Register INTSENSE3 - ADDR 0x10

| Name | Bit # | R/W | Default | Description |
|--------------------------|-------|-----|---------|---|
| SWBSTFAULTS | 0 | R | 0 | SWBST overcurrent limit sense bit 0 = Normal operation 1 = Above current limit |
| Unused | 1 | _ | 0b0 | Unused |
| VPWROVS | 2 | R | 0 | VPWR overvoltage interrupt sense bit |
| Unused | 5:3 | _ | 0b000 | Unused |
| OTP_AUTO_BLOW_ DONE_S | 6 | R | 0 | OTP auto blow sense bit. This bit is high while the auto blow sequence is running. Do not read/write the OTP TBB registers while this bit is 1. |
| OTP_ECCS | 7 | R | 0 | OTP error sense bit 0 = No error detected 1 = OTP error detected |

Table 88. Register INTSTAT4 - ADDR 0x11

| Name | Bit # | R/W | Default | Description |
|--------------|-------|-------|---------|----------------------------------|
| VLDO1FAULTI | 0 | R/W1C | 0 | VLDO1 overcurrent interrupt bit |
| VLDO2FAULTI | 1 | R/W1C | 0 | VLDO2 overcurrent interrupt bit |
| VCC_SDFAULTI | 2 | R/W1C | 0 | VCC_SD overcurrent interrupt bit |
| V33FAULTI | 3 | R/W1C | 0 | V33 overcurrent interrupt bit |
| VLDO3FAULTI | 4 | R/W1C | 0 | VLDO3 overcurrent interrupt bit |
| VLDO4FAULTI | 5 | R/W1C | 0 | VLDO4 overcurrent interrupt bit |
| Unused | 7:6 | - | 0b00 | Unused |

Table 89. Register INTMASK4 - ADDR 0x12

| Name | Bit # | R/W | Default | Description |
|--------------|-------|-----|---------|---------------------------------------|
| VLDO1FAULTM | 0 | R/W | 1 | VLDO1 overcurrent interrupt mask bit |
| VLDO2FAULTM | 1 | R/W | 1 | VLDO2 overcurrent interrupt mask bit |
| VCC_SDFAULTM | 2 | R/W | 1 | VCC_SD overcurrent interrupt mask bit |
| V33FAULTM | 3 | R/W | 1 | V33 overcurrent interrupt mask bit |
| VLDO3FAULTM | 4 | R/W | 1 | VLDO3 overcurrent interrupt mask bit |
| VLDO4FAULTM | 5 | R/W | 1 | VLDO4 overcurrent interrupt mask bit |
| Unused | 7:6 | - | 0b00 | Unused |

Table 90. Register INTSENSE4 - ADDR 0x13

| Name | Bit # | R/W | Default | Description |
|--------------|-------|-----|---------|---|
| VLDO1FAULTS | 0 | R | 0 | VLDO1 overcurrent sense bit 0 = Normal operation 1 = Above current limit |
| VLDO2FAULTS | 1 | R | 0 | VLDO2 overcurrent sense bit 0 = Normal operation 1 = Above current limit |
| VCC_SDFAULTS | 2 | R | 0 | VCC_SD overcurrent sense bit 0 = Normal operation 1 = Above current limit |

Table 90. Register INTSENSE4 - ADDR 0x13 (continued)

| Name | Bit # | R/W | Default | Description |
|-------------|-------|-----|---------|--|
| V33FAULTS | 3 | R | 0 | V33 overcurrent sense bit 0 = Normal operation 1 = Above current limit |
| VLD03FAULTS | 4 | R | 0 | VLDO3 overcurrent sense bit 0 = Normal operation 1 = Above current limit |
| VLDO4FAULTS | 5 | R | 0 | VLDO4 overcurrent sense bit 0 = Normal operation 1 = Above current limit |
| Unused | 7:6 | _ | 0b00 | Unused |

6.6.5 Specific registers

6.6.5.1 IC and version identification

The IC and other version details can be read via identification bits. These are hard-wired on the chip and described in Table 91 to Table 93.

Table 91. Register DEVICEID - ADDR 0x00

| Name | Bit # | R/W | Default | Description |
|----------|-------|-----|---------|---------------|
| DEVICEID | 3:0 | R | 0x0 | 0000 = PF3000 |
| FAMILY | 7:4 | R | 0x3 | 0011 = PF3000 |

Table 92. Register SILICON REV- ADDR 0x03

| Name | Bit # | R/W | Default | Description |
|-----------------|-------|-----|---------|---|
| METAL_LAYER_REV | 3:0 | R | 0x0 | Represents the metal mask revision Pass 0.0 = 0000 Pass 0.15 = 1111 |
| FULL_LAYER_REV | 7:4 | R | 0x1 | Represents the full mask revision Pass 1.0 = 0001 Pass 15.0 = 1111 |

Table 93. Register FABID - ADDR 0x04

| Name | Bit# | R/W | Default | Description |
|--------|------|-----|---------|--|
| FIN | 1:0 | R | 0b00 | Allows for characterizing different options within the same reticule |
| FAB | 3:2 | R | 0b00 | Represents the wafer manufacturing facility |
| Unused | 7:4 | R | 0b0000 | Unused |

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6.6.5.2 Embedded memory

There are four register banks of general purpose embedded memory to store critical data. The data written to MEMA[7:0], MEMB[7:0], MEMC[7:0], and MEMD[7:0] is maintained by the coin cell when the main battery is deeply discharged, removed, or contact-bounced. The contents of the embedded memory are reset by COINPORB. The banks can be used for any system need for bit retention with coin cell backup.

Table 94. Register MEMA ADDR 0x1C

| Name | Bit# | R/W | Default | Description |
|------|------|-----|---------|---------------|
| MEMA | 7:0 | R/W | 0x00 | Memory bank A |

Table 95. Register MEMB ADDR 0x1D

| Name | Bit # | R/W | Default | Description |
|------|-------|-----|---------|---------------|
| MEMB | 7:0 | R/W | 0x00 | Memory bank B |

Table 96. Register MEMC ADDR 0x1E

| Name | Bit# | R/W | Default | Description |
|------|------|-----|---------|---------------|
| MEMC | 7:0 | R/W | 0x00 | Memory bank C |

Table 97. Register MEMD ADDR 0x1F

| Name | Bit# | R/W | Default | Description |
|------|------|-----|---------|---------------|
| MEMD | 7:0 | R/W | 0x00 | Memory bank D |

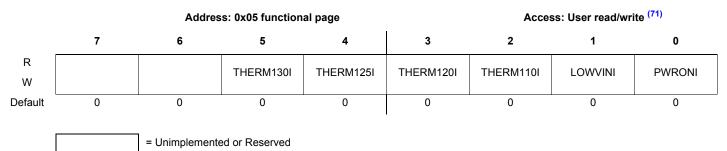
6.6.5.3 Register descriptions

This section describes all the PF3000 registers and their individual bits. Address order is as listed in Register map.

6.6.5.3.1 Interrupt status register 0 (INTSTAT0)

INSTAT0 is one of the four status interrupt registers. This register contains six status flags. Write a logic 1 to clear a flag.

Table 98. Status interrupt register 0 (INTSTAT0)



Notes

71. Read: Anytime Write: Anytime

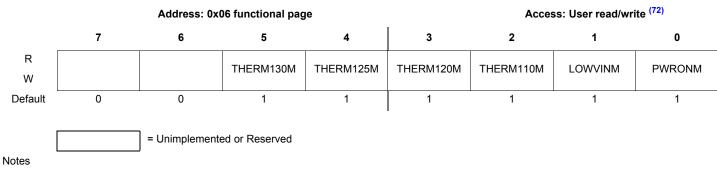
Table 99. INTSTAT0 field descriptions

| Field | Description |
|----------------|--|
| 5 THERM130I | 130 °C Thermal interrupt bit — THERM130I is set to 1 when the THERM130 threshold specified in is crossed in either direction (bidirectional). This flag can only be cleared by writing a 1. Writing a 0 has no effect. 0 Die temperature has not crossed THERM130 threshold. 1 Die temperature has crossed THERM130 threshold. |
| 4 THERM125I | 125 °C Thermal interrupt bit — THERM125 is set to 1 when the THERM125 threshold specified in is crossed in either direction (bi-directional). This flag can only be cleared by writing a 1. Writing a 0 has no effect. 0 Die temperature has not crossed THERM125 threshold. 1 Die temperature has crossed THERM125 threshold. |
| 3 THERM120I | 120 °C Thermal interrupt bit — THERM120I is set to 1 when the THERM120 threshold specified in is crossed in either direction (bidirectional). This flag can only be cleared by writing a 1. Writing a 0 has no effect. O Die temperature has not crossed THERM120 threshold. Die temperature has crossed THERM120 threshold. |
| 2 THERM110I | 110 °C Thermal interrupt bit — THERM110I is set to 1 when the THERM110 threshold specified in is crossed in either direction (bi-directional). This flag can only be cleared by writing a 1. Writing a 0 has no effect. O Die temperature has not crossed THERM110 threshold. 1 Die temperature has crossed THERM110 threshold. |
| 1 LOWVINI | Low-voltage interrupt bit — LOWVINI is set to 1 when a low-voltage event occurs on VIN. This flag can only be cleared by writing a 1. Writing a 0 has no effect. 0 V _{IN} > 2.7 V (typical) 1 V _{IN} < 2.7 V (typical) |
| 0 PWRONI | Power on interrupt bit —PWRONI is set to 1 when the turn on event occurs. This flag can only be cleared by writing a 1. Writing a 0 has no effect. O Power on has not occurred. Power on has occurred. |

6.6.5.3.2 Interrupt status mask register 0 (INTMASK0)

INTMASK0 is the mask register for the status interrupt register INTSTAT0. Write a logic 0 to a bit to unmask the corresponding interrupt. When unmasked, the corresponding interrupt state is reflected on the INTB pin.

Table 100. Interrupt status mask register 0 (INTMASK0)



72. Read: Anytime Write: Anytime

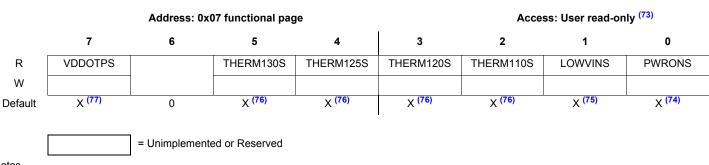
Table 101. INTMASK0 field descriptions

| Field | Description |
|----------------|---|
| 5 THERM130M | 130 °C Thermal interrupt mask bit 0 THERM130I Unmasked 1 THERM130I Masked |
| 4 THERM125M | 125 °C Thermal interrupt mask bit 0 THERM125I Unmasked 1 THERM125I Masked |
| 3 THERM120M | 120 °C Thermal interrupt mask bit 0 THERM120I Unmasked 1 THERM120I Masked |
| 2 THERM110M | 110 °C Thermal interrupt mask bit 0 THERM110I Unmasked 1 THERM110I Masked |
| 1 LOWVINM | Low-voltage interrupt mask bit 0 LOWVINI Unmasked 1 LOWVINI Masked |
| 0 PWRONM | Power on interrupt mask bit 0 PWRONI Unmasked 1 PWRONI Masked |

6.6.5.3.3 Interrupt sense register 0 (INTSENSE0)

This register has seven read-only sense bits. These sense bits reflects the actual state of the corresponding function.

Table 102. Interrupt sense register 0 (INTSENSE0)



Notes

- 73. Read: Anytime
- 74. Default value depends on the initial PWRON pin state.
- 75. Default value depends on the initial VIN voltage.
- 76. Default value depends on the initial temperature of the die.
- 77. Default value depends on the initial VDDOTP pin state.

Table 103. INTSENSE0 field descriptions

| Field | Description |
|----------------|--|
| 7 VDDOTPS | VDDOTP voltage sense bit 0 VDDOTP grounded. 1 VDDOTP to VCOREDIG or greater. |
| 5 THERM130S | 130 °C thermal interrupt sense bit 0 Die temperature below THERM130 threshold. 1 Die temperature above THERM130 threshold. |
| 4 THERM125S | 125 °C thermal interrupt sense bit 0 Die temperature below THERM125 threshold. 1 Die temperature has crossed THERM125 threshold. |

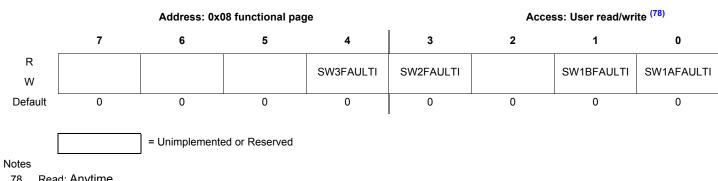
Table 103. INTSENSE0 field descriptions (continued)

| Field | Description |
|----------------|--|
| 3 THERM120S | 120 °C thermal interrupt sense bit 0 Die temperature below THERM120 threshold. 1 Die temperature has crossed THERM120 threshold. |
| 2 THERM110S | 110 °C thermal interrupt sense bit 0 Die temperature below THERM110 threshold. 1 Die temperature has crossed THERM110 threshold. |
| 1 LOWVINS | Low-voltage interrupt sense bit 0 V _{IN} > 2.7 V (typical) 1 V _{IN} < 2.7 V (typical) |
| 0 PWRONS | Power on interrupt sense bit 0 PWRON low. 1 PWRON high. |

6.6.5.3.4 Interrupt status register 1 (INTSTAT1)

INSTAT1 is one of the four status interrupt registers. This register contains four status flags. Write a logic 1 to clear a flag.

Table 104. Status interrupt register 1 (INTSTAT1)



78. Read: Anytime Write: Anytime

Table 105. INTSTAT1 field descriptions

| Field | Description |
|-----------------|---|
| 4 SW3FAULTI | SW3 overcurrent interrupt bit — SW3FAULTI is set to 1 when the SW3 regulator is in current limit protection. This flag can only be cleared by writing a 1. Writing a 0 has no effect. SW3 in normal operation SW3 above current limit |
| 3 SW2FAULTI | SW2 overcurrent interrupt bit — SW2FAULTI is set to 1 when the SW2 regulator is in current limit protection. This flag can only be cleared by writing a 1. Writing a 0 has no effect. SW2 in normal operation SW2 above current limit |
| 1 SW1BFAULTI | SW1B overcurrent interrupt bit — SW1BFAULTI is set to 1 when the SW1B regulator is in current limit protection. This flag can only be cleared by writing a 1. Writing a 0 has no effect. SW1B in normal operation SW1B above current limit |
| 0 SW1AFAULTI | SW1A overcurrent interrupt bit — SW1AFAULTI is set to 1 when the SW1A regulator is in current limit protection. This flag can only be cleared by writing a 1. Writing a 0 has no effect. SW1A in normal operation SW1A above current limit |

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6.6.5.3.5 Interrupt status mask register 1 (INTMASK1)

INTMASK1 is the mask register for the status interrupt register INTSTAT1. Write a logic 0 to a bit to unmask the corresponding interrupt. When unmasked, the corresponding interrupt state is reflected on the INTB pin.

Table 106. Interrupt status mask register 1 (INTMASK1)

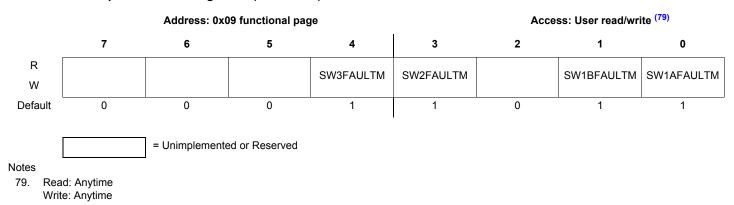


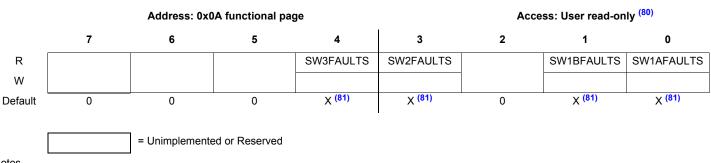
Table 107. INTMASK1 field descriptions

| Field | Description |
|-----------------|---|
| 4 SW3FAULTM | SW3 overcurrent interrupt mask bit 0 SW3FAULTI Unmasked 1 SW3FAULTI Masked |
| 3 SW2FAULTM | SW2 overcurrent interrupt mask bit 0 SW2FAULTI Unmasked 1 SW2FAULTI Masked |
| 1 SW1BFAULTM | SW1B overcurrent interrupt mask bit 0 SW1BFAULTI Unmasked 1 SW1BFAULTI Masked |
| 0 SW1AFAULTM | SW1A overcurrent interrupt mask bit 0 SW1AFAULTI Unmasked 1 SW1AFAULTI Masked |

6.6.5.3.6 Interrupt sense register 1 (INTSENSE1)

This register has four read-only sense bits. These sense bits reflect the actual state of the corresponding function.

Table 108. Interrupt sense register 1 (INTSENSE1)



Notes

80. Read: Anytime

81. Default value depends on the regulator initial state

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Table 109. INTSENSE1 field descriptions

| Field | Description |
|-----------------|--|
| 4 SW3FAULTS | SW3 overcurrent sense bit 0 SW3 in normal operation 1 SW3 above current limit |
| 3 SW2FAULTS | SW2 overcurrent sense bit 0 SW2 in normal operation 1 SW2 above current limit |
| 1 SW1BFAULTS | SW1B overcurrent sense bit 0 SW1B in normal operation 1 SW1B above current limit |
| 0 SW1AFAULTS | SW1A overcurrent sense bit 0 SW1A in normal operation 1 SW1A above current limit |

6.6.5.3.7 Interrupt status register 3 (INTSTAT3)

INSTAT3 is one of the four status interrupt registers. This register contains four status flags. Write a logic 1 to clear a flag.

Table 110. Status Interrupt Register 3 (INTSTAT3)

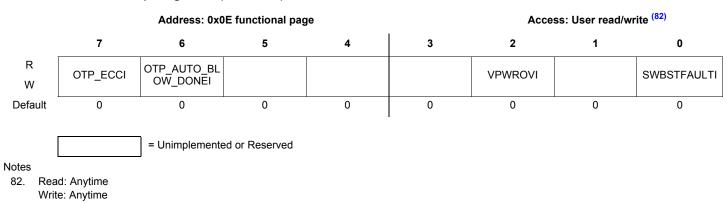


Table 111. INTSTAT3 field descriptions

| Field | Description |
|------------------------------|---|
| 7 OTP_ECCI | OTP error interrupt bit — OTP_ECCI is set to 1 when an error is detected in OTP registers. This flag can only be cleared by writing a 1. Writing a 0 has no effect. O No error detected OTP error detected |
| 6 OTP_AUTO_BL OW_DONEI | OTP auto fuse blow interrupt bit — OTP_AUTO_BLOW_DONEI is set to 1 after the auto fuse blow sequence is completed. This flag can only be cleared by writing a 1. Writing a 0 has no effect. OTP auto fuse blow sequence not completed OTP auto fuse blow sequence completed |
| 2 VPWROVI | VPWR overvoltage interrupt bit — High when an overvoltage event is detected in the front-end LDO circuit. This flag can only be cleared by writing a 1. Writing a 0 has no effect. VPWR in normal operation range. VPWR in overvoltage range. |
| 0 SWBSTFAULTI | SWBST overcurrent limit interrupt bit — SWBSTFAULTI is set to 1 when the SWBST regulator is in current limit protection. This flag can only be cleared by writing a 1. Writing a 0 has no effect. 0 SWBST in normal operation 1 SWBST above current limit |

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6.6.5.3.8 Interrupt status mask register 3 (INTMASK3)

INTMASK3 is the mask register for the status interrupt register INTSTAT3. Write a logic 0 to a bit to unmask the corresponding interrupt. When unmasked, the corresponding interrupt state is reflected on the INTB pin.

Table 112. Interrupt status mask register 3 (INTMASK3)

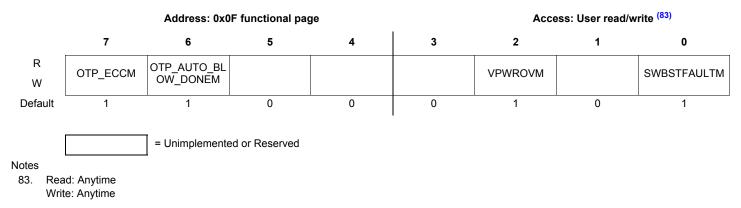


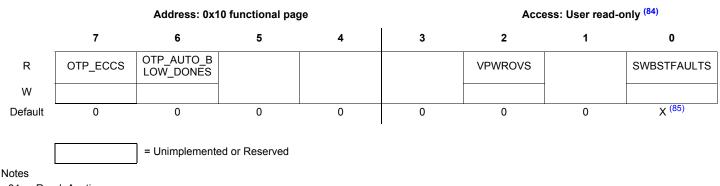
Table 113. INTMASK3 field descriptions

| Field | Description |
|------------------------------|--|
| 7 OTP_ECCM | OTP error interrupt mask bit O OTP_ECCI Unmasked OTP_ECCI Masked |
| 6 OTP_AUTO_BLO W_DONEM | OTP auto blow mask bit 0 OTP_AUTO_BLOW_DONEI Unmasked 1 OTP_AUTO_BLOW_DONEI Masked |
| 2 VPWROVM | VPWR overvoltage interrupt mask bit 0 VPWROVI Unmasked 1 VPWROVI Masked |
| 0 SWBSTFAULTM | SWBST overcurrent limit interrupt mask bit 0 SWBSTFAULTI Unmasked 1 SWBSTFAULTI Masked |

6.6.5.3.9 Interrupt sense register 3 (INTSENSE3)

This register has four read-only sense bits. These sense bits reflect the actual state of the corresponding function.

Table 114. Interrupt sense register 3 (INTSENSE3)



84. Read: Anytime

85. Default value depends on the regulator initial state

Table 115. INTSENSE3 field descriptions

| Field | Description |
|------------------------------|---|
| 7 OTP_ECCS | OTP error sense bit 0 No error detected 1 OTP error detected |
| 6 OTP_AUTO_BLO W_DONES | OTP auto blow sense bit — This bit is high while the auto blow sequence is running. Do not read/write the OTP TBB registers while this bit is 1. 0 SW2 in normal operation 1 SW2 at current limit |
| 2 VPWROVS | VPWR overvoltage interrupt sense bit VPWR in normal operation range. VPWR in overvoltage range. |
| 0 SWBSTFAULTS | SWBST overcurrent limit sense bit 0 SWBST in normal operation 1 SWBST above current limit |

6.6.5.3.10 Interrupt status register 4 (INTSTAT4)

INSTAT4 is one of the four status interrupt registers. This register contains six status flags. Write a logic 1 to clear a flag.

Table 116. Status interrupt register 4 (INTSTAT4)

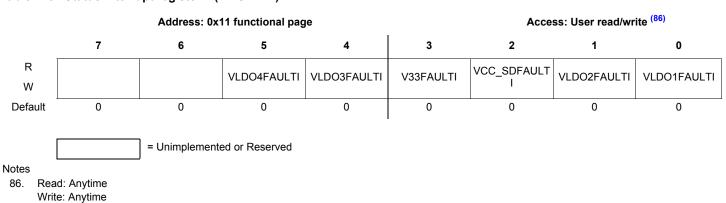


Table 117. INTSTAT4 field descriptions

| Field | Description |
|------------------|---|
| 5 VLDO4FAULTI | VLDO4 overcurrent interrupt bit — VLDO4FAULTI is set to 1 when the VLDO4 regulator is in current limit protection. This flag can only be cleared by writing a 1. Writing a 0 has no effect. ULDO4 in normal operation VLDO4 above current limit |
| 4 VLDO3FAULTI | VLDO3 overcurrent interrupt bit — VLDO3FAULTI is set to 1 when the VLDO3 regulator is in current limit protection. This flag can only be cleared by writing a 1. Writing a 0 has no effect. ULDO3 in normal operation VLDO3 above current limit |
| 3 V33FAULTI | V33 overcurrent interrupt bit — V33FAULTI is set to 1 when the V33 regulator is in current limit protection. This flag can only be cleared by writing a 1. Writing a 0 has no effect. 0 V33 in normal operation 1 V33 above current limit |

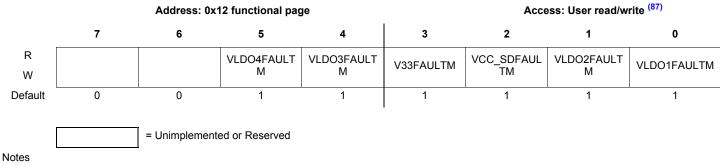
Table 117. INTSTAT4 field descriptions (continued)

| Field | Description |
|-------------------|--|
| 2 VCC_SDFAULTI | VCC_SD overcurrent interrupt bit — VCC_SDFAULTI is set to 1 when the VCC_SD regulator is in current limit protection. This flag can only be cleared by writing a 1. Writing a 0 has no effect. 0 VCC_SD in normal operation 1 VCC_SD above current limit |
| 1 VLDO2FAULTI | VLDO2 overcurrent interrupt bit — VLDO2FAULTI is set to 1 when the VLDO2 regulator is in current limit protection. This flag can only be cleared by writing a 1. Writing a 0 has no effect. VLDO2 in normal operation range. VLDO2 above current limit |
| 0 VLDO1FAULTI | VLDO1 overcurrent interrupt bit — SWBSTFAULTI is set to 1 when the SWBST regulator is in current limit protection. This flag can only be cleared by writing a 1. Writing a 0 has no effect. 0 VLDO1 in normal operation range. 1 VLDO1 above current limit |

6.6.5.3.11 Interrupt status mask register 4 (INTMASK4)

INTMASK4 is the mask register for the status interrupt register INTSTAT4. Write a logic 0 to a bit to unmask the corresponding interrupt. When unmasked, the corresponding interrupt state is reflected on the INTB pin.

Table 118. Interrupt status mask register 4 (INTMASK4)



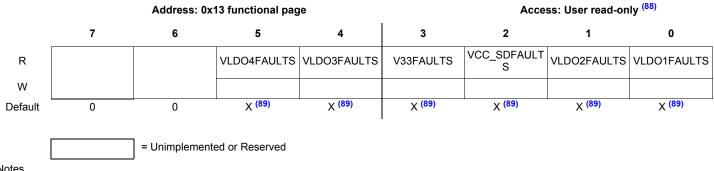
87. Read: Anytime Write: Anytime

Table 119. INTMASK4 field descriptions

| Field | Description |
|-------------------|---|
| 5 VLDO4FAULTM | VLDO4 overcurrent interrupt mask bit 0 VLDO4FAULTI Unmasked 1 VLDO4FAULTI Masked |
| 4 VLDO3FAULTM | VLDO3 overcurrent interrupt mask bit 0 VLDO3FAULTI Unmasked 1 VLDO3FAULTI Masked |
| 3 V33FAULTM | V33 overcurrent interrupt mask bit 0 V33FAULTI Unmasked 1 V33FAULTI Masked |
| 2 VCC_SDFAULTM | VCC_SD overcurrent interrupt mask bit 0 VCC_SDFAULTI Unmasked 1 VCC_SDFAULTI Masked |
| 1 VLDO2FAULTM | VLDO2 Overcurrent interrupt mask bit 0 VLDO2FAULTI Unmasked 1 VLDO2FAULTI Masked |
| 0 VLDO1FAULTM | VLDO1 overcurrent interrupt mask bit 0 VLDO1FAULTI Unmasked 1 VLDO1FAULTI Masked |

6.6.5.3.12 Interrupt sense register 4 (INTSENSE4)

This register has four read-only sense bits. These sense bits reflect the actual state of the corresponding function.



Notes

88. Read: Anytime

Default value depends on the regulator initial state 89.

Table 120. INTSENSE4 Field Descriptions

| Field | Description |
|-----------------------|--|
| 5 VLDO4FAULTS | VLDO4 overcurrent sense bit 0 VLDO4 in normal operation 1 VLDO4 above current limit |
| 4 VLDO3FAULTS | VLDO3 overcurrent sense bit 0 VLDO3 in normal operation 1 VLDO3 above current limit |
| 3 V33FAULTS | V33 overcurrent sense bit 0 V33 in normal operation 1 V33 above current limit |
| 2 VCC_SDFAULT S | VCC_SD overcurrent sense bit 0 VCC_SD in normal operation 1 VCC_SD above current limit |
| 1 VLDO2FAULTS | VLDO2 overcurrent sense bit VLDO2 in normal operation VLDO2 above current limit |
| 0 VLDO1FAULTS | VLDO1 overcurrent sense bit 0 VLDO1 in normal operation 1 VLDO1 above current limit |

6.6.5.3.13 Coin cell control register (COINCTL)

This register is used to control the coin cell charger.

Table 121. Coin cell control register (COINCTL)

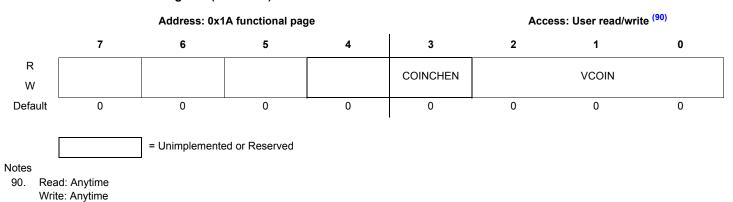
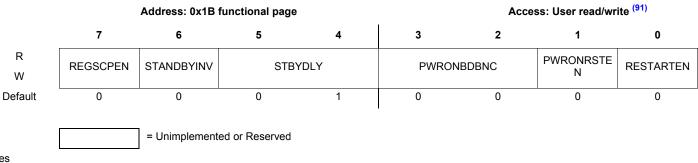


Table 122. COINCTL field descriptions

| Field | Description |
|---------------|--|
| 3 COINCHEN | Coin cell charger enable bit 0 Coin cell charger disabled. 1 Coin cell charger enabled. |
| 2:0 VCOIN | Coin cell charger output voltage selection — This field is used to set the coin cell charging voltage from 2.50 V to 3.30 V. See Table 70 for all options selectable through these bits. |

6.6.5.3.14 Power control register (PWRCTL)

Table 123. Power control register (PWRCTL)



Notes

91. Read: Anytime Write: Anytime

Table 124. PWRCTL field descriptions

| Field | Description |
|------------------|---|
| 7 REGSCPEN | Short-circuit protection enable bit — When REGSCPEN is set to 1, whenever a current limit event occurs on a LDO regulator, this regulator is shutdown. O Short-circuit protection disabled Short-circuit protection enabled |
| 6 STANDBYINV | STANDBY inversion bit —STANDBYINV is used to control the polarity of the STANDBY pin. 0 STANDBY pin is active high 1 STANDBY pin is active low |
| 4:3 STBYDLY | STANDBY delay bits — STBYDLY is used to set the delay between a standby request from the STANDBY pin and the entering in standby mode. 00 No delay 01 One 32 kHz period (default) 10 Two 32 kHz periods 11 Three 32 kHz periods |
| 3:2 PWRONDBNC | PWRON programmable debouncer bits — PWRONDBNC is used to set the debounce time for the PWRON input pin. For configuration, see Table 36. |
| 1 PWRONRSTEN | PWRON reset enable bit — When set to 1, the PF3000 can enter OFF mode when the PWRON pin is held low for 4 seconds or longer. See PWRON Pin section for details. 0 Disallow OFF mode after PWRON held low 1 Allow OFF mode after PWRON held low |
| 0 RESTARTEN | Restart enable bit — When set to 1, the PF3000 restarts automatically after a power off event generated by the PWRON (held low for 4 seconds or longer) when PWR_CFG bit = 1. 0 Automatic restart disabled. 1 Automatic restart enabled. |

6.6.5.3.15 Embedded memory register A (MEMA)

Table 125. Embedded memory register A (MEMA)

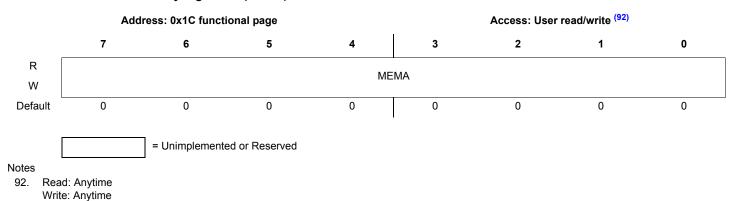


Table 126. MEMA field descriptions

| Field | Description |
|-------------|---|
| 7:0 MEMA | Memory bank A — This register is maintained in case of a main battery loss as long as the coin cell is present. The contents of the embedded memory are reset by COINPORB. |

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6.6.5.3.16 Embedded memory register B (MEMB)

Table 127. Embedded memory register B (MEMB)

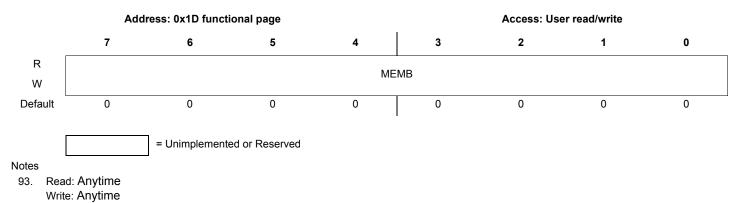


Table 128. MEMB field descriptions

| Field | Description |
|-------------|---|
| 7:0 MEMB | Memory bank B — This register is maintained in case of a main battery loss as long as the coin cell is present. The contents of the embedded memory are reset by COINPORB. |

6.6.5.3.17 Embedded memory register C (MEMC)

Table 129. Embedded Memory Register C (MEMC)

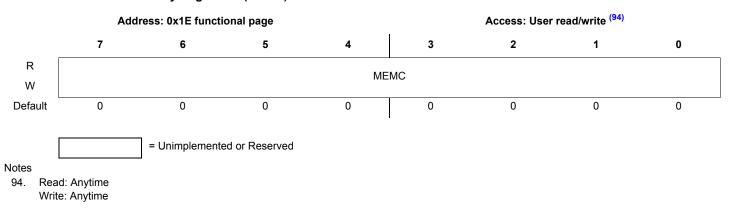


Table 130. MEMC field descriptions

| Field | Description |
|-------------|---|
| 7:0 MEMC | Memory bank C — This register is maintained in case of a main battery loss as long as the coin cell is present. The contents of the embedded memory are reset by COINPORB. |

6.6.5.3.18 **Embedded memory register D (MEMD)**

Table 131. Embedded memory register D (MEMD)

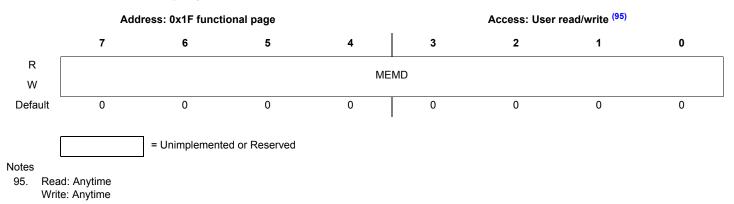


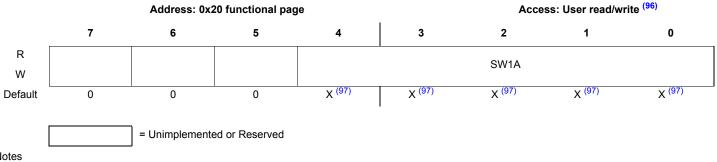
Table 132. MEMD field descriptions

| Field | Description |
|-------------|---|
| 7:0 MEMD | Memory bank D — This register is maintained in case of a main battery loss as long as the coin cell is present. The contents of the embedded memory are reset by COINPORB. |

SW1A voltage control register (SW1AVOLT)

This register is used to set the output voltage of the SW1A regulator in normal operation.

Table 133. SW1A voltage control register (SW1AVOLT)



Notes

96. Read: Anytime Write: Anytime

Default value depends on OTP content.

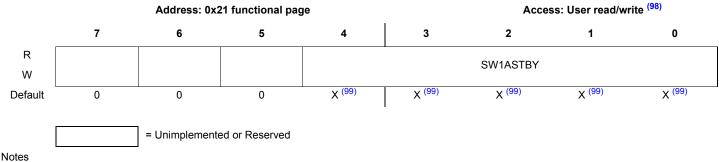
Table 134. SW1AVOLT field descriptions

| Field | Description |
|-------------|---|
| 4:0 SW1A | SW1A output voltage — Refer to Table 53 |

SW1A standby voltage control register (SW1ASTBY)

This register is used to set the output voltage of the SW1A regulator in standby operation.

Table 135. SW1A standby voltage control register (SW1ASTBY)



98. Read: Anytime Write: Anytime

Default value depends on OTP content.

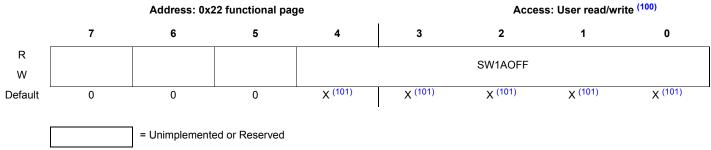
Table 136. SW1ASTBY field descriptions

| Field | Description |
|-----------------|---|
| 4:0 SW1ASTBY | SW1A standby output voltage — Refer to Table 53 |

6.6.5.3.21 SW1A sleep mode voltage control register (SW1AOFF)

This register is used to set the output voltage of the SW1A regulator in sleep mode operation.

Table 137. SW1A sleep mode voltage control register (SW1AOFF)



Notes

Read: Anytime 100. Write: Anytime

Default value depends on OTP content.

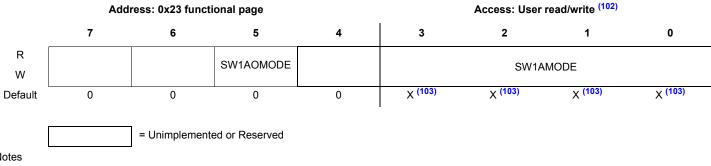
Table 138. SW1AOFF field descriptions

| Field | Description |
|-----------------|--|
| 4:0 SW1ASTBY | SW1A sleep mode output voltage — Refer to Table 53 |

SW1A switching mode selector register (SW1AMODE) 6.6.5.3.22

This register is used to set the switching mode of the SW1A regulator.

Table 139. SW1A switching mode selector register (SW1AMODE)



Notes

Read: Anytime 102. Write: Anytime

Default value depends on OTP content. 103.

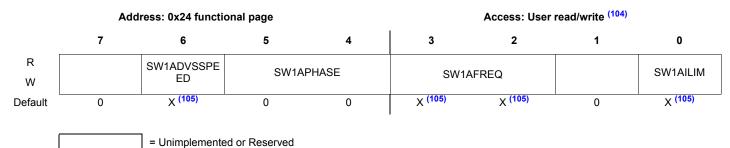
Table 140. SW1AMODE field descriptions

| Field | Description |
|-----------------|--|
| 5 SW1AOMODE | SW1A Off mode bit— This bit configures the mode entered by SW1A after a turn-off event OFF mode entered after a turn-off event. Sleep mode entered after a turn-off event. |
| 3:0 SW1AMODE | SW1A switching mode selector — Refer to Table 47 |

SW1A configuration register (SW1ACONF) 6.6.5.3.23

This register is used to configure DVS, switching frequency, phase and current limit settings of the SW1A regulator.

Table 141. SW1A configuration register (SW1ACONF)



Notes

104. Read: Anytime Write: Anytime

Default value depends on OTP content. 105.

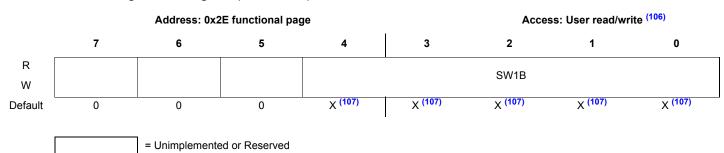
Table 142. SW1ACONF field descriptions

| Field | Description |
|-------------------|---|
| 6 SW1ADVSSPEED | SW1A DVS speed bit— This bit configures the DVS stepping rates speed for SW1A. Refer to the Table 48. 0 25 mV step each 2.0 μs. 1 25 mV step each 4.0 μs. |
| 5:4 SW1APHASE | SW1A phase clock bit— SW1APHASE is used to set the phase clock for SW1A. Refer to Table 49. |
| 3:2 SW1AFREQ | SW1A switching frequency— SW1APHASE is used to set the desired switching frequency for SW1A. Refer to Table 51. |
| 0 SW1AILIM | SW1A current limiter bit— This bit configures the current limit for SW1A. 0 2.75 A (typ). 1 2.0 A (typ). |

6.6.5.3.24 SW1B voltage control register (SW1BVOLT)

This register is used to set the output voltage of the SW1B regulator in normal operation.

Table 143. SW1B voltage control register (SW1BVOLT)



Notes

106. Read: Anytime Write: Anytime

107. Default value depends on OTP content.

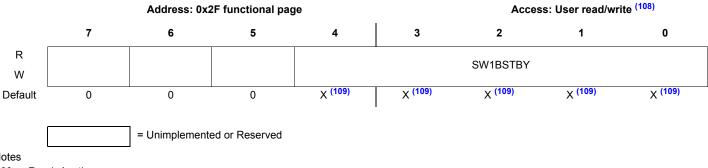
Table 144. SW1BVOLT field descriptions

| Field | Description |
|-------------|--|
| 4:0 SW1B | SW1B output voltage — Refer to Table 53. |

SW1B standby voltage control register (SW1BSTBY) 6.6.5.3.25

This register is used to set the output voltage of the SW1B regulator in standby operation.

Table 145. SW1B standby voltage control register (SW1BSTBY)



Notes

Read: Anytime 108. Write: Anytime

Default value depends on OTP content. 109.

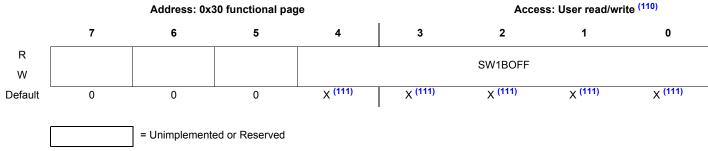
Table 146. SW1BSTBY field descriptions

| Field | Description |
|-----------------|--|
| 4:0 SW1BSTBY | SW1B standby output voltage — Refer to Table 53. |

SW1B sleep mode voltage control register (SW1BOFF)

This register is used to set the output voltage of the SW1B regulator in sleep mode operation.

Table 147. SW1B sleep mode voltage control register (SW1BOFF)



Notes

Read: Anytime 110. Write: Anytime

Default value depends on OTP content.

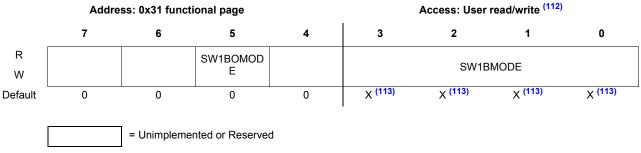
Table 148. SW1BOFF field descriptions

| Field | Description |
|-----------------|---|
| 4:0 SW1BSTBY | SW1B sleep mode output voltage — Refer to Table 53. |

6.6.5.3.27 SW1B switching mode selector register (SW1BMODE)

This register is used to set the switching mode of the SW1B regulator.

Table 149. SW1B switching mode selector register (SW1BMODE)



Notes

113. Default value depends on OTP content.

Table 150. SW1BMODE field descriptions

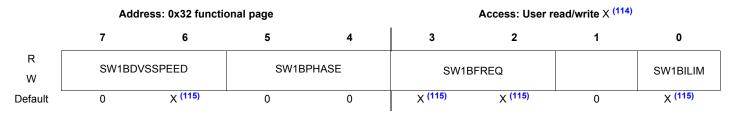
| Field | Description |
|-----------------|--|
| 5 SW1BOMODE | SW1B Off mode bit— This bit configures the mode entered by SW1B after a turn-off event OFF mode entered after a turn-off event. Sleep mode entered after a turn-off event. |
| 3:0 SW1BMODE | SW1B switching mode selector — Refer to Table 47. |

6.6.5.3.28 SW1B configuration register (SW1BCONF)

= Unimplemented or Reserved

This register is used to configure DVS, switching frequency, phase and current limit settings of the SW1B regulator.

Table 151. SW1B configuration register (SW1BCONF)



Notes

114. Read: Anytime

Write: Anytime

115. Default value depends on OTP content.

^{112.} Read: Anytime

Write: Anytime

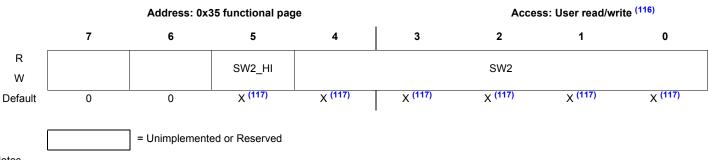
Table 152. SW1BCONF field descriptions

| Field | Description |
|-------------------|---|
| 6 SW1BDVSSPEED | SW1B DVS speed bit— This bit configures the DVS stepping rates speed for SW1B. Refer to the Table 48. 25 mV step each 2.0 μs. 25 mV step each 4.0 μs. |
| 5:4 SW1BPHASE | SW1B phase clock bit— SW1BPHASE is used to set the phase clock for SW1B. Refer to Table 49. |
| 3:2 SW1BFREQ | SW1B switching frequency— SW1BPHASE is used to set the desired switching frequency for SW1B. Refer to Table 51. |
| 0 SW1BILIM | SW1B current limiter bit— This bit configures the current limit for SW1B. 0 2.75 A (typ). 1 2.0 A (typ). |

6.6.5.3.29 SW2 voltage control register (SW2VOLT)

This register is used to set the output voltage of the SW2 regulator in normal operation.

Table 153. SW2 voltage control register (SW2VOLT)



Notes

116. Read: Anytime Write: Anytime

117. Default value depends on OTP content.

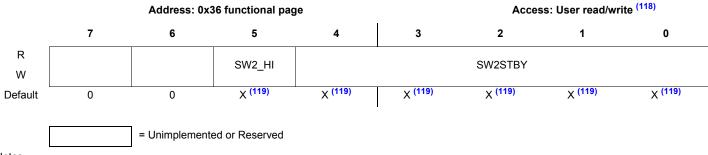
Table 154. SW2VOLT field descriptions

| Field | Description |
|-------------|--|
| 4:0 SW2 | SW2 output voltage — Refer to Table 55. |
| 5 SW2_HI | SW2 Output voltage range —This bit configures the range of SW2 Output voltage. Refer to Table 55. 0 Low output voltage settings 1 High output voltage settings |

6.6.5.3.30 SW2 standby voltage control register (SW2STBY)

This register is used to set the output voltage of the SW2 regulator in standby operation.

Table 155. SW2 standby voltage control register (SW2STBY)



Notes

118. Read: Anytime

Write: Anytime

119. Default value depends on OTP content.

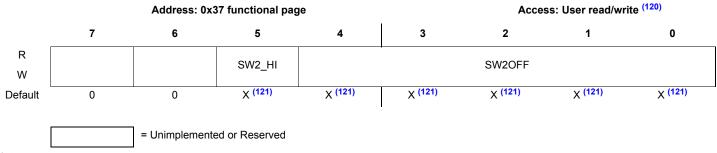
Table 156. SW2STBY field descriptions

| Field | Description |
|----------------|--|
| 4:0 SW2STBY | SW2 standby output voltage — Refer to Table 55. |
| 5 SW2_HI | SW2 output voltage range —This bit configures the range of SW2 Output voltage. Refer to Table 55. 0 Low output voltage settings 1 High output voltage settings |

6.6.5.3.31 SW2 sleep mode voltage control register (SW2OFF)

This register is used to set the output voltage of the SW2 regulator in sleep mode operation.

Table 157. SW2 sleep mode voltage control register (SW2OFF)



Notes

120. Read: Anytime Write: Anytime

121. Default value depends on OTP content.

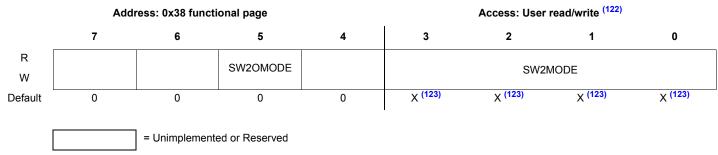
Table 158. SW2OFF field descriptions

| Field | Description |
|----------------|--|
| 4:0 SW2STBY | SW2 sleep mode output voltage — Refer to Table 55. |
| 5 SW2_HI | SW2 output voltage range —This bit configures the range of SW2 Output voltage. Refer to Table 55. 0 Low output voltage settings 1 High output voltage settings |

6.6.5.3.32 SW2 switching mode selector register (SW2MODE)

This register is used to set the switching mode of the SW2 regulator.

Table 159. SW2 switching mode selector register (SW2MODE)



Notes

122. Read: Anytime Write: Anytime

123. Default value depends on OTP content.

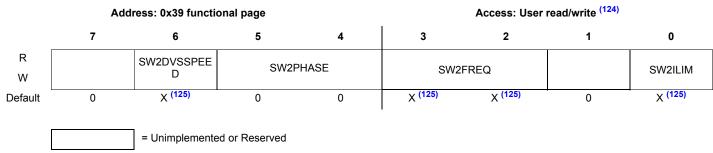
Table 160. SW2MODE field descriptions

| Field | Description |
|----------------|--|
| 5 SW2OMODE | SW2 Off mode bit— This bit configures the mode entered by SW2 after a turn-off event OFF mode entered after a turn-off event. Sleep mode entered after a turn-off event. |
| 3:0 SW2MODE | SW2 switching mode selector — Refer to Table 47. |

6.6.5.3.33 SW2 configuration register (SW2CONF)

This register is used to configure DVS, switching frequency, phase and current limit settings of the SW2 regulator.

Table 161. SW2 configuration register (SW2CONF)



Notes

124. Read: Anytime

Write: Anytime

125. Default value depends on OTP content.

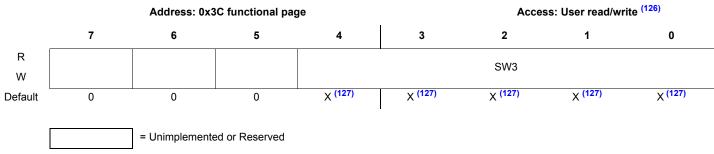
Table 162. SW2CONF field descriptions

| Field | Description |
|------------------|---|
| 6 SW2DVSSPEED | SW2 DVS speed bit- This bit configures the DVS stepping rates speed for SW2. Refer to the Table 48. 0 25 mV step each 2.0 μs. 1 25 mV step each 4.0 μs. |
| 5:4 SW2PHASE | SW2 phase clock bit— SW2PHASE is used to set the phase clock for SW2. Refer to Table 49. |
| 3:2 SW2FREQ | SW2 switching frequency— SW2PHASE is used to set the desired switching frequency for SW2. Refer to Table 51. |
| 0 SW2ILIM | SW2 current limiter bit— This bit configures the current limit for SW2. 0 2.75 A (typ). 1 2.0 A (typ). |

6.6.5.3.34 SW3 voltage control register (SW3VOLT)

This register is used to set the output voltage of the SW3 regulator in normal operation.

Table 163. SW3 voltage control register (SW3VOLT)



Notes

126. Read: Anytime Write: Anytime

127. Default value depends on OTP content.

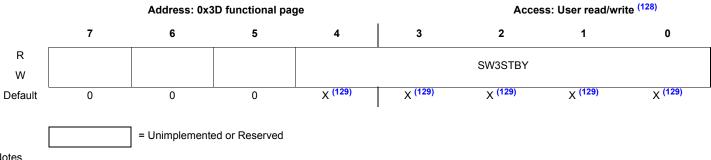
Table 164. SW3VOLT field descriptions

| Field | Description |
|------------|---|
| 4:0 SW3 | SW3 output voltage — Refer to Table 57. |

SW3 standby voltage control register (SW3STBY)

This register is used to set the output voltage of the SW3 regulator in standby operation.

Table 165. SW3 standby voltage control register (SW3STBY)



Notes

Read: Anytime 128. Write: Anytime

Default value depends on OTP content. 129

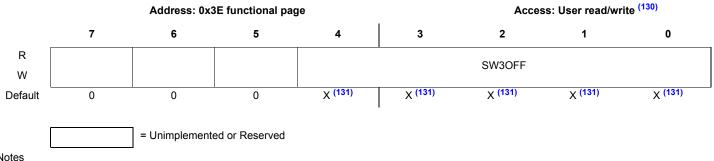
Table 166. SW3STBY field descriptions

| Field | Description |
|----------------|---|
| 4:0 SW3STBY | SW3 standby output voltage — Refer to Table 57. |

SW3 sleep mode voltage control register (SW3OFF)

This register is used to set the output voltage of the SW3 regulator in sleep mode operation.

Table 167. SW3 sleep mode voltage control register (SW3OFF)



Notes

Read: Anytime 130. Write: Anytime

Default value depends on OTP content. 131.

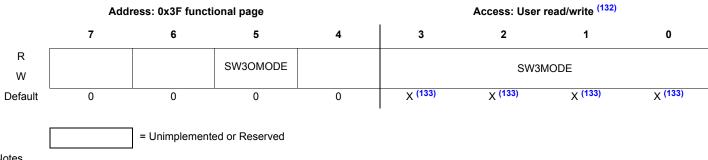
Table 168. SW3OFF field descriptions

| Field | Description |
|----------------|---|
| 4:0 SW3STBY | SW3 sleep mode output voltage — Refer to Refer to Table 57. |

SW3 switching mode selector register (SW3MODE)

This register is used to set the switching mode of the SW3 regulator.

Table 169. SW3 switching mode selector register (SW3MODE)



Notes

Read: Anytime 132.

Write: Anytime

Default value depends on OTP content. 133.

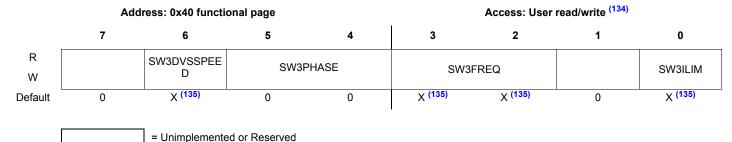
Table 170. SW3MODE field descriptions

| Field | Description |
|----------------|--|
| 5 SW3OMODE | SW3 Off mode bit— This bit configures the mode entered by SW3 after a turn-off event O OFF mode entered after a turn-off event. Sleep mode entered after a turn-off event. |
| 3:0 SW3MODE | SW3 switching mode selector — Refer to Table 47. |

SW3 configuration register (SW3CONF) 6.6.5.3.38

This register is used to configure DVS, switching frequency, phase and current limit settings of the SW3 regulator.

Table 171. SW3 configuration register (SW3CONF)



Notes

Read: Anytime 134. Write: Anytime

Default value depends on OTP content. 135.

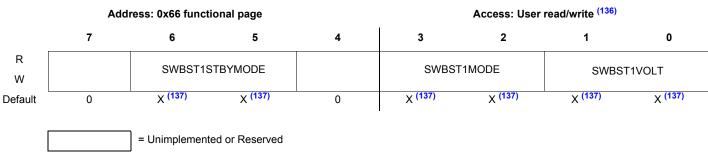
Table 172. SW3CONF field descriptions

| Field | Description |
|------------------|---|
| 6 SW3DVSSPEED | SW3 DVS speed bit— This bit configures the DVS stepping rates speed for SW3. Refer to the Table 48. 0 25 mV step each 2.0 μs. 1 25 mV step each 4.0 μs. |
| 5:4 SW3PHASE | SW3 phase clock bit— SW3PHASE is used to set the phase clock for SW3. Refer to Table 49. |
| 3:2 SW3FREQ | SW3 switching frequency— SW3PHASE is used to set the desired switching frequency for SW3. Refer to Table 51. |
| 0 SW3ILIM | SW3 current limiter bit— This bit configures the current limit for SW3. 0 2.75 A (typ). 1 2.0 A (typ). |

6.6.5.3.39 SWBST setup and control register (SWBSTCTL)

This register is used to configure both the output voltage and switching modes of the SWBST regulator.

Table 173. SWBST configuration register (SWBSTCTL)



Notes

136. Read: Anytime Write: Anytime

137. Default value depends on OTP content.

Table 174. SWBSTCTL field descriptions

| Field | Description |
|-----------------------|---|
| 6:5 SWBST1STBYMODE | SWBST switching mode in standby— SWBST1MODE is used to set the switching mode in standby mode. 00 OFF 01 PFM 10 Auto (138) 11 APS |
| 3:2 SWBST1MODE | SWBST switching mode in normal operation— SWBST1MODE is used to set the switching mode on normal operation. 00 OFF 01 PFM 10 Auto (138) 11 APS |
| 1:0 SWBST1VOLT | SWBST output voltage— SWBST1VOLT is used to set the output voltage for SWBST. 00 5.000 V (typ.) 01 5.050 V (typ.) 10 5.100 V (typ.) 11 5.150 V (typ.) |

Notes

138. In auto mode, the controller automatically switches between PFM and APS modes depending on the load current. Regulator switches in auto mode if enabled in the startup sequence.

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6.6.5.3.40 Front-end LDO control register (LDOGCTL)

This register is used to configure the front-end LDO standby mode operation.

Table 175. Front-end LDO control register (LDOGCTL)

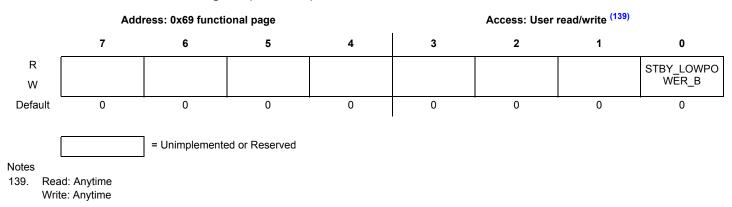


Table 176. LDOGCTL field descriptions

| Field | Description |
|----------------------|--|
| 0 STBY_LOWPOWER_B | Front-end LDO standby mode operation bit—When STBY_LOWPOWER_B bit is set to 1, the front-end LDO does not enter in low-power mode during IC standby mode. 1 Low-power mode disabled during IC standby mode. |

6.6.5.3.41 VREFDDR control register (VREFDDRCTL)

This register is used to control the VREFDDR supply operation.

Table 177. VREFDDR control register (VREFDDRCTL)



Table 178. VREFDDR field descriptions

| Field | Description |
|----------------|--|
| 0 VREFDDREN | VREFDDR supply enable bit— VREFDDREN is used to enable or disable the VREFDDR supply. 0 VREFDDR supply disabled 1 VREFDDR supply enabled |

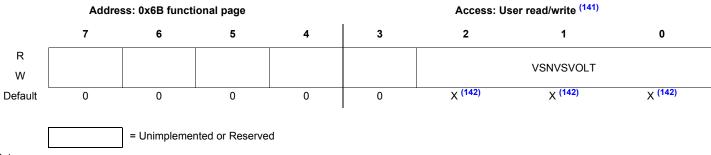
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6.6.5.3.42 VSNVS control register (VSNVSCTL)

This register is used to control the VSNVS supply operation.

Table 179. VSNVS control register (VSNVSCTL)



Notes

141. Read: Anytime Write: Anytime

142. Default value depends on OTP content.

Table 180. VSNVSCTL field descriptions

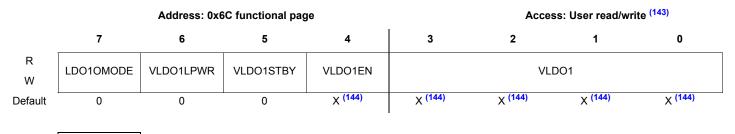
| Field | Description | | | |
|------------------|---|--|--|--|
| 2:0 VSNVSVOLT | VSNVS output voltage configuration— VSNVSVOLT is used to configure the VSNVS output voltage. Values below are typical voltages. 000 = RSVD 001 = RSVD 010 = RSVD 110 = RSVD 101 = RSVD 110 = RSVD 111 = RSVD | | | |

6.6.5.3.43 VLDO1 control register (VLDO1CTL)

= Unimplemented or Reserved

This register is used to configure output voltage, normal and standby mode operation of the VLDO1 regulator.

Table 181. VLDO1 control register (VLDO1CTL)



Notes

143. Read: Anytime Write: Anytime

144. Default value depends on OTP content.

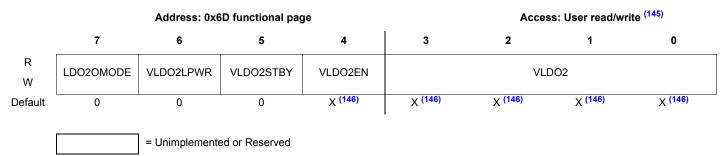
Table 182. VLDO1CTL field descriptions

| Field | Description |
|----------------|--|
| 7 LDO10MODE | VLDO1 OFF mode bit—LDO10MODE is used to configure VLDO1 operating mode when a PWRON turn-off event occurs. VLDO1 in OFF mode if a PWRON turn off event occurs VLDO1 in sleep mode if a PWRON turn off event occurs |
| 6 VLDO1LPWR | VLDO1 Low-power mode enable bit— When VLDO1LPWR is set to 1, VLDO1 can enter Low-power mode per the conditions in the Table 66. 1 Low-power mode enabled |
| 5 VLDO1STBY | VLDO1 standby enable bit— When VLDO1STBY is set to 1, VLDO1 is turned off during standby mode. Refer to Table 66. 0 VLDO1 is ON during standby mode. 1 VLDO1 is OFF during standby mode. |
| 4 VLDO1EN | VLDO1 enable bit — VLDO1EN is used to enable or disable the VLDO1 regulator. 0 VLDO1 disabled 1 VLDO1 enabled |
| 3:0 VLDO1 | VLDO1 output voltage configuration— Refer to Table 62. |

6.6.5.3.44 VLDO2 control register (VLDO2CTL)

This register is used to configure output voltage, normal, and standby mode operation of the VLDO2 regulator.

Table 183. VLDO2 control register (VLDO2CTL)



Notes

145. Read: Anytime Write: Anytime

146. Default value depends on OTP content.

Table 184. VLDO2CTL field descriptions

| Field | Description |
|----------------|--|
| 7 LDO2OMODE | VLDO2 OFF mode bit—LDO2OMODE is used to configure VLDO2 operating mode when a PWRON turn-off event occurs. 0 VLDO2 in OFF mode if a PWRON turn off event occurs 1 VLDO2 in Sleep mode if a PWRON turn off event occurs |
| 6 VLDO2LPWR | VLDO2 low-power mode enable bit— When VLDO2LPWR is set to 1, VLDO2 can enter low-power mode per the conditions in the LDO control table. 0 Low-power mode disabled 1 Low-power mode enabled |
| 5 VLDO2STBY | VLDO2 standby enable bit— When VLDO2STBY is set to 1, VLDO2 is turned off during standby mode. Refer to Table 66. 0 VLDO2 is ON during standby mode. 1 VLDO2 is OFF during standby mode. |
| 4 VLDO2EN | VLDO2 enable bit — VLDO2EN is used to enable or disable the VLDO2 regulator. 0 VLDO2 disabled 1 VLDO2 enabled |
| 3:0 VLDO2 | VLDO2 output voltage configuration— Refer to Table 62. |

6.6.5.3.45 VCC_SD control register (VCC_SDCTL)

This register is used to configure output voltage, normal and standby mode operation of the VCC_SD regulator.

Table 185. CC_SD control register (VCC_SDCTL)

| | Address: 0x6E functional page | | | | Access: User read/write (147) | | | |
|---------|-------------------------------|----------------|----------------|--------------------|-------------------------------|---|--------------------|--------------------|
| | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
| R W | VCC_SDOMOD E | VCC_SDLPWR | VCC_SDSTBY | VCC_SDEN | | | VCC | C_SD |
| Default | 0 | 0 | 0 | X ⁽¹⁴⁸⁾ | 0 | 0 | X ⁽¹⁴⁸⁾ | X ⁽¹⁴⁸⁾ |
| | | = Unimplemente | ed or Reserved | | | | | |

Notes

147. Read: Anytime Write: Anytime

148. Default value depends on OTP content.

Table 186. VCC_SDCTL field descriptions

| Field | Description |
|------------------|---|
| 7 VCC_SDOMODE | VCC_SD OFF mode bit— VCC_SDOMODE is used to configure VCC_SD operating mode when a PWRON turn-off event occurs. 0 VCC_SD in OFF mode if a PWRON turn off event occurs 1 VCC_SD in Sleep mode if a PWRON turn off event occurs |
| 6 VCC_SDLPWR | VCC_SD low-power mode enable bit— When VCC_SDLPWR is set to 1, VCC_SD can enter low-power mode per the conditions in the Table 66. 1 Low-power mode disabled 2 Low-power mode enabled |
| 5 VCC_SDSTBY | VCC_SD standby enable bit— When VCC_SDSTBY is set to 1, VCC_SD is turned off during standby mode. Refer to Table 66. 0 VCC_SD is ON during standby mode. 1 VCC_SD is OFF during standby mode. |
| 4 VCC_SDEN | VCC_SD enable bit — VCC_SDEN is used to enable or disable the VCC_SD regulator. 0 VCC_SD disabled 1 VCC_SD enabled |
| 1:0 VCC_SD | VCC_SD output voltage configuration— Refer to Table 65. |

6.6.5.3.46 V33 control register (V33CTL)

This register is used to configure output voltage, normal, and standby mode operation of the V33 regulator.

Table 187. V33 control register (V33CTL)

| | Addı | ess: 0x6F functi | onal page | | | Access: User | read/write (149) | |
|---------|----------|------------------|----------------|--------------------|---|--------------|--------------------|--------------------|
| | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
| R W | V33OMODE | V33LPWR | V33STBY | V33EN | | | V | 33 |
| Default | 0 | 0 | 0 | X ⁽¹⁵⁰⁾ | 0 | 0 | X ⁽¹⁵⁰⁾ | X ⁽¹⁵⁰⁾ |
| | | = Unimplemente | ed or Reserved | | | | | |

Notes

149. Read: Anytime Write: Anytime

150. Default value depends on OTP content.

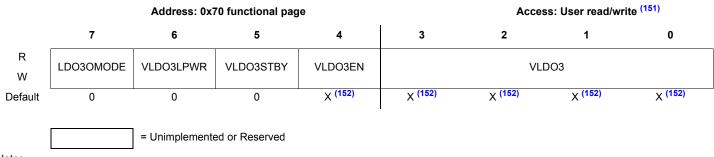
Table 188. V33CTL field descriptions

| Field | Description |
|---------------|--|
| 7 V33OMODE | V33 OFF mode bit— V33OMODE is used to configure V33 operating mode when a PWRON turn-off event occurs. V33 in OFF mode if a PWRON turn off event occurs V33 in sleep mode if a PWRON turn off event occurs |
| 6 V33LPWR | V33 low-power mode enable bit— When V33LPWR is set to 1, V33 can enter low-power mode per the conditions in the Table 66. 0 Low-power mode disabled 1 Low-power mode enabled |
| 5 V33STBY | V33 standby enable bit— When V33STBY is set to 1, V33 is turned off during standby mode. Refer to Table 66. 0 V33 is ON during standby mode. 1 V33 is OFF during standby mode. |
| 4 V33EN | V33 Enable bit — V33EN is used to enable or disable the VLDO2 regulator. 0 V33 disabled 1 V33 enabled |
| 1:0 V33 | V33 output voltage configuration— Refer to Table 64. |

6.6.5.3.47 VLDO3 control register (VLDO3CTL)

This register is used to configure output voltage, normal, and standby mode operation of the VLDO3 regulator.

Table 189. VLDO3 control register (VLDO3CTL)



Notes

151. Read: Anytime Write: Anytime

152. Default value depends on OTP content.

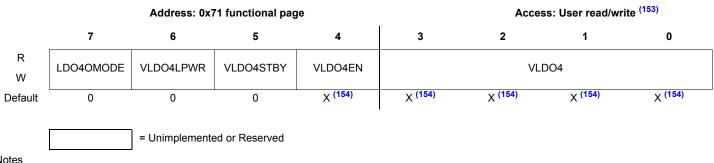
Table 190. VLDO3CTL field descriptions

| Field | Description |
|----------------|--|
| 7 LDO3OMODE | VLDO3 OFF mode bit—LDO3OMODE is used to configure VLDO3 operating mode when a PWRON turn-off event occurs. 0 VLDO3 in OFF mode if a PWRON turn off event occurs 1 VLDO3 in sleep mode if a PWRON turn off event occurs |
| 6 VLDO3LPWR | VLDO3 low-power mode enable bit— When VLDO3LPWR is set to 1, VLDO3 can enter low-power mode per the conditions in the Table 66. 1 Low-power mode enabled |
| 5 VLDO3STBY | VLDO3 standby enable bit— When VLDO3STBY is set to 1, VLDO3 is turned off during standby mode. Refer to Table 66. 0 VLDO3 is ON during standby mode. 1 VLDO3 is OFF during standby mode. |
| 4 VLDO3EN | VLDO3 enable bit — VLDO3EN is used to enable or disable the VLDO3 regulator. 0 VLDO3 disabled 1 VLDO3 enabled |
| 3:0 VLDO3 | VLD03 output voltage configuration— Refer to Table 63. |

6.6.5.3.48 VLDO4 control register (VLDO4CTL)

This register is used to configure output voltage, normal, and standby mode operation of the VLDO4 regulator.

Table 191. VLDO4 control register (VLDO4CTL)



Notes

153. Read: Anytime

Write: Anytime

Default value depends on OTP content.

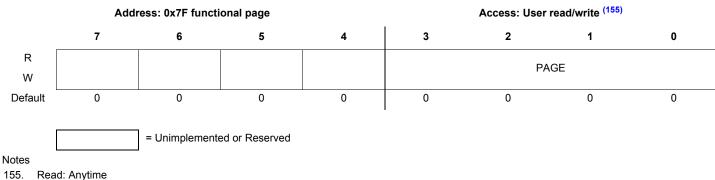
Table 192. VLDO4CTL field descriptions

| Field | Description |
|----------------|--|
| 7 LDO4OMODE | VLDO4 OFF mode bit—LDO4OMODE is used to configure VLDO4 operating mode when a PWRON turn-off event occurs. ULDO4 in OFF mode if a PWRON turn off event occurs VLDO4 in sleep mode if a PWRON turn off event occurs |
| 6 VLDO4LPWR | VLDO4 low-power mode enable bit— When VLDO4LPWR is set to 1, VLDO4 can enter low-power mode per the conditions in the Table 66. 1 Low-power mode enabled |
| 5 VLDO4STBY | VLDO4 standby enable bit— When VLDO4STBY is set to 1, VLDO4 is turned off during standby mode. Refer to Table 66. 0 VLDO4 is ON during standby mode. 1 VLDO4 is OFF during standby mode. |
| 4 VLDO4EN | VLDO4 enable bit — VLDO4EN is used to enable or disable the VLDO4 regulator. 0 VLDO4 disabled 1 VLDO4 enabled |
| 3:0 VLDO4 | VLDO4 output voltage configuration— Refer to Table 63. |

6.6.5.3.49 Page selection register

This register is used to access the extended register pages.

Table 193. Page selection register



Write: Anytime

PF3000

101

Table 194. Page register field descriptions

| Field | Description |
|-------------|--|
| 3:0 PAGE | Register page selection — The PAGE field is used to select one of the three available register pages. 0000 Functional page selected 0001 Extended page 1 selected 0010 Extended page 2 selected |

6.6.6 Register map

The register map is comprised of thirty-two pages, and its address and data fields are each eight bits wide. Only the first two pages can be accessed. On each page, registers 0 to 0x7F are referred to as 'functional', and registers 0x80 to 0xFF as 'extended'. On each page, the functional registers are the same, but the extended registers are different. To access registers in Extended page 1, one must first write 0x01 to the page register at address 0x7F, and to access registers Extended page 2, one must first write 0x02 to the page register at address 0x7F. To access the Functional page from one of the extended pages, no write to the page register is necessary.

Registers that are missing in the sequence are reserved; reading from them returns a value 0x00, and writing to them has no effect. The contents of all registers are given in the tables defined in this chapter; each table is structure as follows:

Name: Name of the bit

Bit #: The bit location in the register (7-0) **R/W:** Read / Write access and control

- · R is read-only access
- · R/W is read and write access
- · RW1C is read and write access with write 1 to clear

Reset: Reset signals are color coded based on the following legend.

| Bits reset by SC and VCOREDIG_PORB |
|--|
| Bits reset by PWRON or loaded default or OTP configuration |
| Bits reset by DIGRESETB |
| Bits reset by PORB or RESETBMCU |
| Bits reset by VCOREDIG_PORB |
| Bits reset by POR or OFFB |

Default: The value after reset, as noted in the default column of the memory map.

- · Fixed defaults are explicitly declared as 0 or 1.
- "X" corresponds to Read/Write bits that are initialized at start-up, based on the OTP fuse settings or default if V_{DDOTP} = 1.5 V. Bits are subsequently I²C modifiable, when their reset has been released. "X" may also refer to bits that may have other dependencies. For example, some bits may depend on the version of the IC, or a value from an analog block, for instance the sense bits for the interrupts.

6.6.6.1 Register map

Table 195. Functional page

| | | | | | | | BITS | [7:0] | | | |
|------|---------------|------------|------------------|---------------------|-------------------------|-----------------|-----------------|---------------|------------------|-----------------|-----------------|
| Add | Register name | R/W | Default | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
| 00 | DeviceID | R | 8'b0011_0000 | - | - | - | - | | DEVICE | ID [3:0] | |
| 00 | Deviceib | K | 0.00011_0000 | 0 | 0 | 1 | 1 | 0 | 0 | 0 | 0 |
| 03 | SILICONREVI | R | 8'b0001 0000 | FULL_LAYER_REV[3:0] | | | | METAL_LAY | ER_REV[3:0] | | |
| 03 | D | K | 8'b0001_0000 | 0 | 0 | 0 | 1 | 0 | 0 | 0 | 0 |
| 04 | FABID | R | 8'b0000_0000 | - | - | - | - | FAB | [1:0] | FIN | [1:0] |
| 04 | TABID | IX. | 0.0000_0000 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| 05 | INTSTAT0 | RW1C | 8'b0000_0000 | - | - | THERM130I | THERM125I | THERM120I | THERM110I | LOWVINI | PWRONI |
| 03 | INISTATO | KWIO | 0.00000_0000 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| 06 | INTMASK0 | R/W | 8'b0011_1111 | - | - | THERM130M | THERM125M | THERM120M | THERM110M | LOWVINM | PWRONM |
| 00 | INTIMACIO | 1000 | 0.00011_1111 | 0 | 0 | 1 | 1 | 1 | 1 | 1 | 1 |
| 07 | INTSENSE0 | R | 8'b00xx_xxxx | VDDOTPS | ICTESTS | THERM130S | THERM125S | THERM120S | THERM110S | LOWVINS | PWRONS |
| O1 | INTOLNOLO | IX. | 0 00000 | 0 | 0 | х | х | х | х | х | х |
| 08 | INTSTAT1 | RW1C | 8'b0000_0000 | - | - | - | SW3FAULTI | SW2FAULTI | - | SW1BFAULTI | SW1AFAULTI |
| 00 | INISIAII | 14410 | 0.50000_0000 | 0 | 0 | 0 | 0 | 0 | х | 0 | 0 |
| 09 | INTMASK1 | TMASK1 R/W | R/W 8'b0111_1111 | ı | - | - | SW3FAULTM | SW2FAULTM | - | SW1BFAULTM | SW1AFAULTM |
| 00 | IIVIW/ CITT | | | 0 | 1 | 1 | 1 | 1 | 1 | 1 | 1 |
| 0A | INTSENSE1 | R | R 8'b0xxx_xxxx | ı | - | _ | SW3FAULTS | SW2FAULTS | _ | SW1BFAULTS | SW1AFAULTS |
| 0, 1 | | | 0.20,000_,0000 | 0 | х | x | х | х | х | х | x |
| 0E | INTSTAT3 | RW1C | 8,90000_0000 | OTP_ECCI | OTP AUTO BLOW DONE | - | - | - | VPWROVI | - | SWBSTFAULT I |
| | | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| 0F | INTMASK3 | R/W | 8'b1100_0101 | OTP_ECCM | OTP_AUTO_B LOW_DONEM | - | - | - | VPWROVI | - | SWBSTFAULT M |
| | | | | 1 | 1 | 0 | 0 | 0 | 1 | 0 | 1 |
| 10 | INTSENSE3 | R | 8'b0000_000x | OTP_ECCS | OTP_AUTO_B LOW_DONES | - | - | - | VPWROVS | - | SWBSTFAULT S |
| | | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| 11 | INTSTAT4 | RW1C | 8'b0000_0000 | - | - | VLDO4FAULTI | VLDO3FAULTI | V33FAULTI | VCC_SDFAUL TI | VLDO2FAULTI | VLDO1FAULTI |
| | | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| 12 | INTMASK4 | R/W | 8'b0011_1111 | - | - | VLDO4 FAULTM | VLDO3 FAULTM | V33 FAULTM | VCC_SDFAUL TM | М | VLDO1FAULT M |
| | | | | 0 | 0 | 1 | 1 | 1 | 1 | 1 | 1 |
| 13 | INTSENSE4 | R | 8'b00xx_xxxx | - | - | VLDO4 FAULTS | VLDO3 FAULTS | V33 FAULTS | VCC_SD FAULTS | VLDO2 FAULTS | VLDO1 FAULTS |
| | | | | 0 | 0 | х | х | х | х | х | х |
| 1A | COINCTL | R/W | R/W 8'b0000_0000 | - | - | - | - | COINCHEN | | VCOIN[2:0] | |
| | | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |

Table 195. Functional page (continued)

| | | | | BITS[7:0] | | | | | | | | |
|-----|---------------|------------------|------------------|-----------|------------------|-----------|-----------|--------|--------------|----------------|-----------|--|
| Add | Register name | R/W | Default | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 | |
| 1B | PWRCTL | R/W | 8'b0001_0000 | REGSCPEN | STANDBYINV | STBYD | DLY[1:0] | PWRONB | DBNC[1:0] | PWRONRSTE N | RESTARTEN | |
| | | | | 0 | 0 | 0 | 1 | 0 | 0 | 0 | 0 | |
| 1C | MEMA | R/W | 8'b0000_0000 | | | | MEM | A[7:0] | | | | |
| | | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | |
| 1D | MEMB | R/W | 8'b0000_0000 | | 1 | I | MEM | B[7:0] | 1 | _ | 1 | |
| | | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | |
| 1E | MEMC | R/W | 8'b0000_0000 | | ı | | MEM | C[7:0] | ı | _ | | |
| | | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | |
| 1F | MEMD | R/W 8'b0000_0000 | | | T | T | MEM | D[7:0] | T | | T | |
| | | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | |
| 20 | SW1AVOLT | R/W | 8'b000x_xxxx | - | - | - | | i | SW1A[4:0] | | | |
| | | | | 0 | 0 | 0 | - | - | - | - | - | |
| 21 | SW1ASTBY | R/W | 8'b000x_xxxx | - | - | - | | i | SW1ASTBY[4:0 |] | | |
| | | | | 0 | 0 | 0 | - | - | - | - | - | |
| 22 | SW1AOFF R/W | R/W | 8'b000x_xxxx | - | - | - | | | SW1AOFF[4:0] | | | |
| | | | | 0 | 0 | 0 | - | - | - | - | - | |
| 23 | SW1AMODE | R/W | R/W 8'b0000_xxxx | - | - | SW1AOMODE | - | | SW1AM | IODE[3:0] | | |
| | | | _ | 0 | 0 | 0 | х | - | - | - | - | |
| 24 | SW1ACONF | R/W | 8'bxx00_0100 | - | SW1ADVSSP EED | SW1APH | HASE[1:0] | SW1AFI | REQ[1:0] | - | SW1AILIM | |
| | | | | x | -1 | 0 | 0 | - | - | 0 | 0 | |
| 2E | SW1BVOLT | R/W | 8'b0xx1_0010 | - | - | - | | | SW1B[4:0] | | | |
| | | | | 0 | х | х | 1 | 0 | 0 | 0 | 0 | |
| 2F | SW1BSTBY | R/W | 8'b0xx1_0010 | - | - | - | | | SW1BSTBY[4:0 |] | | |
| | GW120121 | | 0 200K1_0010 | 0 | х | х | 1 | 0 | 0 | 1 | 0 | |
| 30 | SW1BOFF | R/W | 8'b0xx1_0010 | ı | _ | _ | | | SW1BOFF[4:0] | | | |
| 00 | OWIDOTT | 1077 | 0 B0XX1_0010 | 0 | х | x | 1 | 0 | 0 | 1 | 0 | |
| 31 | SW1BMODE | R/W | 8'b0001 1000 | 1 | - | SW1BOMODE | - | | SW1BM | IODE[3:0] | | |
| 01 | OWIDMODE | 1077 | 0 00001_1000 | 0 | 0 | 0 | - | - | - | - | - | |
| 32 | SW1BCONF | R/W | 8'bx100_0100 | - | SW1BDVS SPEED | SW1BPF | HASE[1:0] | SW1BFI | REQ[1:0] | - | SW1BILIM | |
| | | | | х | - | 0 | 0 | - | - | 0 | 0 | |
| 35 | SW2VOLT | R/W | 8'b0xxx 0110 | - | - | - | - | SW2_HI | | SW2[2:0] | | |
| 35 | SWZVOLI | FV/VV | 9 DOXXX_0110 | 0 | х | х | х | - | - | - | _ | |
| 36 | OMOGTON | R/W | RIPONAL ANDER | - | - | - | - | SW2_HI | | SW2STBY[2:0] | | |
| 30 | SW2STBY | FV VV | 8'b0xxx_xxxx | 0 | х | х | х | - | - | - | _ | |
| 37 | SW2OFF | R/W | 8'b0xxx_xxxx | - | - | - | - | SW2_HI | | SW2STBY[2:0] | | |
| 31 | GVVZUFF | IVVV | 0.00447_4444 | 0 | х | х | х | - | - | - | _ | |

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Table 195. Functional page (continued)

| | | | | | BITS[7:0] | | | | | | | | |
|------|---------------|--------|------------------|-----------------|-----------------|-------------|-----------|--------|----------------|---------------|-----------|--|--|
| Add | Register name | R/W | Default | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 | | |
| 38 | SW2MODE | R/W | 8'b0010_1000 | - | - | SW2OMODE | - | | SW2M0 | DDE[3:0] | | | |
| 30 | SWZIMODE | IVVV | 0.00010_1000 | 0 | 0 | 1 | 0 | 1 | 0 | 0 | 0 | | |
| 39 | SW2CONF | R/W | 8'bxx01_0100 | - | SW2DVS SPEED | SW2PH | ASE[1:0] | SW2FF | REQ[1:0] | - | SW2ILIM | | |
| | | | | × | - | 0 | 1 | - | - | 0 | 0 | | |
| 3C | SW3VOLT | R/W | 8'b0xxx_1100 | - | - | - | _ | | SW3 | 3[3:0] | | | |
| 00 | CWOVOET | 1077 | 0 DOXXX_1100 | 0 | х | х | x | 1 | - | - | - | | |
| 3D | SW3STBY | R/W | 8'b0xxx_1100 | - | - | - | - | | SW3ST | TBY[3:0] | | | |
| 0.5 | 0.1100.12.1 | | 0.000.000_1.100 | 0 | х | х | х | ı | _ | - | - | | |
| 3E | SW3OFF | R/W | 8'b0xxx_1100 | - | - | - | - | | SW3O | FF[3:0] | | | |
| OL. | 0110011 | 1077 | 0.000000 | 0 | х | x | х | ı | - | - | ī | | |
| 3F | SW3MODE | R/W | 8'b0011_1000 | - | - | SW3OMODE | _ | | SW3M0 | DDE[3:0] | | | |
| OI . | OWOMODE | 1000 | 0.00011_1000 | 0 | 0 | 1 | 1 | 1 | 0 | 0 | 0 | | |
| 40 | SW3CONF | R/W | 8'bxx10_0100 | - | SW3DVS SPEED | SW3PH | ASE[1:0] | SW3FF | REQ[1:0] | - | SW3ILIN | | |
| | | | | x | - | 1 | 0 | - | - | 0 | 0 | | |
| 66 | SWBSTCTL R/W | | 8'b0xx0_10xx | - | SWBST1STE | BYMODE[1:0] | - | SWBST1 | MODE[1:0] - | SWBST1 | VOLT[1:0] | | |
| | | | | 0 | - | - | 0 | ı | - | - | ī | | |
| 69 | 9 LDOGCTL | R/W | R/W 8'b0xxx_xxx0 | - | - | - | _ | - | - | - | STBY_LP | | |
| 00 | 2200012 | | 0.000.000_00.00 | 0 | х | х | х | х | х | х | х | | |
| 6A | VREFDDRCTL | R/W 8' | 8'b000x_0000 | _ | _ | _ | VREFDDREN | - | _ | - | - | | |
| | | | | 0 | 0 | 0 | - | 0 | 0 | 0 | 0 | | |
| 6B | VSNVSCTL | R/W | 8'b0000_0110 | - | - | - | - | - | , | VSNVSVOLT[2:0 |)] | | |
| | | | | 0 | 0 | 0 | 0 | 0 | 1 | 1 | 0 | | |
| 6C | VLDO1CTL | R/W | 8'b010x_1110 | LDO10MODE | VLDO1LPWR | VLDO1STBY | VLDO1EN | | VLDC | 01[3:0] | | | |
| | , | | | 0 | 0 | 0 | - | - | - | - | _ | | |
| 6D | VLDO2CTL | R/W | 8'b000x_1000 | LDO2OMODE | VLDO2LPWR | VLDO2STBY | VLDO2EN | | VLDC | 02[3:0] | | | |
| | , | | | 0 | 0 | 0 | - | - | - | - | _ | | |
| 6E | VCC_SDCTL | R/W | 8'b000x_xx10 | VCC_SDOMO DE | VCC_SDLPW R | VCC_SDSTBY | VCC_SDEN | - | - | vcc_ | SD[1:0] | | |
| | | | | 0 | 0 | 0 | - | x | х | _ | - | | |
| 6F | V33CTL | R/W | 8'b000x_xx10 | V33OMODE | V33LPWR | V33STBY | V33EN | - | - | V33 | B[1:0] | | |
| | | | | 0 | 0 | 0 | - | x | х | _ | - | | |
| 70 | VLDO3CTL | R/W | 8'b010x_0000 | VLDO3OMOD E | VLD03LPWR | VLDO3STBY | VLDO3EN | | VLDC | 03[3:0] | | | |
| | | | 1 | 0 | 0 | 0 | - | - | - | - | - | | |
| 71 | VLDO4CTL | R/W | 8'b000x_xxxx | VLDO4OMOD E | VLDO4LPWR | VLDO4STBY | VLDO4EN | | 1 | 04[3:0] | | | |
| | | | ļ | 0 | 0 | 0 | - | - | - | - | _ | | |
| 7F | Page Register | R/W | 8'b0000_0000 | - | - | - | | | PAGE[4:0] | ı | | | |
| | | | _ | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | | |

Table 196. Extended page 1

| Address | Register | TVDE | Default | BITS[7:0] | | | | | | | | |
|---------|---------------------|--------------|---------------|-----------|-----------|-----------------|-----------|------------|--------------|-------------------------|---------------------|--|
| Address | Name | TYPE | Default | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 | |
| 80 | OTP FUSE READ EN | R/W | 8'b000x_xxx0 | - | - | - | - | - | - | - | OTP FUSE READ EN | |
| | NEAD EIV | | | 0 | 0 | 0 | х | х | х | х | х | |
| 84 | OTP LOAD MASK | R/W | 8'b0000_0000 | START | RL PWBRTN | FORCE PWRCTL | RL PWRCTL | RL OTP | RL OTP ECC | RL OTP FUSE | RL TRIM FUSE | |
| | | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | |
| 8A | OTP ECC SE1 | R | 8'bxxx0_0000 | - | - | - | ECC5_SE | ECC4_SE | ECC3_SE | ECC2_SE | ECC1_SE | |
| | | | _ | х | х | х | 0 | 0 | 0 | 0 | 0 | |
| 8B | RSVD | R | 8'bxxx0_0000 | | | | | | | | | |
| | | | | _ | _ | _ | ECC5_DE | ECC4_DE | ECC3_DE | ECC2_DE | ECC1_DE | |
| 8C | OTP ECC DE1 | R | 8'bxxx0_0000 | х | х | x | 0 | 0 | 0 | 0 | 0 | |
| | | | | | | | | | | | | |
| 8D | RSVD | R | 8'bxxx0_0000 | | | | | | | | | |
| | | | | | | | | OT | P SW1A VOLT[| 4:0] | | |
| A0 | OTP SW1A VOLT | R/W | 8'b00xx_xxxx | x | х | x | х | x | x | x | х | |
| | OTD OWAA | | | | | | | | 01 | - P_SW1A_SEQ[| <u>[</u> 2:0] | |
| A1 | OTP SW1A SEQ | | | | | | | | | | | |
| | OTP SW1x | | | - | - | - | - | OTP_SW1_0 | CONFIG[1:0] | OTP_SW1 | _FREQ[1:0] | |
| A2 | CONFIG | R/W | 8'b000x_xxXx | х | х | х | х | х | x | х | х | |
| | OTP SW1B | DAM SILO | | | | | | ОТ | P_SW1B_VOLT[| 4:0] | L | |
| A8 | VOLT | R/W | 8'b00xx_xxxx | х | х | х | х | x | x | х | х | |
| 40 | OTP SW1B | DAM | 011-00 | | | | | | 07 | P_SW1B_SEQ[| 2:0] | |
| A9 | SEQ | R/W | 8'b00xx_xxxx | х | х | х | х | х | х | x | х | |
| | DOV/D | DAM | 011-00 | | | | | | | | | |
| AA | RSVD | R/W | 8'b00xx_xxxx | x | х | х | х | x | x | х | х | |
| 4.0 | OTP SW2 | DAY | 011-0 | | | | | OTP_SW2_HI | 01 | rp_sw2_volt[2 | 2:0] | |
| AC | VOLT | R/W | 8'b0xxx_xxxx | х | х | х | х | х | х | х | х | |
| AD | OTP SW2 SEQ | R/W | OlbOvan vanar | | | | | - | 0 | TP_SW2_SEQ[2 | :0] | |
| AD | OTF SW2 SEQ | PC/VV | 8'b0xxx_xxxx | х | х | х | х | х | х | х | х | |
| ۸۲ | OTP SW2 | R/W | 0!h0000 00w | _ | - | - | - | - | - | OTP_SW2 | _FREQ[1:0] | |
| AE | CONFIG | R/W | 8'b0000_00xx | 0 | 0 | 0 | х | х | 0 | х | х | |
| В0 | OTP SW3 | R/W | OlbOvan vanar | | | | - | | OTP_SW3 | _VOLT[3:0] | | |
| ВО | VOLT | FC/VV | 8'b0xxx_xxxx | х | х | х | х | х | х | х | х | |
| B1 | OTD OWN OFO | 8'h0vvv vvvv | | | | | - | 0 | TP_SW3_SEQ[2 | :0] | | |
| DI | OTP SW3 SEQ | R/W | 8'b0xxx_xxxx | х | х | х | х | х | х | х | х | |
| B2 | OTP SW3 | R/W | 8'h0vvv vvvv | | | | - | | | OTP_SW3 | _FREQ[1:0] | |
| υz | CONFIG | IV VV | 8'b0xxx_xxxx | х | х | х | х | х | х | х | х | |
| BC | OTP SWBST | R/W | 8'b0000_00xx | _ | - | - | - | - | - | OTP_SWBS | T_VOLT[1:0] | |
| 50 | VOLT | 10.44 | 3 50000_00XX | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | |

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Table 196. Extended page 1 (continued)

| Addross | Register | TYPE | Dofault | | | | вітѕ | [7:0] | | | |
|------------|-------------------|-------|------------------|---------|---|---|-------------------|-------|-------------------|--------------|-----------------------|
| Address | Name | TTPE | Default | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
| BD | OTP SWBST | R/W | 8'b0000_xxxx | 1 | - | - | - | ı | ОТІ | P_SWBST_SEQ | [2:0] |
| 55 | SEQ | 1011 | O DOGGO_XXXX | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| C0 | OTP VSNVS | R/W | 8'b0000_0xxx | _ | _ | - | - | - | OTF | VSNVS_VOLT | [2:0] |
| | VOLT | | 0.50000_0,000 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| C4 | RSVD | R/W | 8'b000x_x0xx | - | - | - | - | - | - | - | - |
| | | | | 0 | 0 | 0 | х | х | х | х | х |
| C8 | OTP VLDO1 VOLT | R/W | 8'b0000_xxxx | | | | | | OTP_VLDO | 1_VOLT[3:0] | |
| | VOLT | | _ | 0 | 0 | 0 | 0 | х | х | х | х |
| C9 | OTP VLDO1 | R/W | 8'b0000_xxxx | | | | | | OTP_VLDO | 1_SEQ[3:0] | |
| | SEQ | | _ | 0 | 0 | 0 | 0 | х | х | х | х |
| СС | OTP VLDO2 | R/W | 8'b0000_xxxx | | | | | | OTP_VLDO: | 2_VOLT[3:0] | |
| | VOLT | | _ | 0 | 0 | 0 | 0 | х | х | х | х |
| CD | OTP VLDO2 | R/W | 8'b0000 xxxx | | | | | | OTP_VLDO | 2_SEQ[3:0] | |
| | SEQ | | | 0 | 0 | 0 | 0 | x | х | х | х |
| D0 | OTP VCC_SD | R/W | 8'b0000_xxxx | | | | | - | | OTP_VCC_9 | SD_VOLT[2:0] |
| 20 | VOLT | | 0.0000_,0.00 | 0 | 0 | 0 | 0 | х | х | x | х |
| D1 | D1 OTP VCC_SD | R/W | W 8'b0000_xxxx | | | | | | OTF | VCC_SD_SEC | Q[2:0] |
| J. | SEQ | | 0.0000_,0.00 | 0 | 0 | 0 | 0 | 0 | х | x | х |
| D4 | OTP V33 | R/W | R/W 8'b0000_xxxx | | | | | | | OTP_V33 | _VOLT[2:0] |
| ٥. | VOLT | | 0.0000_,0.00 | 0 | 0 | 0 | 0 | х | х | x | х |
| D5 | OTP V33 SEQ | R/W | 8'b0000_xxxx | | | | | | 0 | TP_V33_SEQ[3 | :0] |
| 20 | 011 100 024 | | 0.0000_,0.00 | 0 | 0 | 0 | 0 | х | х | x | х |
| D8 | OTP VLDO3 | R/W | 8'b0000_xxxx | | | | | | OTP_VLDO: | 3_VOLT[3:0] | |
| 50 | VOLT | 1000 | 0.00000_xxxx | 0 | 0 | 0 | 0 | х | х | х | х |
| D9 | OTP VLDO3 | R/W | 8'b0000_xxxx | | | | | | OTP_VLDO | 3_SEQ[3:0] | |
| <i>D</i> 3 | SEQ | 1000 | 0.00000_xxxx | 0 | 0 | 0 | 0 | х | x | х | х |
| DC | OTP VLDO4 | R/W | 8'b0000_xxxx | | | | | | OTP_VLDO | 4_VOLT[3:0] | |
| | VOLT | | | 0 | 0 | 0 | 0 | х | х | х | х |
| DD | OTP VLDO4 | R/W | 8'b0000_xxxx | | | | | | OTP_VLDO | 4_SEQ[3:0] | |
| | SEQ | | | 0 | 0 | 0 | 0 | х | х | х | х |
| E0 | OTP PU CONFIG1 | R/W | 8'b000x_xxxx | | | | OTP_PWRON _CFG | | OTP_SWDVS _CLK | | OTP_SEQ_CL K_SPEED |
| | | | | x | х | х | х | x | х | х | х |
| E4 | OTP FUSE | R/W | 8'b0000_00x0 | TBB_POR | - | - | - | - | - | - | - |
| | POR1 | | | 0 | 0 | 0 | 0 | 0 | 0 | х | 0 |
| E5 | RSVD | R/W | 8'b0000_00x0 | - | _ | - | _ | - | _ | | - |
| | T.OVD | 1000 | 3 50000_0000 | 0 | 0 | 0 | 0 | 0 | 0 | | 0 |
| E6 | RSVD | R/W | 8'b0000_00x0 | - | - | _ | - | - | - | | - |
| LU | 1.000 | 17/14 | 0.50000_00000 | 0 | 0 | 0 | 0 | 0 | 0 | | 0 |

Table 196. Extended page 1 (continued)

| Address | Register | TYPE | Default | | | | BITS | [7:0] | | | |
|---------|---|-------|------------------|---------------------|---|---|------|--------------------|-----|---------------|-----------|
| Audiess | Name | 1112 | Delauit | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
| E7 | RSVD | R | 8'b0000_00x0 | - | ı | - | - | - | - | | - |
| 2, | Er ROVE | · · | 0.0000_0000 | 0 | 0 | 0 | 0 | 0 | 0 | | 0 |
| E8 | OTP PWRGD | R/W/M | 8'b0000_000x | - | ı | - | _ | - | _ | _ | OTP_PG_EN |
| 23 | EN | | 8 DUUUU_000X | 0 | 0 | 0 | 0 | 0 | 0 | х | 0 |
| F0 | RSVD | R/W | R/W 8'b000x_xxxx | - | - | - | | | | | |
| | | | | 0 | 0 | 0 | x | х | x | х | х |
| F1 | RSVD | R/W | R/W 8'b000x_xxxx | - | - | - | | | | | |
| | 1.075 | | | 0 | 0 | 0 | x | х | x | х | х |
| F7 | OTP BLOWN | R/W | 8'b0000_000x | - | - | - | - | - | - | - | OTP_BLOWN |
| | 011 5201111 | | 0 00000_000x | 0 | 0 | 0 | 0 | 0 | 0 | 0 | х |
| FF | OTP I2C ADDR | | 8'b0000_1xxx | USE_DEFAUL T_ADD | | - | | I2C_SLV ADDR[3] | ОТР | _I2C_SLV ADDF | R[2:0] |
| | ,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,, | | | 0 | 0 | 0 | 0 | 1 | x | x | х |

Table 197. Extended page 2

| Address | Register | TYPE | Default | | | | BITS | 6[7:0] | | | | |
|---------|----------------------|------|---------------|--------------------------------|---------|-------|---------------------|---------------------|-----------------------|----------------------|-----------------------|--|
| Address | Name | 1172 | Delault | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 | |
| 81 | SW1A | R/W | 8'b1111 1111 | RSVD | RSVD | RSVD | RSVD | RSVD | RSVD SW1A_PWRSTG[2:0] | | | |
| 01 | PWRSTG | F/VV | 801111_1111 | 1 | 1 | 1 | 1 | 1 | 1 | 1 | 1 | |
| 83 | SW1B PWRSTG | R | 8'b1111_1111 | RSVD | RSVD | RSVD | RSVD | RSVD | | | 3_PWRSTG[2:0] RSVD | |
| | 1 1111010 | | | 1 | 1 | 1 | 1 | 1 | 1 | 1 | 1 | |
| 84 | SW2 PWRSTG | R | 8'b1111 1111 | RSVD | RSVD | RSVD | RSVD | RSVD | S | W2_PWRSTG[2: RSVD | 0] | |
| | | | | 1 | 1 | 1 | 1 | 1 | 1 | 1 | 1 | |
| 85 | 85 SW3 PWRSTG | R | 8'b1111_1111 | RSVD | RSVD | RSVD | RSVD | RSVD | S | W3_PWRSTG[2: RSVD | 0] | |
| | | | | 1 | 1 | 1 | 1 | 1 | 1 | 1 | 1 | |
| 88 | PWRCTRL R | R | 8'b0000_0001 | - | - | - | - | - | - | OTP_PWRGD _EN | PG_SHDWN_ EN | |
| | | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 1 | |
| 8D | I2C WRITE ADDRESS | R/W | 8'b0000 0000 | | | I | 2C_WRITE_ADE | RESS_TRAP[7: | 0] | | | |
| 0.5 | TRAP | | 0.0000_0000 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | |
| 8E | I2C TRAP PAGE | R/W | 8,P0000_0000 | LET_IT_ ROLL | RSVD | RSVD | | 120 | C_TRAP_PAGE[4 | 4:0] | | |
| | PAGE | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | |
| 8F | I2C TRAP | R/W | 8'b0000 00000 | I2C_WRITE_ADDRESS_COUNTER[7:0] | | | | | | | | |
| | CNTR | | _ | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | |
| 90 | IO DRV | R/W | 8'b00xx xxxx | SDA_D | RV[1:0] | RS | VD | INTB_DRV[1:0] | | RESETBMO | CU_DRV[1:0] | |
| | | | _ | 0 | 0 | х | х | х | х | х | х | |
| D0 | OTP AUTO ECC0 | R/W | 8'b0000_0000 | - | - | - | AUTO_ECC _BANK5 | AUTO_ECC _BANK4 | AUTO_ECC_B ANK3 | AUTO_ECC _BANK2 | AUTO_ECC_B ANK1 | |
| | | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | |
| D8 | Reserved | _ | 8'b0000 0000 | | | | AUTO_BLO | W_TIME[7:0] | | | | |
| | | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | |
| D9 | Reserved | - | 8'b0000_0000 | START | RELOAD | EN_RW | AUTO_FUSE_ BLOW5 | AUTO_FUSE_ BLOW4 | AUTO_FUSE_ BLOW3 | AUTO_FUSE_ BLOW2 | AUTO_FUSE_ BLOW1 | |
| | | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | |

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Table 197. Extended page 2 (continued)

| Address | Register | TYPE | Default - | | | | вітя | 6[7:0] | | | | | |
|---------|----------------------|-----------------|------------------|------------------|-------------------|-------------------|-------------------|------------------|--------------------|--------------------|------------------|---------|--|
| Address | Name | ITPE | | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 | | |
| E1 | OTP ECC CTRL1 | R/W | 8'b0000_0000 | RSVD | ECC1_CALC_ CIN | ECC1_CIN_TBB[5:0] | | | | | | | |
| | OTALI | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | | |
| E2 | OTP ECC CTRL2 | R/W | 8,0000_0000 | RSVD | ECC2_CALC_ CIN | | ECC2_CIN_TBB[5:0] | | | | | | |
| | 011122 | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | | |
| E3 | OTP ECC CTRL3 | PECC RL3 R/W | 8'b0000_0000 | RSVD | ECC3_CALC_ CIN | | | ECC3_CIN | N_TBB[5:0] | | | | |
| | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | | | |
| E4 | E4 OTP ECC CTRL4 R/W | R/W | 8'b0000_0000 | RSVD | ECC4_CALC_ CIN | ECC4_CIN_TBB[5:0] | | | | | | | |
| | | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | | |
| E5 | OTP ECC CTRL5 | R/W | 8'b0000_0000 | RSVD | ECC5_CALC_ CIN | | | ECC5_CIN | N_TBB[5:0] | | | | |
| | OTILES | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | | |
| F1 | OTP FUSE CTRL1 | R/W | R/W 8'b0000_0000 | 1 | - | - | - | ANTIFUSE1_E N | ANTIFUSE1_L OAD | ANTIFUSE1_R W | BYPASS1 | | |
| | 011121 | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | | |
| F2 | OTP FUSE CTRL2 | R/W | 8'b0000_0000 | ı | - | ı | _ | ANTIFUSE2_E N | ANTIFUSE2_L OAD | ANTIFUSE2_R W | BYPASS2 | | |
| | OTTLE | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | | |
| F3 | OTP FUSE CTRL3 | R/W | R/W | R/W 8'b0000_0000 | - | - | - | - | ANTIFUSE3_E N | ANTIFUSE3_L OAD | ANTIFUSE3_R W | BYPASS3 | |
| | OTILES | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | | |
| F4 | OTP FUSE CTRL4 | R/W | 8'b0000_0000 | - | - | - | - | ANTIFUSE4_E | ANTIFUSE4_L OAD | ANTIFUSE4_R W | BYPASS4 | | |
| | OTAL | | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | | |
| F5 | OTP FUSE CTRL5 | R/W | 8'b0000_0000 | - | - | - | - | ANTIFUSE5_E N | ANTIFUSE5_L OAD | ANTIFUSE5_R W | BYPASS5 | | |
| | OTINES | | _ | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | | |

7 Typical applications

7.1 Application diagram

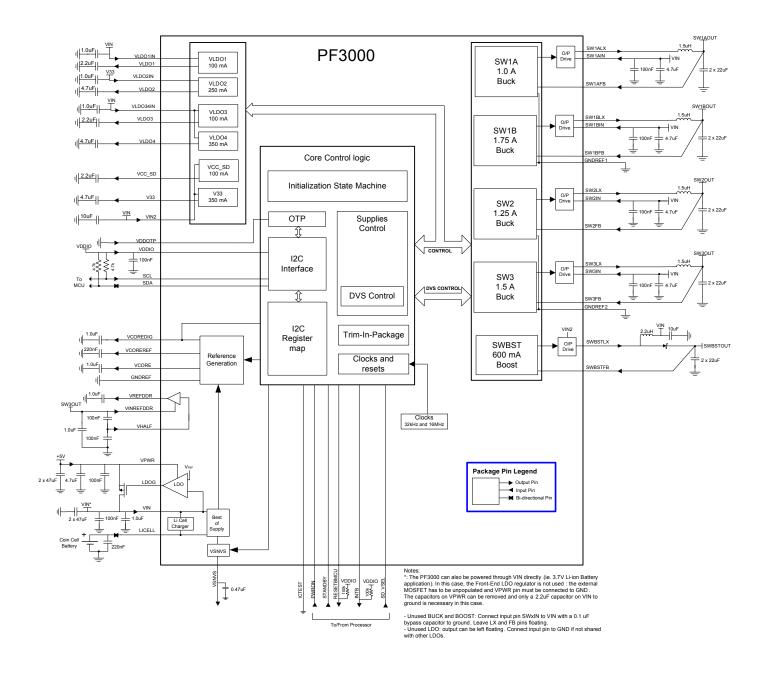


Figure 36. Typical application schematic

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8 Bill of materials

The following table provides a complete list of the recommended components on a full featured system using the PF3000 Device for -40 °C to 85 °C applications. Components are provided with an example part number; equivalent components may be used.

Table 198. Bill of materials for -40 °C to 85 °C applications

| Value | Qty | Description | Part# | Manufacturer | Component/Pin |
|-------------|--------|--|--------------------|--------------|--|
| PMIC | | | | | l |
| N/A | 1 | Power management IC | PF3000 | NXP | IC |
| Buck regula | ators | | | <u>'</u> | |
| 1.5 µH | 4 | IND PWR 1.5 μH at 1.0 MHz 2.9 A 20% 2016 | DFE201610E-1R5M | TOKO INC. | SW1A, SW1B, SW2, SW3 inductors |
| 1.5 μπ | 4 | IND PWR 1.5 μH at 1.0 MHz 2.2 A 20% 1210 | BRL3225T1R5M | Taiyo Yuden | Alternate for low-power applications |
| 4.7 µF | 4 | CAP CER 4.7 μF 10 V 20% X5R 0402 | GRM155R61A475MEAA | Murata | SW1A, SW1B, SW2, SW3 input capacitors |
| 0.1 μF | 4 | CAP CER 0.1 μF 10 V 20% X5R 0201 | GRM033R61A104ME84 | Murata | SW1A, SW1B, SW2, SW3 input capacitors (optional) |
| 22 µF | 8 | CAP CER 22 μF 10 V 20% X5R 0603 | GRM188R61A226ME15 | Murata | SW1A, SW1B, SW2, SW3 output capacitors |
| Boost regul | ator | | | <u>'</u> | |
| 22 | 1 | IND PWR 2.2 µH at 1.0 MHz 2.4 A 20% 2016 | DFE201610E-2R2M | TOKO INC. | SWBST inductor |
| 2.2 µH | I | IND PWR 2.2 µH at 1.0 MHz 1.85 A 20% 1210 | BRL3225T2R2M | Taiyo Yuden | Alternate for low-power applications |
| 10 μF | 1 | CAP CER 10 µF 10 V 20% X5R 0402 | GRM155R61A106ME11 | Murata | SWBST input capacitor |
| N/A | 1 | DIODE SCH PWR RECT 1.0 A 20 V SMT | MBR120LSFT3G | ON Semi | SWBST diode |
| 22 μF | 2 | CAP CER 22 µF 10 V 20% X5R 0603 | GRM188R61A226ME15D | Murata | SWBST output capacitors |
| Linear regu | lators | | | ' | |
| 1.0 µF | 3 | CAP CER 1.0 μF 10 V 20% X5R 0201 | GRM033R61A105ME44 | Murata | VLDO1, VLDO2, VLDO3 and VLDO4 input capacitors |
| 2.2 µF | 3 | CAP CER 2.2 μF 10 V 20% X5R 0201 | GRM033R61A225ME47 | Murata | VLDO1, VLDO3, VCC_SD output capacitors |
| 10 μF | 1 | CAP CER 10 µF 10 V 20% X5R 0402 | GRM155R61A106ME11 | Murata | V33 and VCC_SD input capacitor |
| 4.7 µF | 3 | CAP CER 4.7 μF 10 V 20% X5R 0402 | GRM155R61A475MEAA | Murata | VLDO2, VLDO4, V33 output capacitors |
| Miscellaneo | ous | | | | |
| 1.0 µF | 4 | CAP CER 1.0 μF 10 V 20% X5R 0201 | GRM033R61A105ME44 | Murata | VCORE, VCOREDIG, VREFDDR, VINREFDDR capacitors |
| 0.22 μF | 2 | CAP CER 0.22 μF 10 V 20% X5R 0201 | GRM033R61A224ME90 | Murata | VCOREREF and Coin Cell output capacitors |
| 0.47 μF | 1 | CAP CER 0.47 μF 10 V 20% X5R 0201 | GRM033R61A474ME90 | Murata | VSNVS output capacitor |
| 47 μF | 4 | CAP CER 47 μF 10 V 20% X5R 0805 | GRM21BR61A476ME15 | Murata | Front-end LDO capacitors for VIN and VPWR. |

Table 198. Bill of materials for -40 °C to 85 °C applications (continued)

| Value | Qty | Description | Part# | Manufacturer | Component/Pin |
|--------|-----|--------------------------------------|-------------------|---------------|---|
| 2.2 µF | 1 | CAP CER 2.2 μF 10 V 20% X5R 0201 | GRM033R61A225ME47 | Murata | VIN input capacitor when not using Front-end LDO |
| 0.1 µF | 5 | CAP CER 0.1 µF 10 V 10% X5R 0201 | GRM033R61A104KE84 | Murata | VDDIO, VHALF, VPWR, VIN input capacitors (optional) |
| N/A | 1 | TRAN PMOS 11. A 12 V 12 SOT- 1220 | PMPB15XP | NXP | External MOSFET |
| 100 k | 2 | RES MF 100 k 1/16 W 1% 0402 | RC0402FR-07100KL | Yageo America | Pull-up resistors |
| 4.7 k | 2 | RES MF 4.70 k 1/20 W 1% 0201 | RC0201FR-074K7L | Yageo America | I ² C pull-up resistors |

The following table provides a complete list of the recommended components on a full featured system using the PF3000 Device for -40 °C to 105 °C applications. Components are provided with an example part number, equivalent components may be used.

Table 199. Bill of materials for -40 °C to 105 °C applications

| Value | Qty | Description | Part# | Manufacturer | Component/Pin |
|-------------|----------|--|--------------------|--------------|--|
| РМІС | <u> </u> | | | | |
| N/A | 1 | Power management IC | PF3000 | NXP | IC |
| Buck regula | itors | | | · | |
| 1.5 µH | 4 | IND PWR 1.5 µH at 1.0 MHz 2.9 A 20% 2016 | DFE201610E-1R5M | Toko Inc. | SW1A, SW1B, SW2, SW3 inductors |
| 1.5 μΠ | 4 | IND PWR 1.5 µH at 1.0 MHz 2.2 A 20% 1210 | BRL3225T1R5M | Taiyo Yuden | Alternate for low-power applications |
| 4.7 µF | 4 | CAP CER 4.7 μF 10 V 10% X7S 0603 | GRM188C71A475KE11 | Murata | SW1A, SW1B, SW2, SW3 input capacitors |
| 0.1 µF | 4 | CAP CER 0.1 μF 10 V 10% X7S 0201 | GRM033C71A104KE14 | Murata | SW1A, SW1B, SW2, SW3 input capacitors (optional) |
| 22 μF | 8 | CAP CER 22 µF 10 V 20% X7T 0805 | GRM21BD71A226ME44 | Murata | SW1A, SW1B, SW2, SW3 output capacitors |
| Boost regul | ator | - | | 1 | |
| 22 | 1 | IND PWR 2.2 µH at 1.0 MHz 2.4 A 20% 2016 | DFE201610E-2R2M | Toko Inc. | SWBST Inductor |
| 2.2 µH | μιι ι | IND PWR 2.2 µH at 1.0 MHz 1.85 A 20% 1210 | BRL3225T2R2M | Taiyo Yuden | Alternate for low-power applications |
| 10 μF | 1 | CAP CER 10 μF 10 V 20% X7T 0603 | GRM188D71A106MA73 | Murata | SWBST input capacitor |
| N/A | 1 | DIODE SCH PWR RECT 1.0 A 20 V SMT | MBR120LSFT3G | ON Semi | SWBST diode |
| 22 μF | 2 | CAP CER 22 μF 10 V 20% X5R 0603 | GRM188R61A226ME15D | Murata | SWBST output capacitors |
| inear regu | lators | | | | |
| 1.0 µF | 3 | CAP CER 1.0 μF 10 V 10% X7S 0402 | GRM155C71A105KE11 | Murata | VLDO1, VLDO2, VLDO3 and VLDO4 input capacitors |
| 2.2 µF | 3 | CAP CER 2.2 µF 10 V 10% X7S 0402 | GRM155C71A225KE11 | Murata | VLDO1, VLDO3, VCC_SD output capacitors |
| 10 μF | 1 | CAP CER 10 μF 10 V 20% X7T 0603 | GRM188D71A106MA73 | Murata | V33 and VCC_SD input capacitor |

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Table 199. Bill of materials for -40 $^{\circ}\text{C}$ to 105 $^{\circ}\text{C}$ applications (continued)

| Value | Qty | Description | Part# | Manufacturer | Component/Pin |
|--------------|-----|--------------------------------------|-------------------|---------------|--|
| 4.7 µF | 3 | CAP CER 4.7 µF 10 V 10% X7S 0603 | GRM188C71A475KE11 | Murata | VLDO2, VLDO4, V33 output capacitors |
| Miscellaneou | ıs | | | | |
| 1.0 μF | 4 | CAP CER 1.0 μF 10 V 10% X7R 0402 | GRM155C71A105KE11 | Murata | VCORE, VCOREDIG, VREFDDR, VINREFDDR capacitors |
| 0.22 μF | 2 | CAP CER 0.22 μF 10 V 10% X7R 0402 | GRM155R71A224KE01 | Murata | VCOREREF and coin cell output capacitors |
| 0.47 μF | 1 | CAP CER 0.47 μF 10 V 20% X5R 0201 | GRM155R71A474KE01 | Murata | VSNVS output capacitor |
| 47 μF | 4 | CAP CER 47 µF 10 V 20% X7R 1210 | GRM32ER71A476ME15 | Murata | Front-end LDO capacitors for VIN and VPWR. |
| 2.2 µF | 1 | CAP CER 2.2 μF 10 V 10% X7S 0402 | GRM155C71A225KE11 | Murata | VIN input capacitor when not using front-end LDO |
| 0.1 µF | 5 | CAP CER 0.1 µF 10 V 10% X7S 0201 | GRM033C71A104KE14 | Murata | VDDIO, VHALF, VPWR, VIN input capacitors (optional) |
| N/A | 1 | TRAN PMOS 11. A 12 V 12 SOT- 1220 | PMPB15XP | NXP | External MOSFET |
| 100 k | 2 | RES MF 100k 1/16 W 1% 0402 | RC0402FR-07100KL | Yageo America | Pull-up resistors |
| 4.7 k | 2 | RES MF 4.70k 1/20 W 1% 0201 | RC0201FR-074K7L | Yageo America | I ² C pull-up resistors |

9 Thermal information

9.1 Rating data

The thermal rating data of the packages has been simulated with the results listed in Thermal ratings. Junction to ambient thermal resistance nomenclature: the JEDEC specification reserves the symbol $R_{\theta JA}$ or θJA (Theta-JA) strictly for junction-to-ambient thermal resistance on a 1s test board in natural convection environment. $R_{\theta JMA}$ or θJMA (Theta-JMA) is used for both junction-to-ambient on a 2s2p test board in natural convection and for junction-to-ambient with forced convection on both 1s and 2s2p test boards. It is anticipated that the generic name, Theta-JA, continues to be commonly used. The JEDEC standards can be consulted at https://www.jedec.org.

9.2 Estimation of junction temperature

An estimation of the chip junction temperature T_{,I} can be obtained from the equation:

 $T_J = T_A + (R_{\theta JA} \times P_D)$

with:

T_A = Ambient temperature for the package in °C

R_{0.IA} = Junction to ambient thermal resistance in °C/W

P_D = Power dissipation in the package in W

The junction to ambient thermal resistance is an industry standard value that provides a quick and easy estimation of thermal performance. Unfortunately, there are two values in common usage: the value determined on a single layer board $R_{\theta JMA}$ and the value obtained on a four layer board $R_{\theta JMA}$. Actual application PCBs show a performance close to the simulated four layer board value although this may be somewhat degraded in case of significant power dissipated by other components placed close to the device.

At a known board temperature, the junction temperature T_J is estimated using the following equation

 $T_J = T_B + (R_{\theta JB} \times P_D)$ with

T_B = Board temperature at the package perimeter in °C

R_{0.IB} = Junction to board thermal resistance in °C/W

P_D = Power dissipation in the package in W

When the heat loss from the package case to the air can be ignored, acceptable predictions of junction temperature can be made.

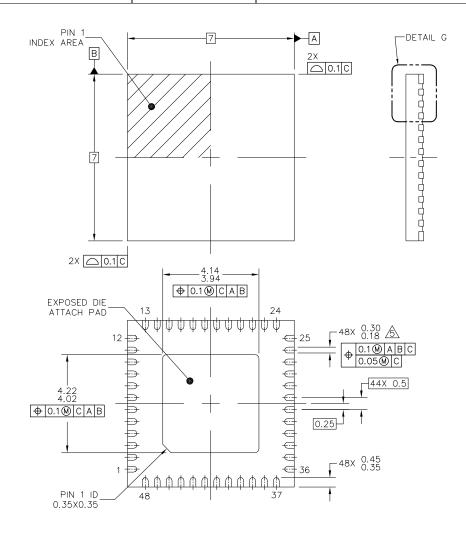
10 Packaging

10.1 Packaging dimensions

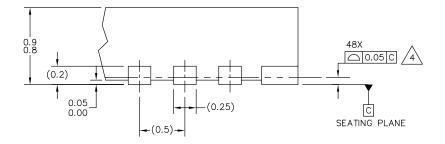
Package dimensions are provided in package drawings. To find the most current package outline drawing, go to www.nxp.com and perform a keyword search for the drawing's document number. See the Thermal Characteristics section for specific thermal characteristics for each package.

Table 200. Package drawing information

| Package | Suffix | Package outline drawing number |
|---|--------|--------------------------------|
| 48-pin QFN 7X7 mm - 0.5mm pitch | EP | 98ASA00719D |
| 48 QFN 7.0 mm x 7.0 mm WF-type (wettable flank) | ES | 98ASA00933D |



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|--|--------------------|--------------------|-------------------|----------|
| TITLE: | DOCUME | NT NO: 98ASA00719D | REV: B | |
| QFN, THERMALLY ENHANCED, 7 X 7 X 0.85, 0.5 PITCH, 48 TERMINAL | | | RD: NON-JEDEC | |
| , x , x e.ee, e.e + 11en, | | | 27 JUN 2014 | |



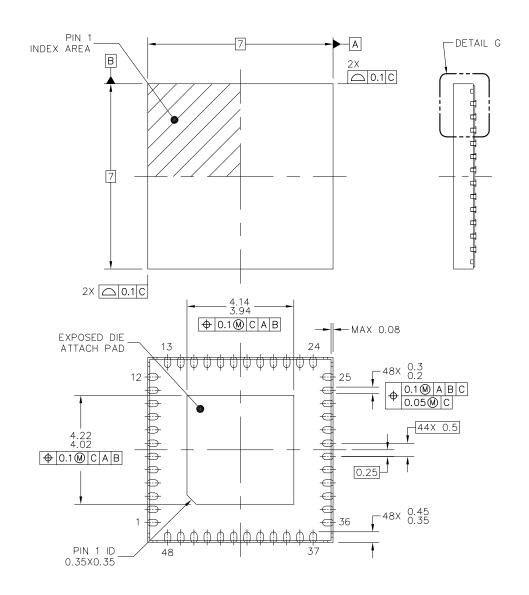
DETAIL G VIEW ROTATED 90°CW

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|--|---------------|---------------|----------------------|--------|
| TITLE: | | | NT NO: 98ASA00719D | REV: B |
| QFN, THERMALLY ENH 7 X 7 X 0.85, 0.5 PITCH. | STANDAR | RD: NON-JEDEC | | |
| 7 % 7 % 0.03, 0.3 111011, | | 27 | JUN 2014 | |

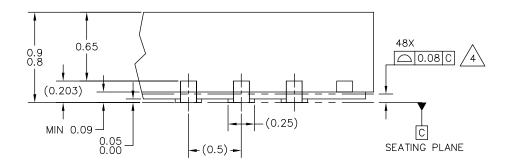
NOTES:

- 1. ALL DIMENSIONS ARE IN MILLIMETERS.
- 2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- 3. THIS IS A NON-JEDEC REGISTERED PACKAGE.
- 4. COPLANARITY APPLIES TO LEADS AND DIE ATTACH FLAG.
- DIMENSION APPLIES TO METALLIZED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.3 MM FROM TERMINAL TIP. IF THE TERMINAL HAS THE OPTIONAL RADIUS ON THE OTHER END OF THE TERMINAL, THE DIMENSION SHOULD NOT BE MEASURED IN THAT RADIUS AREA.

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|---|---------------|---------|---------------------|---------|----|
| TITLE: | LANGER | DOCUMEN | NT NO: 98ASA00719D | REV: | В |
| QFN, THERMALLY ENHANCED, 7 X 7 X 0.85. 0.5 PITCH. 48 TERMINAL | | | RD: NON-JEDEC | | |
| / // // d.dd, d.d | | | 27 | JUN 201 | 14 |



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|---|---------------|--------------------|----------------------|--------|
| TITLE: | DOCUME | NT NO: 98ASA00933D | REV: 0 | |
| QFN, THERMALLY ENH 7 X 7 X 0.85. 0.5 PITCH. | STANDAF | RD: NON-JEDEC | | |
| / X / X 0.85, 0.5 FITCH, 46 TERMINAL | | | 23 SE | P 2015 |



DETAIL G VIEW ROTATED 90°CW

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|--|---------------|-------|--------------------|------------|
| OFN. THERMALLY ENHANCED. | | | NT NO: 98ASA00933D | REV: 0 |
| | | | RD: NON-JEDEC | |
| | | : | 23 SEP 2015 | |

NOTES:

- 1. ALL DIMENSIONS ARE IN MILLIMETERS.
- 2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- 3. THIS IS A NON-JEDEC REGISTERED PACKAGE.
- 4 COPLANARITY APPLIES TO LEADS, CORNER LEADS AND DIE ATTACH PAD.
- 5. MIN METAL GAP SHOULD BE 0.2 MM.

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|--|---------------|---------|--------------------|------------|
| TITLE: QFN, THERMALLY ENHANCED, 7 X 7 X 0.85, 0.5 PITCH, 48 TERMINAL | | DOCUME | NT NO: 98ASA00933D | REV: 0 |
| | | STANDAF | RD: NON-JEDEC | |
| | | | 23 | 3 SEP 2015 |

11 Revision history

| Revision | Date | Description of changes |
|----------|---------|--|
| 1.0 | 11/2014 | Initial release |
| 2.0 | 2/2015 | VREFDDR output accuracy spec re-formatted Added typical performance waveforms Corrected OTP option 1 set points LDO current limit specifications updated VPWR LDO output voltage accuracy specification updated Updated register names of Extended Page 1 registers to maintain consistency throughout document Added typical bill of materials |
| 3.0 | 2/2015 | Corrected Register INTSENSE0 - ADDR 0x07 Added orderable part numbers PC32PF3000A5EP and PC34PF3000A5EP |
| 4.0 | 6/2015 | Included i.MX Series processor Redefined voltages for SW1A and SW1A/B Corrected typographic errors Improved bill of materials capacitors Updated SW1A/B, SW1A, and SW1B Output Voltage Accuracy Added note on LICELL for Operating Input Voltage Improved temperature range to 105 °C Updated ILIM max values for Linear regulators VCOREDIG/VCOREREF tables updated Updated LSL of ISW1BLIM to 2.4 A |
| 5.0 | 6/2015 | Replaced i.MX Series by i.MX 7 Added i.MX 6UL processor Updated Bill of Materials Table 199 |
| 6.0 | 8/2015 | Added MC32PF3000A6EP, MC34PF3000A6EP, MC32PF3000A7EP, and MC34PF3000A7EP parts to the Orderable Part Variations Table Updated Table 42 Removed i.MX 6 DL note on Power Virus Updated the definition of rated current for switchers and linear regulators |
| 7.0 | 3/2016 | Added 98ASA00933D and the page 1 package image for wettable flank Changed Table 2, pins 7, 10, 18, and 28, from Bypass with at least a 10 μF to Bypass with at least a 4.7 μF Added PC33PF3000A0ES, PC33PF3000A3ES, PC33PF3000A4ES, PC33PF3000A5ES, PC33PF3000A6ES, and PC33PF3000A7ES to Table 1 |
| | 8/2016 | Changed PC33PF3000A0ES, PC33PF3000A3ES, PC33PF3000A4ES, PC33PF3000A6ES, and PC33PF3000A7ES to MC parts in Table 1 |
| | 9/2016 | Updated Table 66 LDO Control to accurately describe all modes |
| 8.0 | 3/2017 | Added MC32PF3000A8EP and MC34PF3000A8EP parts to Table 1 Added new note ⁽²⁾ to Table 1 Updated V _{SW1AACC} parameter in Table 7 Added OTP configuration for A8 to Table 42 Updated Table 80 (changed default value to 1) |
| 9.0 | 8/2017 | Updated notes ⁽⁴⁷⁾ and ⁽⁴⁹⁾ as per 201707041I |

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